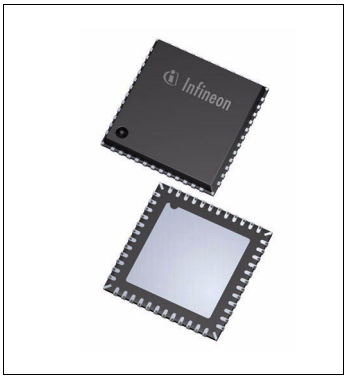
# TLE9862QXA40

## Microcontroller with LIN and H-Bridge MOSFET Driver for Automotive Applications
## A-Step



## Features

- 32-bit Arm®* Cortex®-M3 core
- 256 KB flash
- 8 KB RAM
- On-chip OSC and PLL for clock generation
- MOSFET driver including charge pump
- 1 LIN 2.2 transceiver
- High-speed operational amplifier for motor current sensing via shunt
- Single power supply from 5.5 V to 27 V
- Temperature range $T_j$ = -40°C to +150°C

## Potential applications

- Wiper
- Aux. pumps
- Fans
- Window lift
- Sunroof
- Tailgate

## Product validation

Qualified for automotive applications. Product validation according to AEC-Q100/101.

## Description

| Type | Package | Marking |
|---|---|---|
| TLE9862QXA40 | VQFN-48-29 | |

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# 1 Overview

### Summary of Features

- 32-bit Arm® Cortex®-M3 core
  - Up to 40 MHz clock frequency
  - One clock per machine cycle architecture
- On-chip memory
  - 256 KB flash including
  - 4 KB EEPROM (emulated in flash)
  - 512 byte 100-time programmable memory (100TP)
  - 8 KB RAM
  - Boot ROM for startup firmware and flash routines
- On-chip OSC and PLL for clock generation
  - PLL loss-of-lock detection
- MOSFET driver including charge pump
- 10 general-purpose I/O Ports (GPIO)
- 5 analog inputs, 10-bit A/D Converter (ADC1)
- 16-bit timers - GPT12, Timer2, Timer21, and Timer3
- Capture/compare unit for PWM signal generation (CCU6)
- 2 full-duplex serial interfaces (UART) with LIN support (for UART1 only)
- 2 synchronous serial channels (SSC)
- On-chip debug support via 2-wire SWD
- 1 LIN 2.2 transceiver
- 1 high-voltage monitoring input
- Single power supply from 5.5 V to 27 V
- Extended power supply voltage range from 3 V to 28 V
- Low-dropout voltage regulators (LDO)
- High-speed operational amplifier for motor current sensing via shunt
- 5 V voltage supply for external loads (e.g., Hall sensor)
- Core logic supply at 1.5 V
- Programmable window watchdog (WDT1) with independent on-chip clock source
- Power-saving modes
  - MCU slow-down mode
  - Sleep mode
  - Stop mode
  - Cyclic wake-up sleep mode
- Power-on and undervoltage/brownout reset generator
- Overtemperature protection
- Short-circuit protection
- Loss of clock detection with fail-safe mode entry for low system power consumption
- Temperature range $T_j$ = -40°C to +150°C

## Overview

- Package VQFN-48 with LTI feature
- Green package (RoHS compliant)
- AEC-qualified

## 1.1 Abbreviations

The following acronyms and terms are used within this document. List see in **Table 1**.

**Table 1 Acronyms**

| Acronyms | Name |
|---|---|
| AHB | Advanced High-performance Bus |
| APB | Advanced Peripheral Bus |
| CCU6 | Capture compare unit 6 |
| CGU | Clock generation unit |
| CMU | Cyclic management unit |
| CP | Charge pump for MOSFET driver |
| CSA | Current-sense amplifier |
| DPP | Data post-processing |
| ECC | Error correction code |
| EEPROM | Electrically erasable programmable read only memory |
| EIM | Exceptional interrupt measurement |
| FSM | Finite state machine |
| GPIO | General-purpose input/output |
| H-Bridge | Half-bridge |
| ICU | Interrupt control unit |
| IEN | Interrupt enable |
| IIR | Infinite impulse response |
| LDM | Load instruction |
| LDO | Low-dropout voltage regulator |
| LIN | Local interconnect network |
| LSB | Least significant bit |
| LTI | Lead tip inspection |
| MCU | Microcontroller unit |
| MF | Measurement functions |
| MSB | Most significant bit |
| MPU | Memory protection unit |
| MRST | Master receive, slave transmit |
| MTSR | Master transmit, slave receive |
| MU | Measurement unit |
| NMI | Non-maskable interrupt |
| NVIC | Nested vector interrupt controller |
| NVM | Non-volatile memory |
| OTP | One-time programmable |
| OSC | Oscillator |
| PBA | Peripheral bridge |

**Table 1 Acronyms** (cont'd)

| Acronyms | Name |
|---|---|
| PCU | Power control unit |
| PD | Pull-down |
| PGU | Power supply generation unit |
| PLL | Phase-locked loop |
| PPB | Private Peripheral Bus |
| PU | Pull-up |
| PWM | Pulse-width modulation |
| RAM | Random-access memory |
| RCU | Reset control unit |
| RMU | Reset management unit |
| ROM | Read-only memory |
| SCU-DM | System control unit – digital modules |
| SCU-PM | System control unit – power modules |
| SFR | Special function register |
| SOW | Short open window (for WDT) |
| SPI | Serial Peripheral Interface |
| SSC | Synchronous serial channel |
| STM | Store instruction |
| SWD | Arm® Serial Wire Debug |
| TCCR | Temperature compensation control register |
| TMS | Test mode select |
| TSD | Thermal shut-down |
| UART | Universal asynchronous receiver-transmitter |
| VBG | Voltage reference bandgap |
| VCO | Voltage-controlled oscillator |
| VPRE | Preregulator |
| WDT | Watchdog timer in SCU-DM |
| WDT1 | Watchdog timer in SCU-PM |
| WMU | Wake-up management unit |
| 100TP | 100-time programmable |

# 2 Block diagram

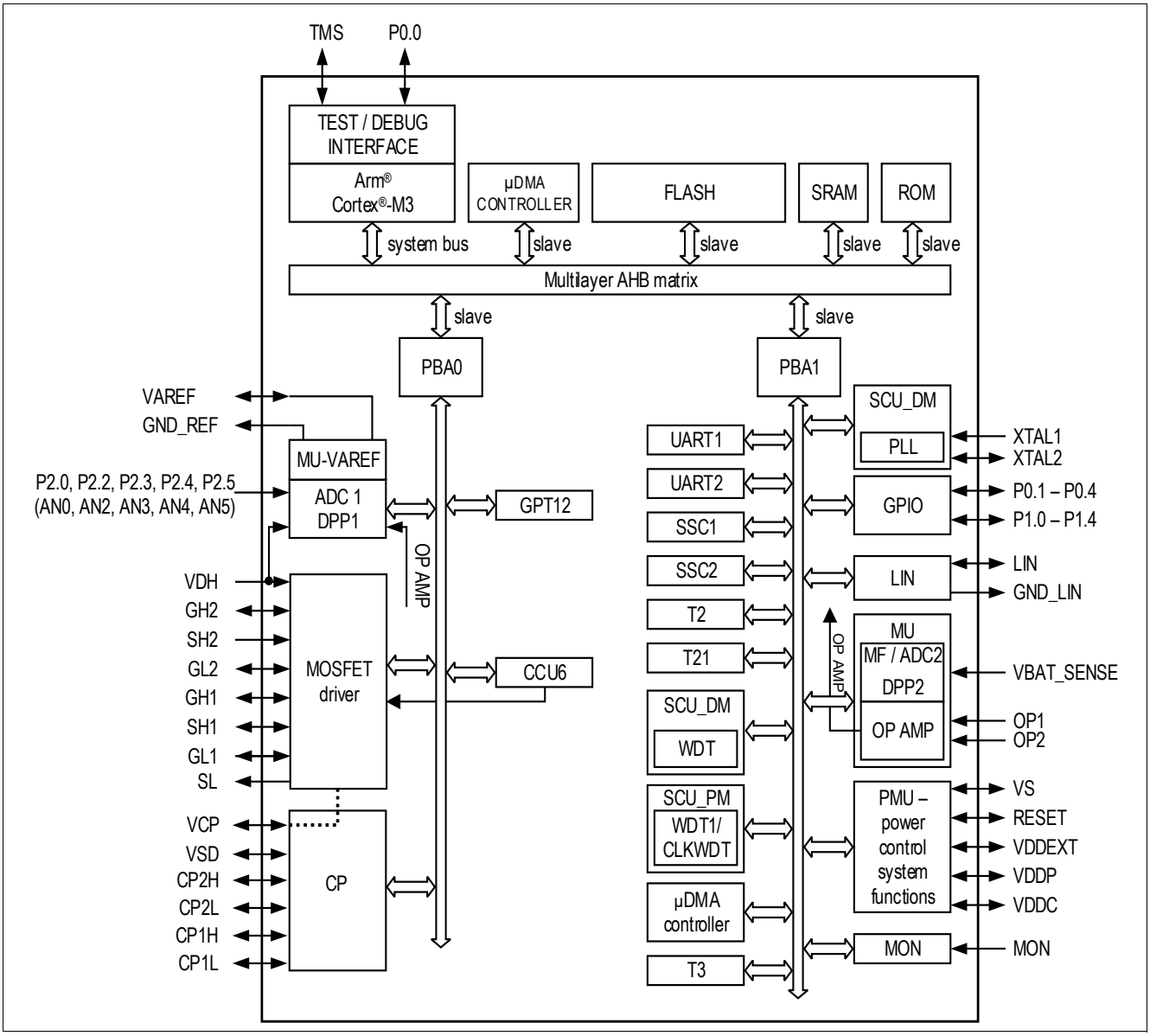


**Figure 1 Block diagram**

# 3 Device pinout and pin configuration

## 3.1 Device pinout

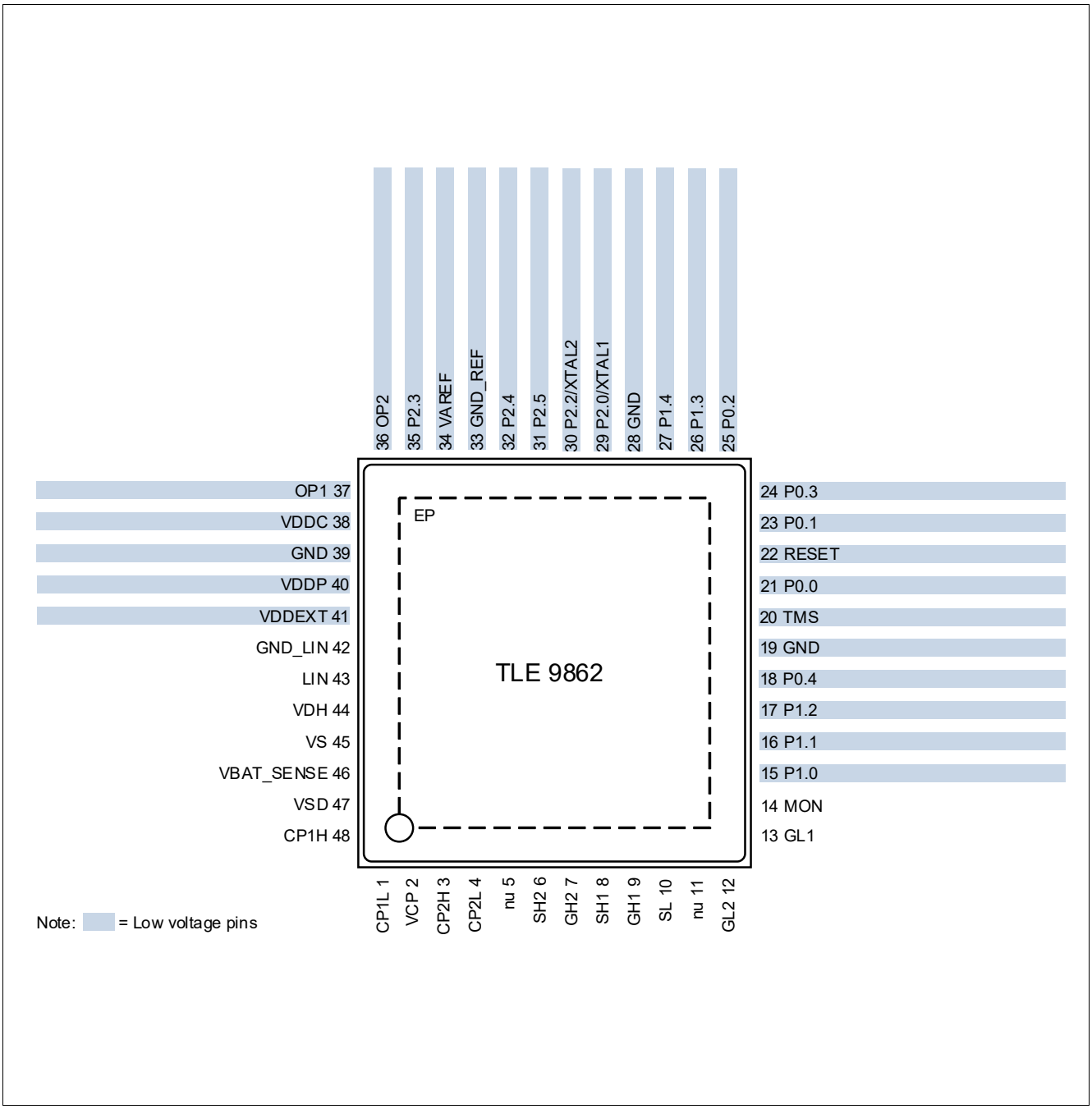


**Figure 2 Device pinout**

## 3.2 Pin configuration

After a reset, all pins are configured as input (except supply and LIN pins) with one of the following settings:

- Pull-up device enabled only (PU)
- Pull-down device enabled only (PD)
- Input with both pull-up and pull-down devices disabled (I)
- Output with output stage deactivated = high-impedance state (Hi-Z)

The functions and default states of the TLE9862QXA40 external pins are provided in the following table.

Type: indicates the pin type.

- I/O: Input or output
- I: Input only
- O: Output only
- P: Power supply

Not all alternate functions are listed.

**Table 2 Pin definitions and functions**

| Symbol | Pin number | Type | Reset state[1)] | Function | |
|---|---|---|---|---|---|
| **P0** | | | | **Port 0**<br>Port 0 is a 5-bit bidirectional general-purpose I/O port. Alternate functions can be assigned and are listed in the port description. The main functions are listed below. | |
| P0.0 | 21 | I/O | I/PU | SWD | Serial wire debug clock |
| P0.1 | 23 | I/O | I/PU | GPIO | General-purpose I/O<br>Alternate function mapping see **Table 8**. |
| P0.2 | 25 | I/O | I/PD | GPIO | General-purpose I/O<br>Alternate function mapping see **Table 8**.<br><br>*Note: For a functional SWD connection, this GPIO must be tied to zero.* |
| P0.3 | 24 | I/O | I/PU | GPIO | General-purpose I/O<br>Alternate function mapping see **Table 8**. |
| P0.4 | 18 | I/O | I/PD | GPIO | General-purpose I/O<br>Alternate function mapping see **Table 8**. |
| **P1** | | | | **Port 1**<br>Port 1 is a 5-bit bidirectional general-purpose I/O port. Alternate functions can be assigned and are listed in the port description. The main functions are listed below. | |
| P1.0 | 15 | I/O | I | GPIO | General-purpose I/O<br>Alternate function mapping see **Table 8**. |
| P1.1 | 16 | I/O | I | GPIO | General-purpose I/O<br>Alternate function mapping see **Table 9**. |
| P1.2 | 17 | I/O | I | GPIO | General-purpose I/O<br>Alternate function mapping see **Table 9**. |

**Table 2 Pin definitions and functions** (cont'd)

| Symbol | Pin number | Type | Reset state[1)] | Function | |
|---|---|---|---|---|---|
| P1.3 | 26 | I/O | I | GPIO | General-purpose I/O, used for inrush transistor<br>Alternate function mapping see **Table 9**. |
| P1.4 | 27 | I/O | I | GPIO | General-purpose I/O<br>Alternate function mapping see **Table 9**. |
| **P2** | | | | **Port 2**<br>Port 2 is a 5-bit general-purpose input-only port.<br>Alternate functions can be assigned and are listed in the port description. The main functions are listed below. | |
| P2.0/XTAL1 | 29 | I/I | I | AN0 | ADC analog input 0<br>Alternate function mapping see **Table 10**. |
| P2.2/XTAL2 | 30 | I/O | I | AN2 | ADC analog input 2<br>Alternate function mapping see **Table 10**. |
| P2.3 | 35 | I | I | AN3 | ADC analog input 3<br>Alternate function mapping see **Table 10**. |
| P2.4 | 32 | I | I | AN4 | ADC analog input 4<br>Alternate function mapping see **Table 10**. |
| P2.5 | 31 | I | I | AN5 | ADC analog input 5<br>Alternate function mapping see **Table 10**. |
| **Power supply** | | | | | |
| VS | 45 | P | – | Battery supply input | |
| VDDP | 40 | P | – | [2)]I/O port supply (5.0 V). Connect external buffer capacitor. | |
| VDDC | 38 | P | – | [3)]Core supply (1.5 V in Active mode).<br>Do not connect external loads, but connect an external buffer capacitor. | |
| VDDEXT | 41 | P | – | External voltage supply output (5.0 V, 20 mA) | |
| GND | 19 | P | – | GND digital | |
| GND | 28 | P | – | GND digital | |
| GND | 39 | P | – | GND analog | |
| **Monitor input** | | | | | |
| MON | 14 | I | – | High voltage monitor input | |
| **LIN interface** | | | | | |
| LIN | 43 | I/O | – | LIN bus interface input/output | |
| GND_LIN | 42 | P | – | LIN ground | |
| **Charge pump** | | | | | |
| CP1H | 48 | P | – | Charge pump capacity 1 high, connect external C | |
| CP1L | 1 | P | – | Charge pump capacity 1 low, connect external C | |
| CP2H | 3 | P | – | Charge pump capacity 2 high, connect external C | |
| CP2L | 4 | P | – | Charge pump capacity 2 low, connect external C | |
| VCP | 2 | P | – | Charge pump capacity | |

**Table 2 Pin definitions and functions** (cont'd)

| Symbol | Pin number | Type | Reset state[1)] | Function |
|---|---|---|---|---|
| VSD | 47 | P | – | Battery supply input for charge pump |
| **MOSFET driver** | | | | |
| VDH | 44 | P | – | Voltage drain high-side MOSFET driver |
| SH2 | 6 | P | – | Source high-side FET 2 |
| GH2 | 7 | P | – | Gate high-side FET 2 |
| SH1 | 8 | P | – | Source high-side FET 1 |
| GH1 | 9 | P | – | Gate high-side FET 1 |
| SL | 10 | P | – | Source low-side FET |
| GL2 | 12 | P | – | Gate low-side FET 2 |
| GL1 | 13 | P | – | Gate low-side FET 1 |
| **Others** | | | | |
| GND_REF | 33 | P | – | GND for VAREF |
| VAREF | 34 | I/O | – | 5V ADC1 reference voltage, optional buffer or input |
| OP1 | 37 | I | – | Negative operational amplifier input |
| OP2 | 36 | I | – | Positive operational amplifier input |
| TMS | 20 | I<br>I/O | I/PD | TMS Test mode select input<br>SWD Serial Wire Debug input/output |
| RESET | 22 | I/O | – | Reset input, not available during sleep mode |
| VBAT_SENSE | 46 | I | – | Battery supply voltage sense input |
| EP | – | – | – | Exposed pad, connect to GND |

1) Only valid for digital IO.
2) Also named VDD5V.
3) Also named VDD1V5.

# 4 Modes of operation

The TLE9862QXA40 highly integrated circuit contains analog and digital functional blocks. An embedded 32-bit microcontroller is available for system and interface control. On-chip, low-dropout regulators are provided for internal and external power supply. An internal oscillator provides a cost-effective clock that is particularly well suited for LIN communications. A LIN transceiver is available as a communication interface. Driver stages for an H-bridge with external MOSFET are integrated, featuring PWM capability, protection features, and a charge pump for operation at low supply voltage. A 10-bit SAR ADC is implemented for high-precision sensor measurement. An 8-bit ADC is used for diagnostic measurements.

The Micro controller unit supervision and system protection (including a reset feature) is complemented by a programmable window watchdog. A cyclic wake-up circuit, supply voltage supervision and integrated temperature sensors are available on-chip.

All relevant modules offer power saving modes in order to support automotive applications connected to terminal 30. A wake-up from power-save mode is possible via a LIN bus message, via the monitoring input, or using a programmable time period (cyclic wake-up).

The TLE9862QXA40 has several operation modes mainly to support low power consumption requirements.

### Reset mode

The Reset mode is a transition mode used, e.g., during power-up of the device after a power-on reset, or after wake-up from Sleep mode. In this mode, the on-chip power supplies are enabled and all other modules are initialized. Once the core supply VDDC is stable, the device enters Active mode. If the watchdog timer WDT1 fails more than four times, the device performs a fail-safe transition to Sleep mode.

### Active mode

In Active mode, all modules are activated and the TLE9862QXA40 is fully operational.

### Stop mode

Stop mode is one of two major low-power modes. The transition to the low-power modes is performed by setting the corresponding bits in the mode control register. In Stop mode, the embedded microcontroller is still powered, allowing for shorter wake-up response times. Wake-up from this mode is possible through LIN bus activity, by using the high-voltage monitoring pin, or through the corresponding 5 V GPIOs.

### Stop mode with cyclic wake-up

The Cyclic Wake-Up mode is a special operating mode of the Stop mode. The transition to the Cyclic Wake-Up mode is performed by first setting the corresponding bits in the mode control register, followed by the Stop Mode command. In addition to the cyclic wake-up behavior (wake-up after a programmable time period), asynchronous wake events via the activated sources (LIN and/or MON) are available, as in normal Stop mode.

### Sleep mode

The Sleep mode is a low-power mode. The transition to the low-power mode is performed by setting the corresponding bits in the MCU mode control register or in case of failure (see below). In Sleep mode the embedded microcontroller power supply is deactivated, allowing for the lowest system power consumption. A wake-up from this mode is possible by LIN bus activity, the High Voltage Monitor Input pin, or through cyclic wake-up.

### Sleep mode in case of failure

Sleep mode is activated after 5 consecutive watchdog failures or in case of supply failure (5 times). In this case, MON is enabled as the wake source and cyclic wake-up is activated with 1 s of dead time.

## Modes of operation

### Sleep Mode with cyclic wake-up

The Cyclic Wake-Up mode is a special operating mode of the Sleep mode. The transition to Cyclic Wake-Up mode is performed by first setting the corresponding bits in the mode control register followed by the Sleep Mode and Stop Mode commands. In addition to the cyclic wake-up behavior (wake-up after a programmable time period), asynchronous wake events via the activated sources (LIN and/or MON) are available, as in normal Sleep mode.

When using Sleep mode with cyclic wake-up, the voltage regulator is switched off and started again with the wake. A limited number of registers is buffered during sleep, and can be used by software, e.g., for counting sleep/wake cycles.

### MCU Slow Down mode

In MCU Slow Down mode the MCU frequency is reduced to save power during operation. LIN communication is still possible. LS MOSFET can be activated.

### Wake-up source prioritization

All wake-up sources have the same priority. In order to handle the asynchronous nature of the wake-up sources, the first wake-up signal will initiate the wake-up sequence. Nevertheless, all wake-up sources are latched in order to provide all wake-up events to the application software. The software can clear the wake-up source flags. This is to ensure that no wake-up event is lost.

As the default wake-up source, the MON input is activated after power-on reset only. Additionally, the device is in Cyclic Wake-Up mode with the configurable dead time setting.

The following table shows the possible power mode configurations including the Stop mode.

**Table 3 Power mode configurations**

| Module/function | Active mode | Stop mode | Sleep mode | Comment |
|---|---|---|---|---|
| VDDEXT | ON/OFF | ON (no dynamic load)/OFF | OFF | – |
| Bridge Driver | ON/OFF | OFF | OFF | |
| LIN TRx | ON/OFF | Wake-up only/OFF | Wake-up only/OFF | – |
| VS sense | ON/OFF<br>Brownout detection | Brownout detection | POR on VS | Brownout detection performed in PCU |
| VBAT_SENSE | ON/OFF | OFF | OFF | – |
| GPIO 5V (wake-up) | n.a. | Disabled/static | OFF | – |
| GPIO 5V (active) | ON | ON | OFF | – |
| WDT1 | ON | OFF | OFF | – |
| CYCLIC WAKE | n.a. | Cyclic wake-up/ cyclic sense/OFF | Cyclic wake-up/OFF | – |
| Measurement | ON[1)] | OFF | OFF | – |
| MCU | ON/slow-down/STOP | STOP[2)] | OFF | – |
| CLOCK GEN (MC) | ON | OFF | OFF | – |
| LP_CLK (18 MHz) | ON | OFF | OFF | WDT1 |
| LP_CLK2 (100 kHz) | ON/OFF | ON/OFF | ON/OFF | For cyclic wake-up |

1) May not be switched off due to safety reasons.

2) MC PLL clock disabled, MC supply reduced to $V_{DDCOUT\_Stop\_Red}$.

## Modes of operation

### Wake-up levels and transitions

The wake-up can be triggered by rising, falling, or both signal edges for the monitor input, GPIOs, by LIN, or by cyclic wake-up.

# 5 Power management unit (PMU)

## 5.1 Features

- System mode control (startup, sleep, stop and active)
- Power management (cyclic wake-up)
- Control of system voltage regulators with diagnosis (overload, short, overvoltage)
- Fail-safe mode detection and operation in case of system errors (watchdog fail)
- Wake-up sources configuration and management (LIN, MON, GPIOs)
- System error logging

## 5.2 Introduction

The power management unit is responsible for generating all required voltage supplies for the embedded MCU (VDDC, VDDP) and the external supply (VDDEXT). The power management unit is designed to ensure fail-safe behavior of the system IC by controlling all system modes, including the corresponding transitions. Additionally, the PMU provides well-defined sequences for the system mode transitions and generates hierarchical reset priorities. The reset priorities control the reset behavior of all system functions, especially the reset behavior of the embedded MCU. All these functions are controlled by a state machine. The system master function of the PMU uses an independent logic supply and system clock. For this reason, the PMU has an "Internal logic supply and system clock" module which works independently of the MCU clock.

### 5.2.1 Block diagram

The following figure shows the structure of the power management unit. **Table 4** describes the submodules in more detail.

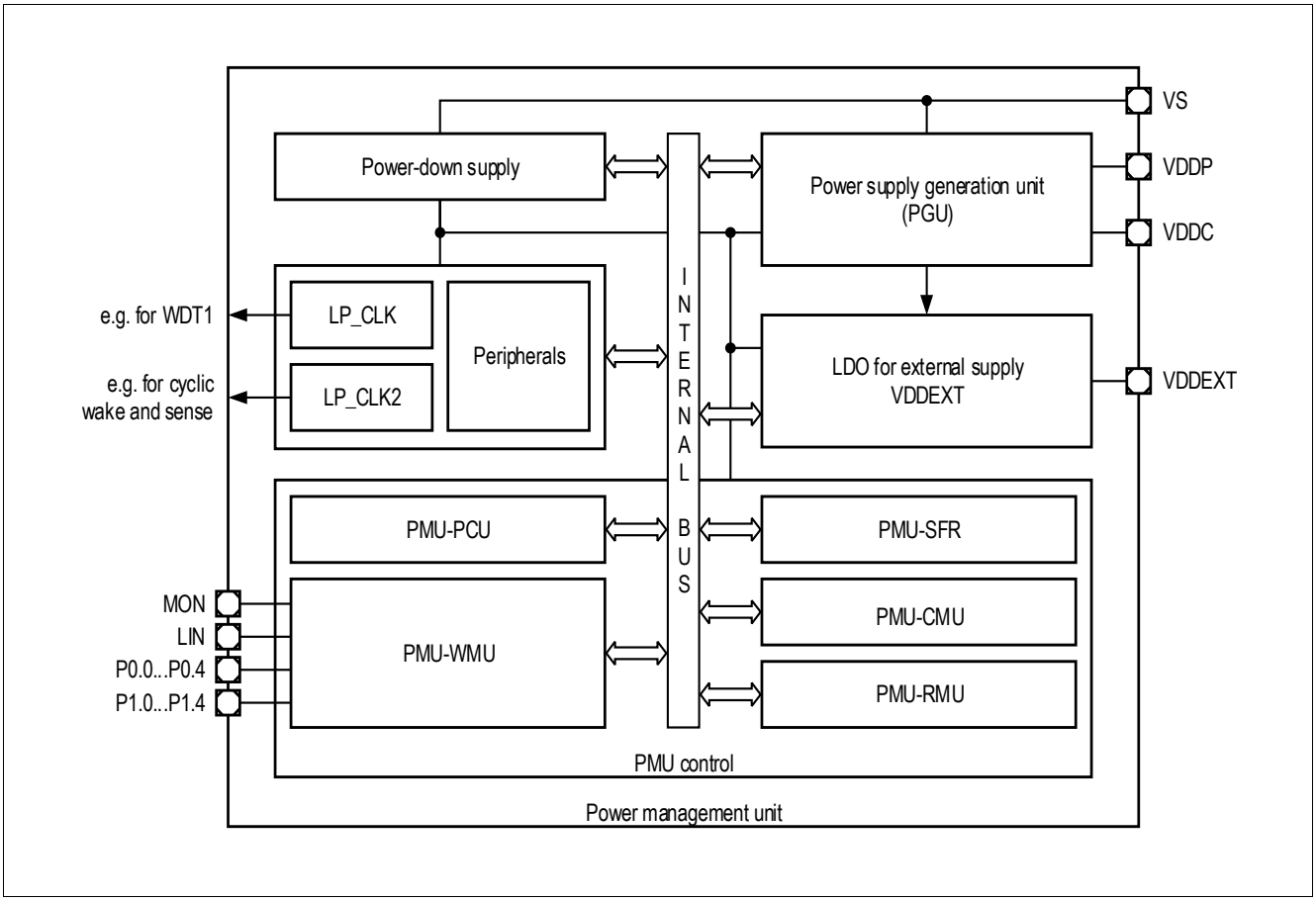


**Figure 3 Power management unit block diagram**

**Table 4 Description of PMU submodules**

| Module name | Modules | Functions |
|---|---|---|
| Power-down supply | Independent supply voltage generation for PMU. | This supply is dedicated to the PMU to ensure an operation independently of generated power supplies (VDDP, VDDC). |
| LP_CLK (18 MHz) | • Clock source for all PMU submodules.<br>• Backup clock source for the system.<br>• Clock source for WDT1. | This ultra-low-power oscillator generates the clock for the PMU.<br>This clock is also used as the backup clock for the system in case of PLL clock failures and as an independent clock source for WDT1. |
| LP_CLK2 (100 kHz) | Clock source for PMU. | This ultra-low-power oscillator generates the clock for the PMU in Stop mode and in the cyclic modes. |
| Peripherals | Peripheral blocks of PMU. | These blocks include the analog peripherals to ensure a stable and fail-safe PMU startup and operation (bandgap, bias). |

**Table 4 Description of PMU submodules** (cont'd)

| Module name | Modules | Functions |
|---|---|---|
| Power supply generation unit (PGU) | Voltage regulators for VDDP and VDDC. | This block includes the voltage regulators for the pad supply (VDDP) and the core supply (VDDC). |
| VDDEXT | Voltage regulator for VDDEXT to supply external modules (e.g., sensors). | This voltage regulator is a dedicated supply for external modules and can also be used for cyclic sense operations (e.g., with hall sensor). |
| PMU-SFR | All extended special function registers that are relevant to the PMU. | This module contains all registers needed to control and monitor the PMU. |
| PMU-PCU | Power control unit of the PMU. | This block is responsible for controlling all power-related actions within the PGU module. It also contains all regulator-related diagnostics such as undervoltage and overvoltage detection as well as overcurrent and short-circuit diagnostics. |
| PMU-WMU | Wake-up management unit of the PMU. | This block is responsible for controlling all actions related to wake-up within the PMU module. |
| PMU-CMU | Cyclic management unit of the PMU. | This block is responsible for controlling all actions in cyclic mode. |
| PMU-RMU | Reset management unit of the PMU. | This block generates resets triggered by the PMU, such as undervoltage or short-circuit reset, and passes all resets to the relevant modules and their registers. |

### 5.2.2 PMU modes overview

The following state diagram shows the available modes of the device.

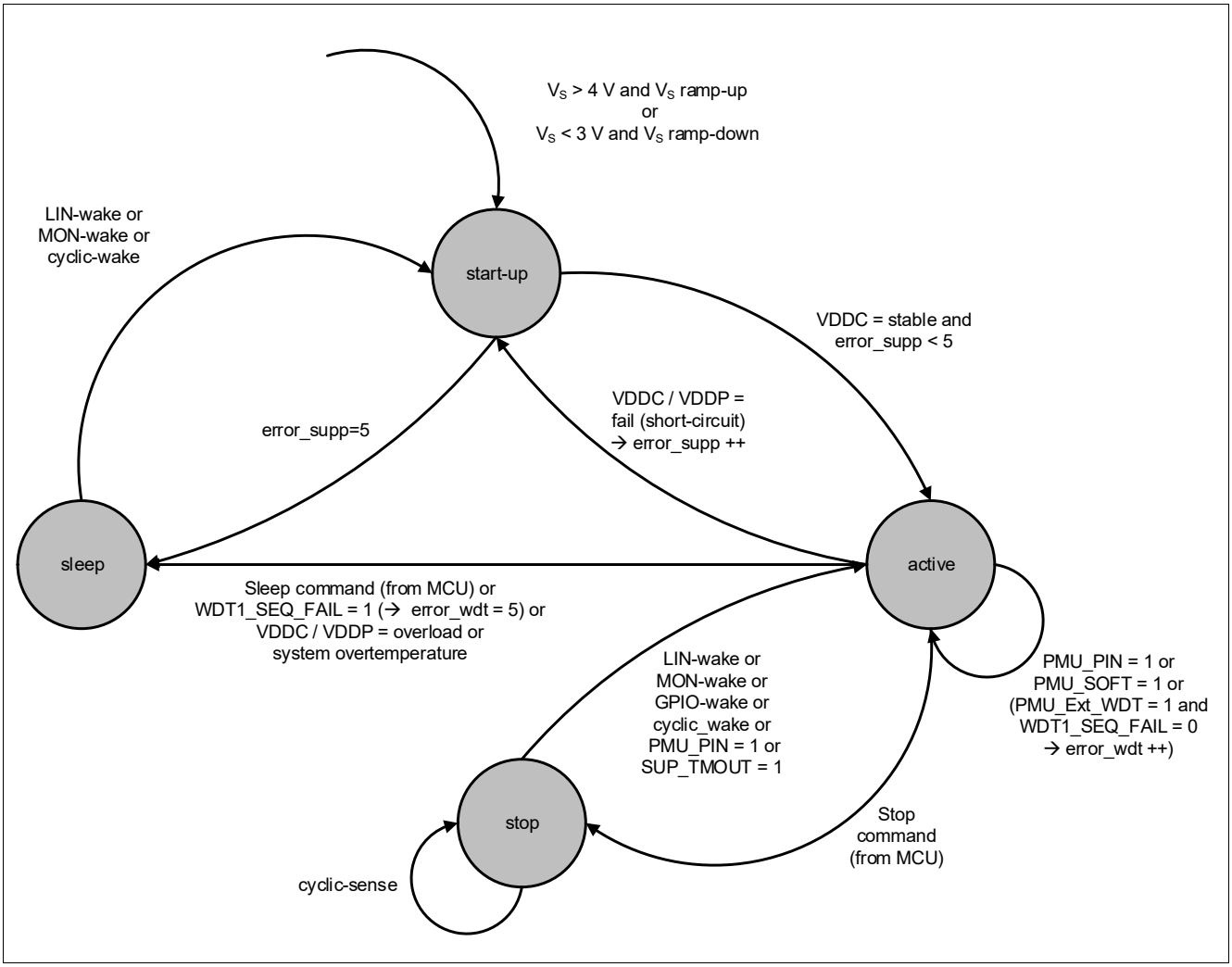


**Figure 4 Power management unit system modes**

## 5.3 Power supply generation unit (PGU)

### 5.3.1 Voltage regulator 5.0 V (VDDP)

This module represents the 5 V voltage regulator, which provides the pad supply for the parallel port pins and other 5 V analog functions (e.g. LIN transceiver).

**Features**

- 5 V low-drop voltage regulator
- Overcurrent monitoring and shutdown with MCU signaling (interrupt)
- Overvoltage monitoring with MCU signaling (interrupt)
- Undervoltage monitoring with MCU signaling (interrupt)
- Undervoltage monitoring with reset (undervoltage reset, $V_{DDPUV}$)
- Preregulator for the VDDC regulator
- GPIO supply
- Pull-down current source at the output for Sleep mode only (typ. 5 mA)

The output capacitor $C_{VDDP}$ is mandatory to ensure proper regulator functionality.

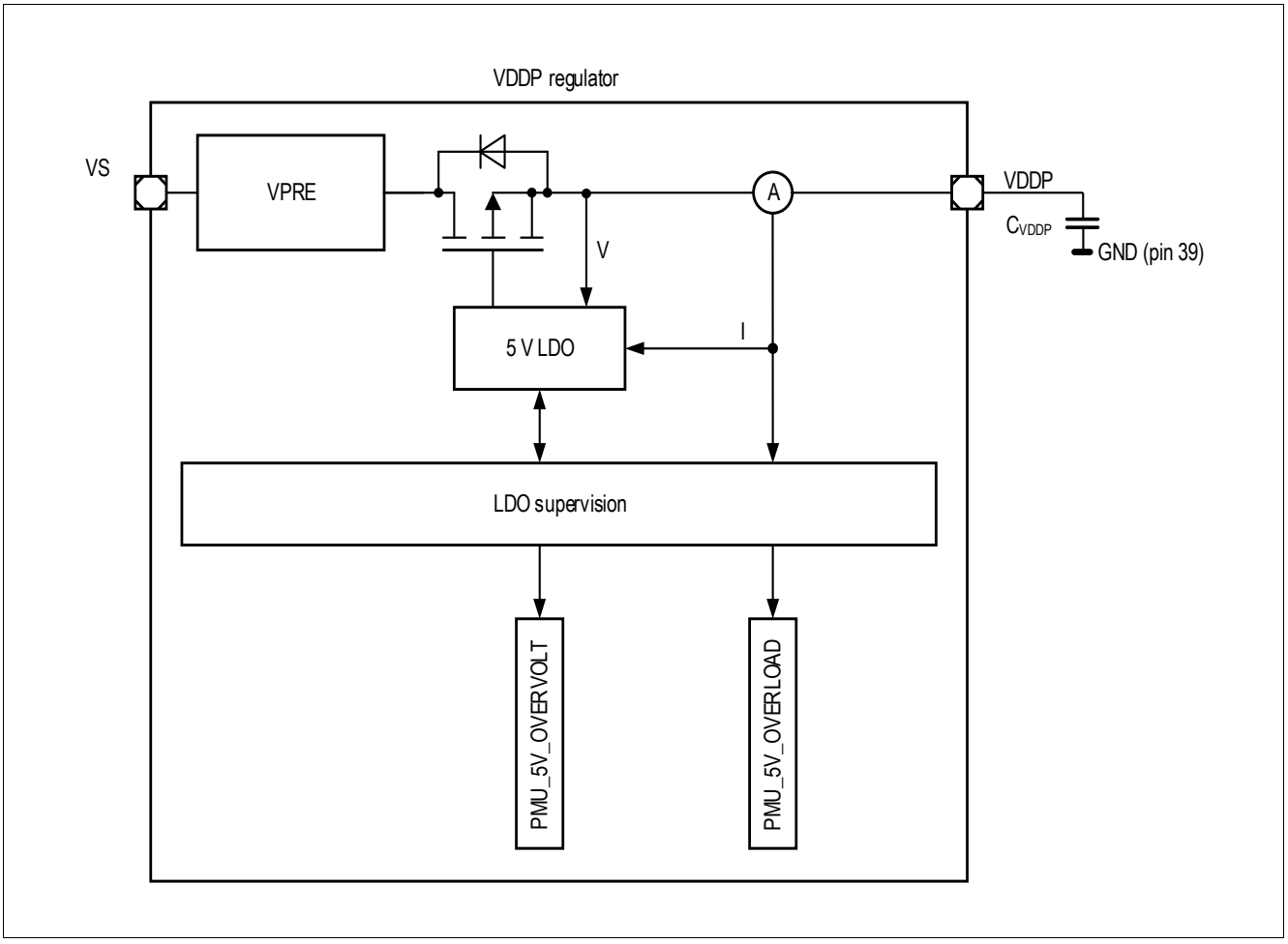


**Figure 5 Module block diagram of the VDDP voltage regulator**

### 5.3.2 Voltage regulator 1.5 V (VDDC)

This module represents the 1.5 V voltage regulator, which provides the supply for the microcontroller core, the digital peripherals, and other internal analog 1.5 V functions (e.g., ADC2) of the chip. To further reduce the current consumption of the MCU during Stop mode the output voltage can be lowered to $V_{DDCOUT\_Stop\_Red}$.

**Features**

- 1.5 V low-drop voltage regulator
- Overcurrent monitoring and shutdown with MCU signaling (interrupt)
- Overvoltage monitoring with MCU signaling (interrupt)
- Undervoltage monitoring with MCU signaling (interrupt)
- Undervoltage monitoring with reset
- Pull-down current source at the output for Sleep mode only (typ. 100 µA)

The output capacitor $C_{VDDC}$ is mandatory to ensure a proper regulator functionality.

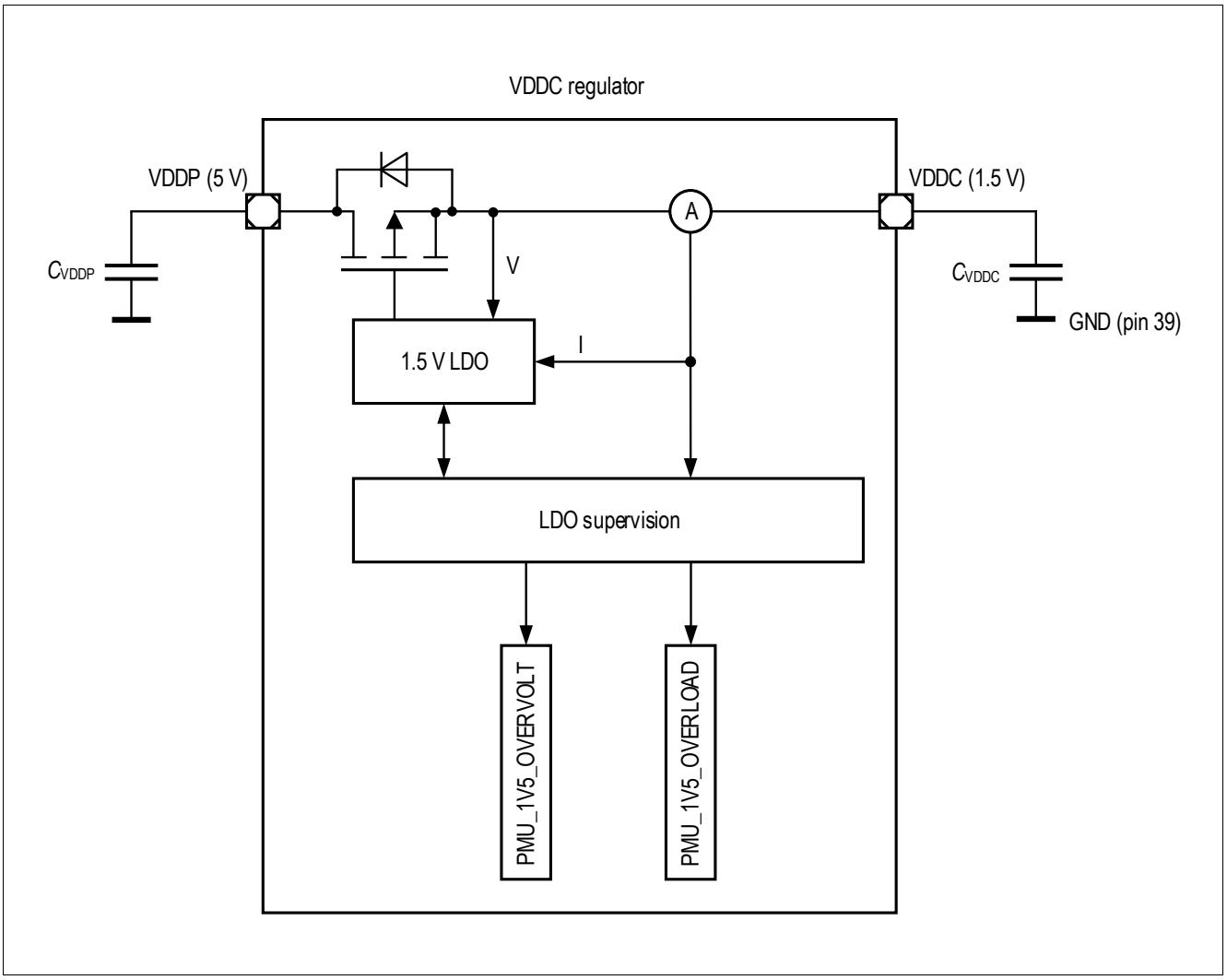


**Figure 6 Module block diagram of the VDDC voltage regulator**

### 5.3.3 External voltage regulator 5.0 V (VDDEXT)

This module represents the 5 V voltage regulator, which serves as a supply for external circuits. It can be used, e.g., to supply an external sensor, LEDs, or potentiometers.

**Features**

- Switchable +5 V, low-drop voltage regulator
- Switch-on overcurrent blanking time in order to drive small capacitive loads
- Overcurrent monitoring and shutdown with MCU signaling (interrupt)
- Overvoltage monitoring with MCU signaling (interrupt)
- Undervoltage monitoring with MCU signaling (interrupt)
- Pull-down current source at the output for Sleep mode only (typ. 100 µA)
- Cyclic sense option together with GPIOs

The output capacitor $C_{VDDEXT}$ is mandatory to ensure a proper regulator functionality.

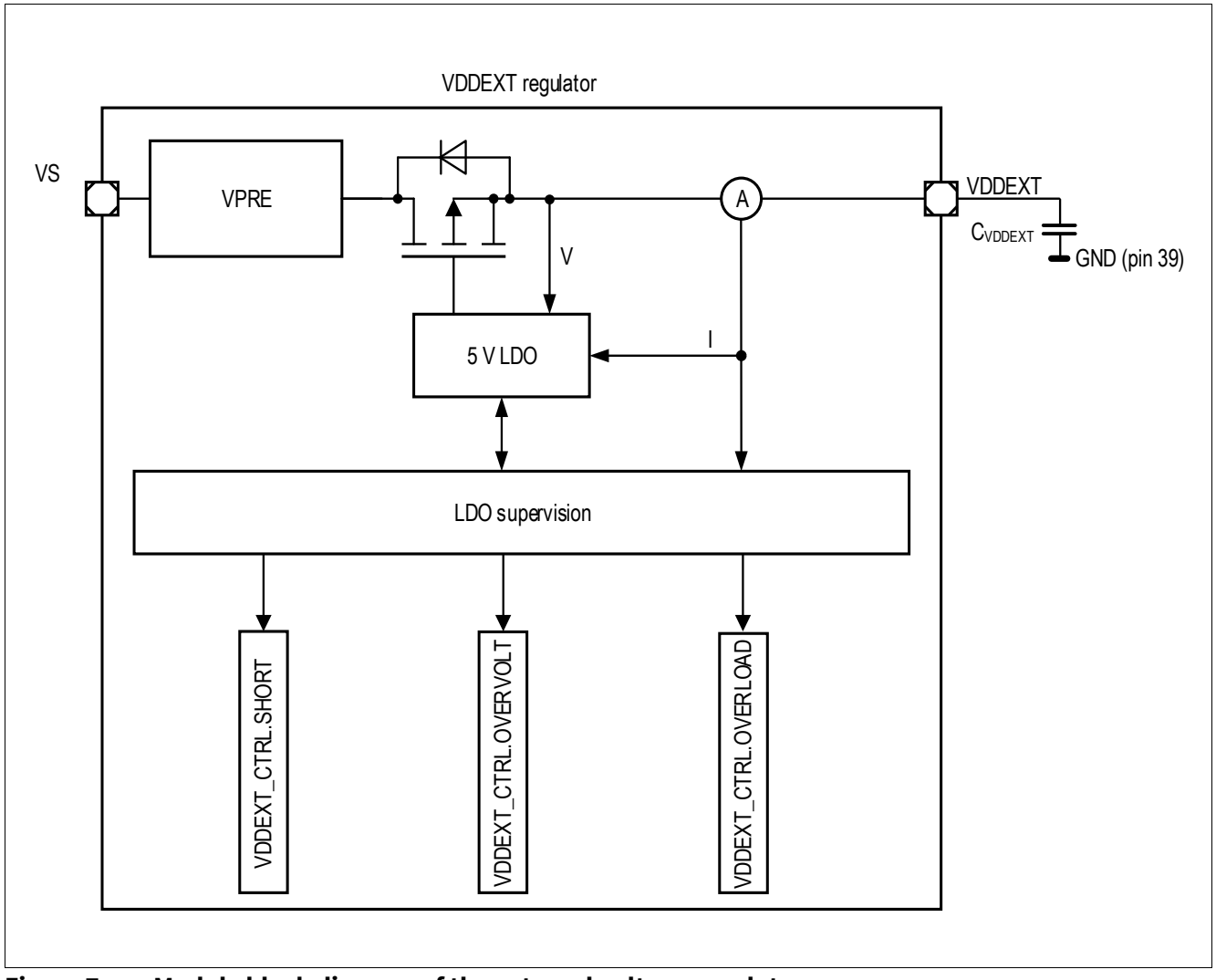


**Figure 7 Module block diagram of the external voltage regulator**

# 6 System control unit – digital modules (SCU-DM)

## 6.1 Features

- Flexible clock configuration features
- Reset management of all system resets
- System modes control for all power modes (Active mode, Stop mode, Sleep mode)
- Enabling interrupts for many system peripherals
- General-purpose input/output control
- Debug mode control of system peripherals

## 6.2 Introduction

The system control unit (SCU) supports all central control tasks in the TLE9862QXA40. The SCU is made up of the following submodules:

- Clock system and control
- Reset control
- Power management
- Interrupt management
- General port control
- Flexible peripheral management
- Module suspension control
- Watchdog timer
- Error detection and correction in data memory
- Miscellaneous control

### 6.2.1 Block diagram

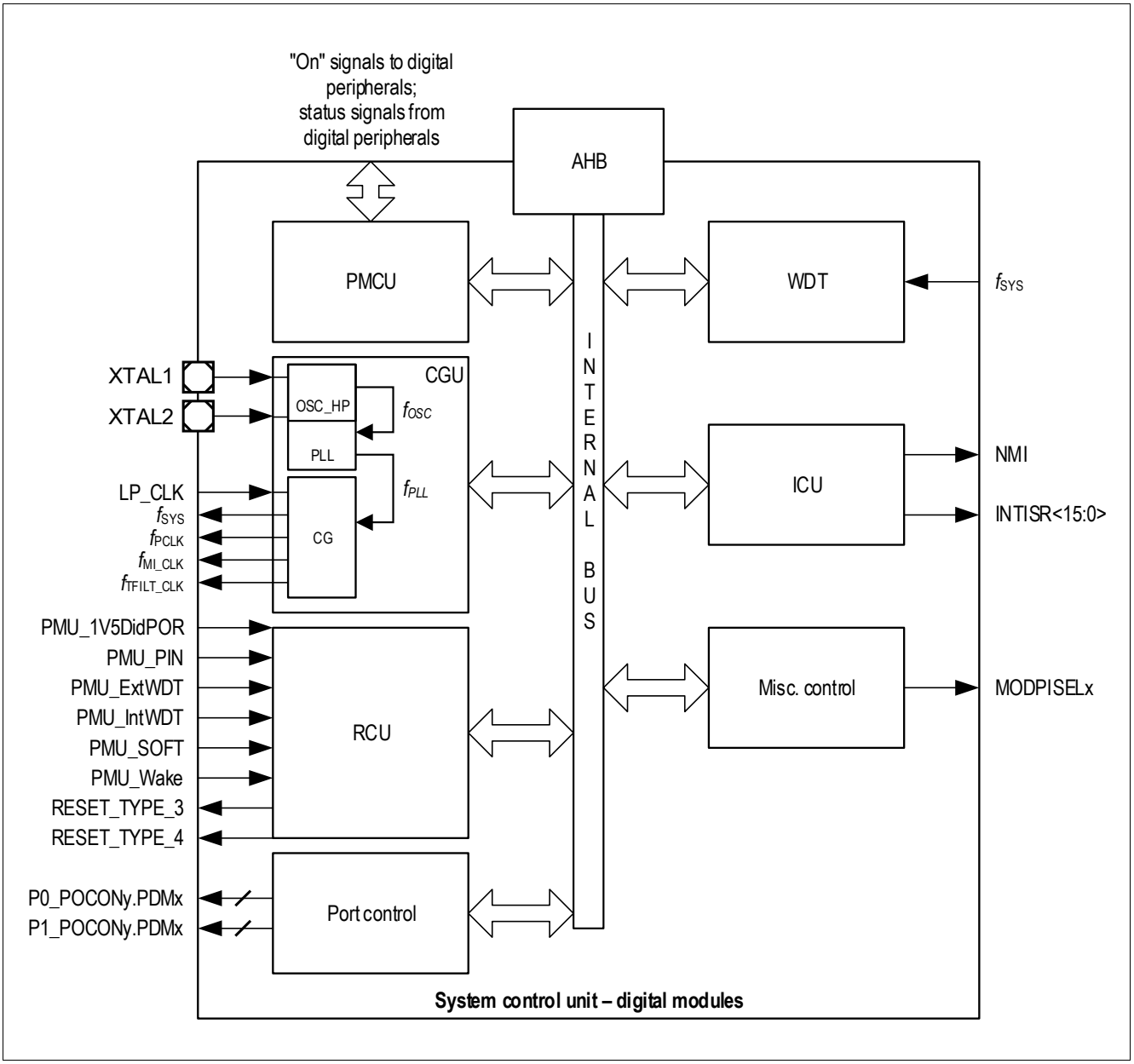


**Figure 8 System control unit – digital modules block diagram**

**AHB (Advanced High-Performance Bus)**

**PMCU (power module control unit)**

**WDT (watchdog timer in SCU-DM)**

- $f_{SYS}$: System clock

### System control unit – digital modules (SCU-DM)

#### CGU (clock generation unit)

- $f_{SYS}$: System clock
- $f_{PCLK}$: Peripheral clock
- $f_{MI\_CLK}$: Measurement interface clock
- $f_{TFILT\_CLK}$: Analog module filter clock
- LP_CLK Clock source for all PMU submodules and WDT1

#### ICU (interrupt control unit)

- NMI (non-maskable interrupt)
- INTISR<15,13:4,1,0> External interrupt signals

#### RCU (reset control unit)

- PMU_1V5DidPOR Undervoltage reset of power-down supply
- PMU_PIN Reset generated by reset pin
- PMU_ExtWDT WDT1 reset
- PMU_IntWDT WDT (SCU) reset
- PMU_SOFT Software reset
- PMU_Wake Sleep mode/Stop mode exit with reset
- RESET_TYPE_3 Peripheral reset (contains all resets)
- RESET_TYPE_4 Peripheral reset (without SOFT and WDT reset)

#### Port control

- P0_POCONy.PDMx Driver strength control
- P1_POCONy.PDMx Driver strength control

#### Miscellaneous control

- MODPISELx mode selection registers for UART (source section) and timer (trigger or count selection)

## 6.3 Clock generation unit

The clock generation unit (CGU) enables a flexible clock generation for the TLE9862QXA40. During user program execution, the frequency can be modified to optimize the performance/power consumption ratio, allowing power consumption to be adapted to the actual application state.

The CGU in the TLE9862QXA40 consists of one oscillator circuit (OSC_HP), a phase-locked loop (PLL) module with an internal oscillator (OSC_PLL), and a clock control unit (CCU). The CGU can convert a low-frequency input/external clock signal to a high-frequency internal clock.

The system clock $f_{SYS}$ is generated from one of the following selectable clocks:

- PLL clock output $f_{PLL}$
- Direct clock from oscillator OSC_HP $f_{OSC}$
- Low-precision clock $f_{LP\_CLK}$ (hardware-enabled for startup after reset and during power-down wake-up sequence)

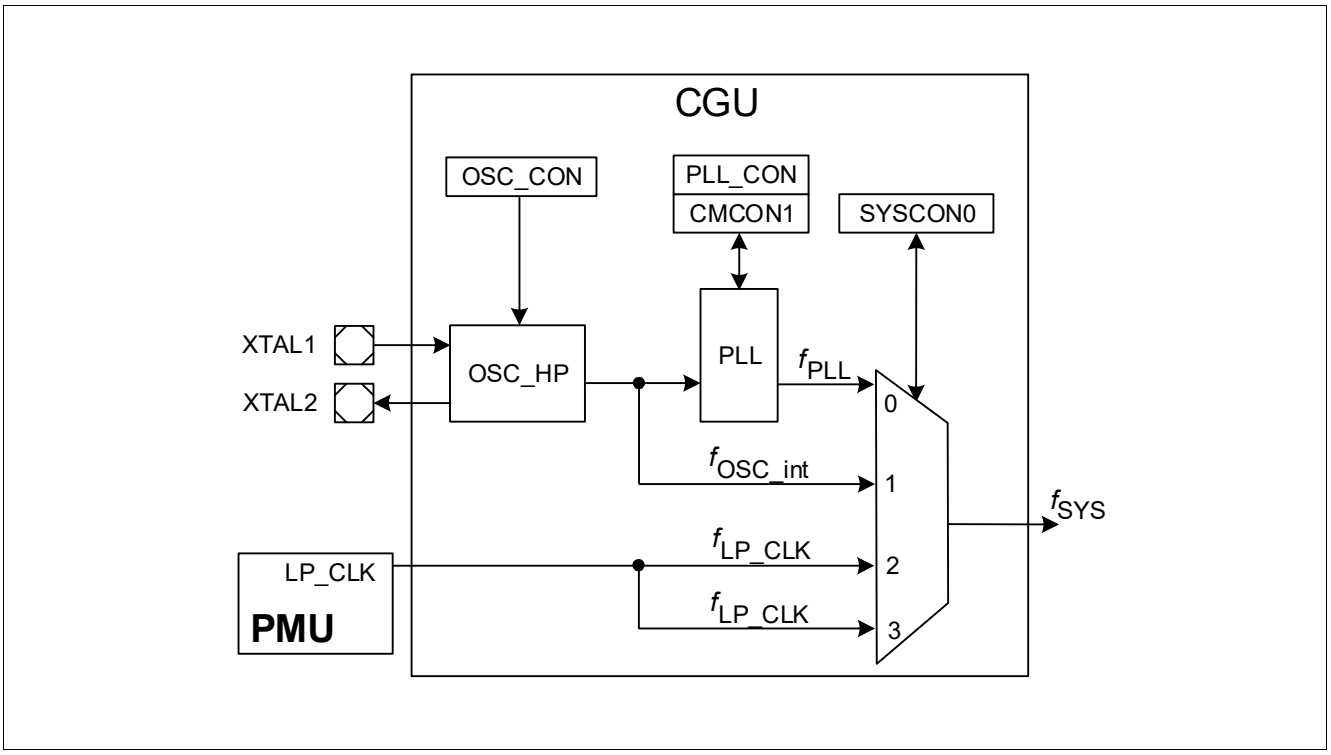


**Figure 9 Clock generation unit block diagram**

The following sections describe the different parts of the CGU.

### 6.3.1 Low-precision clock

The clock source LP_CLK is a low-precision RC oscillator (LP-OSC) with a nominal frequency of 18 MHz that is enabled by hardware as an independent clock source for the TLE9862QXA40 startup after reset and during the power-down wake-up sequence. $f_{LP\_CLK}$ is not user-configurable.

### 6.3.2 High-precision oscillator circuit (OSC_HP)

The high-precision oscillator circuit, designed to work with either an external crystal oscillator or an external stable clock source, consists of an inverting amplifier with XTAL1 as the input and XTAL2 as the output.

### 6.3.2.1 External input clock mode

When supplying the clock signal directly, not using an external crystal and bypassing the oscillator, the input frequency needs to be equal or greater than 4 MHz if the PLL VCO part is used.

When using an external clock signal, it must be connected to XTAL1. XTAL2 is left open (unconnected).

### 6.3.2.2 External crystal mode

When using an external crystal, its frequency can be within the range of 4 MHz to 25 MHz. An external oscillator load circuitry must be used, connected to the XTAL1 and XTAL2 pins. It normally consists of two load capacitances C1 and C2. A series damping resistor could be required for some crystals. The exact values and the corresponding operating ranges depend on the crystal and have to be determined and optimized in cooperation with the crystal vendor using the negative-resistance method. The following load cap values can be used as starting points for the evaluation:

**Table 5 External CAP capacitors**

| Fundamental mode crystal frequency (approx., MHz) | Load caps $C_1$, $C_2$ (pF) |
|---|---|
| 4 | 33 |
| 8 | 18 |
| 12 | 12 |
| 16 | 10 |
| 20 | 10 |
| 25 | 8 |

# 7 System control unit – power modules (SCU-PM)

## 7.1 Features

- Clock watchdog unit (CWU): Supervises all clocks with NMI signaling relevant to power modules.
- Interrupt control unit (ICU): All interrupt flags and status flags with system relevance.
- Power control unit (PCU): Takes over control when device enters and exits Sleep and Stop mode.
- External watchdog (WDT1): Independent system watchdog for monitoring system activity.

## 7.2 Introduction

### 7.2.1 Block diagram

The system control unit of the power modules consists of the submodules in the figure shown below:

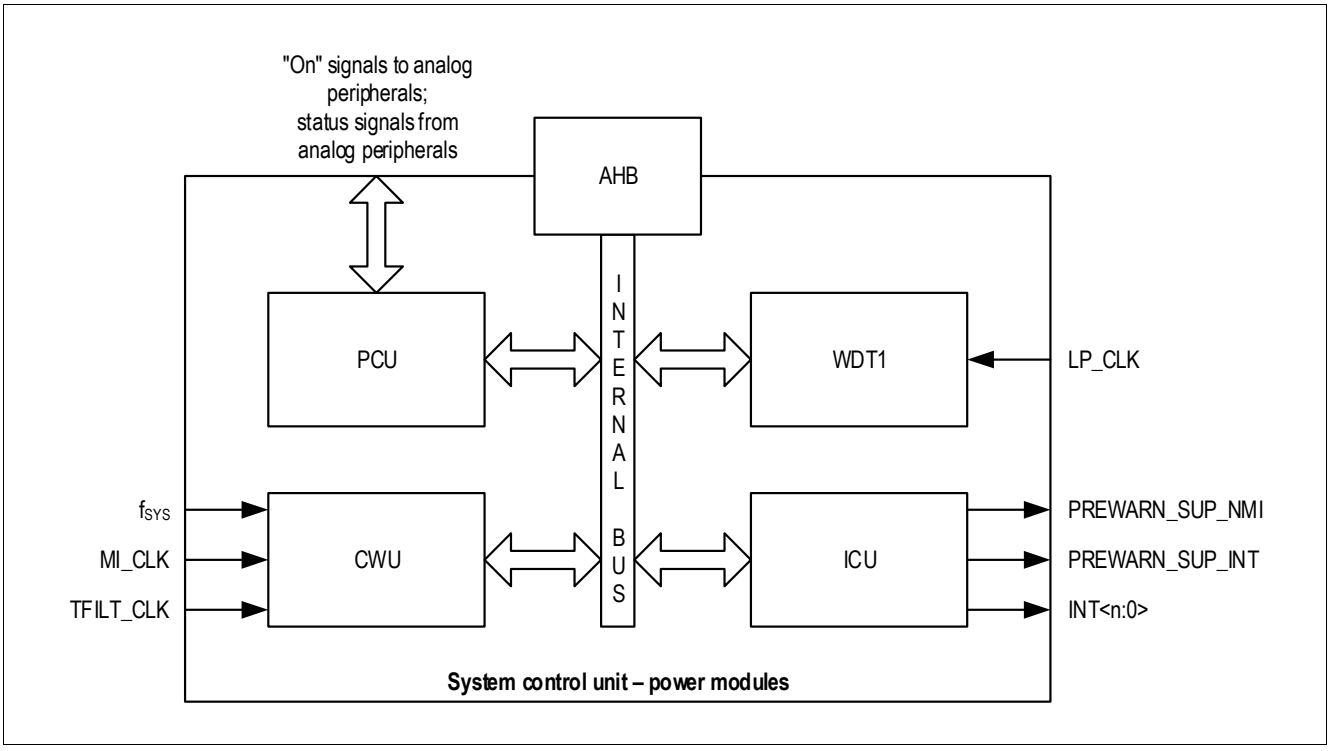


**Figure 10 Block diagram of system control unit – power modules**

**AHB (Advanced High-performance Bus)**

**CWU (clock watchdog unit)**

- $f_{sys}$: System frequency
- MI_CLK: Measurement interface clock (analog clock), derived from fsys using division factors 1/2/3/4
- TFILT_CLK: Clock used for digital filters, derived from $f_{sys}$ using configurable division factors

### WDT1 (system watchdog)

- LP_CLK Clock source for all PMU submodules and WDT1

### ICU (interrupt control unit)

- PREWARN_SUP_NMI Supply prewarning NMI request
- PREWARN_SUP_INT Supply prewarning interrupt
- Grouping of peripheral interrupts for external interupt nodes:
  - Grouping single peripheral interrupts for interrupt node INT<2> (measurement unit (MU))
  - Grouping single peripheral interrupts for interrupt node INT<3> (ADC1-VAREF)
  - Grouping single peripheral interrupts for interrupt node INT<10> (UART1-LIN transceiver)
  - Grouping single peripheral interrupts for interrupt node INT<14> (bridge driver)

# 8 Arm® Cortex®-M3 core

## 8.1 Features

The key features of the Arm® Cortex®-M3 implemented are listed below.

**Processor core: a low-gate-count core, with low-latency interrupt processing**

- A subset of the Thumb®-2 instruction set
- Banked stack pointer (SP) only
- 32-bit hardware divide instructions, SDIV and UDIV (Thumb-2 instructions)
- Handler and thread modes
- Thumb and debug states
- Interruptible-continued instructions LDM/STM, push/pop for low interrupt latency
- Automatic processor state saving and restoration for low-latency interrupt service routine (ISR) entry and exit
- Arm® architecture v7-M Style BE8/LE support
- Arm®v6 unaligned accesses

**Nested vectored interrupt controller (NVIC) closely integrated with the processor core to achieve low latency interrupt processing**

- Interrupts, configurable from 1 to 16
- Bits of priority (4)
- Dynamic reprioritization of interrupts
- Priority grouping. This enables selection of preemptive interrupt levels and non-preemptive interrupt levels.
- Support for tail-chaining and late arrival of interrupts. This enables back-to-back interrupt processing without the overhead of state-saving and restoration between interrupts.
- Processor state automatically saved on interrupt entry, and restored on interrupt exit, with no instruction overhead.

**Bus interfaces**

- Advanced High-performance Bus-Lite (AHB-Lite) interfaces: ICode, DCode, and system bus interface
- Memory access alignment
- Write buffer for buffering of write data

## 8.2 Introduction

The Arm® Cortex®-M3 processor is a leading 32-bit processor and provides a high-performance and cost-optimized platform for a broad range of applications including microcontrollers, automotive body systems and industrial control systems. Like the other Arm® Cortex® family processors, the Arm® Cortex®-M3 processor implements the Thumb®-2 instruction set architecture. With the optimized feature set the Arm® Cortex®-M3 delivers 32-bit performance in an application space that is usually associated with 8- and 16-bit microcontrollers.

### 8.2.1 Block diagram

**Figure 11** shows the functional blocks of the Arm® Cortex®-M3.

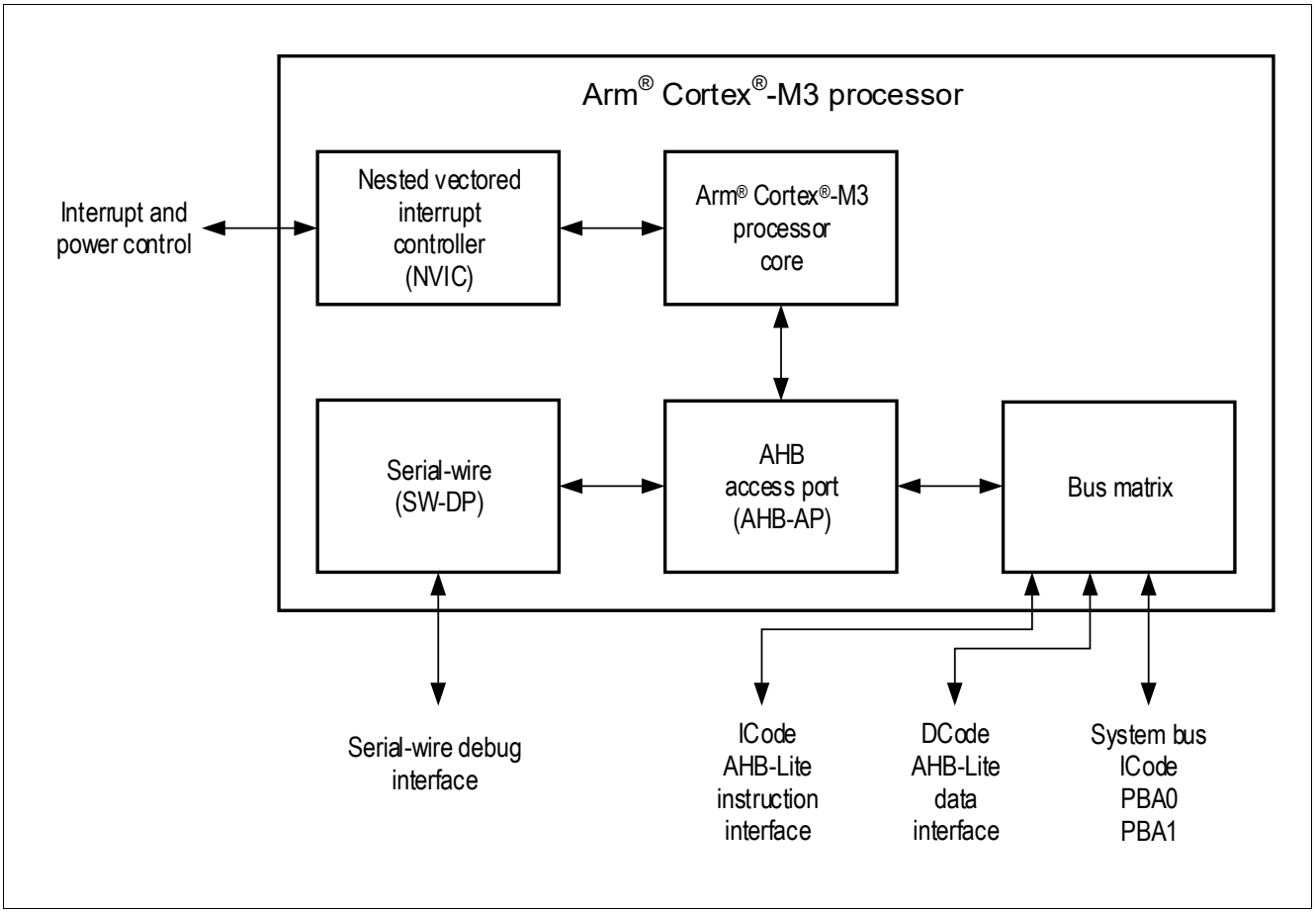


**Figure 11 Arm® Cortex®-M3 block diagram**

# 9 DMA controller

**Figure 12** shows the top level block diagram of the TLE9862QXA40.

The bus matrix allows the µDMA to access the PBA0, PBA1, and RAM.

## 9.1 Features

The principal features of the DMA Controller are:

- It is compatible with AHB-Lite for DMA transfers.
- It is compatible with APB for register programming.
- It has a single AHB-Lite master for transferring data using a 32-bit address bus and a 32-bit data bus.
- It supports 13 DMA channels.
- Each DMA channel has dedicated handshake signals.
- Each DMA channel has a programmable priority level.
- Each priority level arbitrates using a fixed priority that is determined by the DMA channel number. The DMA also supports multiple transfer types:
  - Memory-to-memory
  - Memory-to-peripheral
  - Peripheral-to-memory
- It supports multiple DMA cycle types.
- It supports multiple DMA transfer data widths.
- Each DMA channel can access a primary and an alternate channel control data structure.
- All the channel control data is stored in system memory (RAM) in little-endian format.
- It performs all DMA transfers using the single AHB-Lite burst type. The destination data width is equal to the source data width.
- The number of transfers in a single DMA cycle can be programmed from 1 to 1024.
- The transfer address increment can be greater than the data width.

## 9.2 Introduction

Please also refer to **Chapter 9.3**, **Functional description**.

### 9.2.1 Block diagram

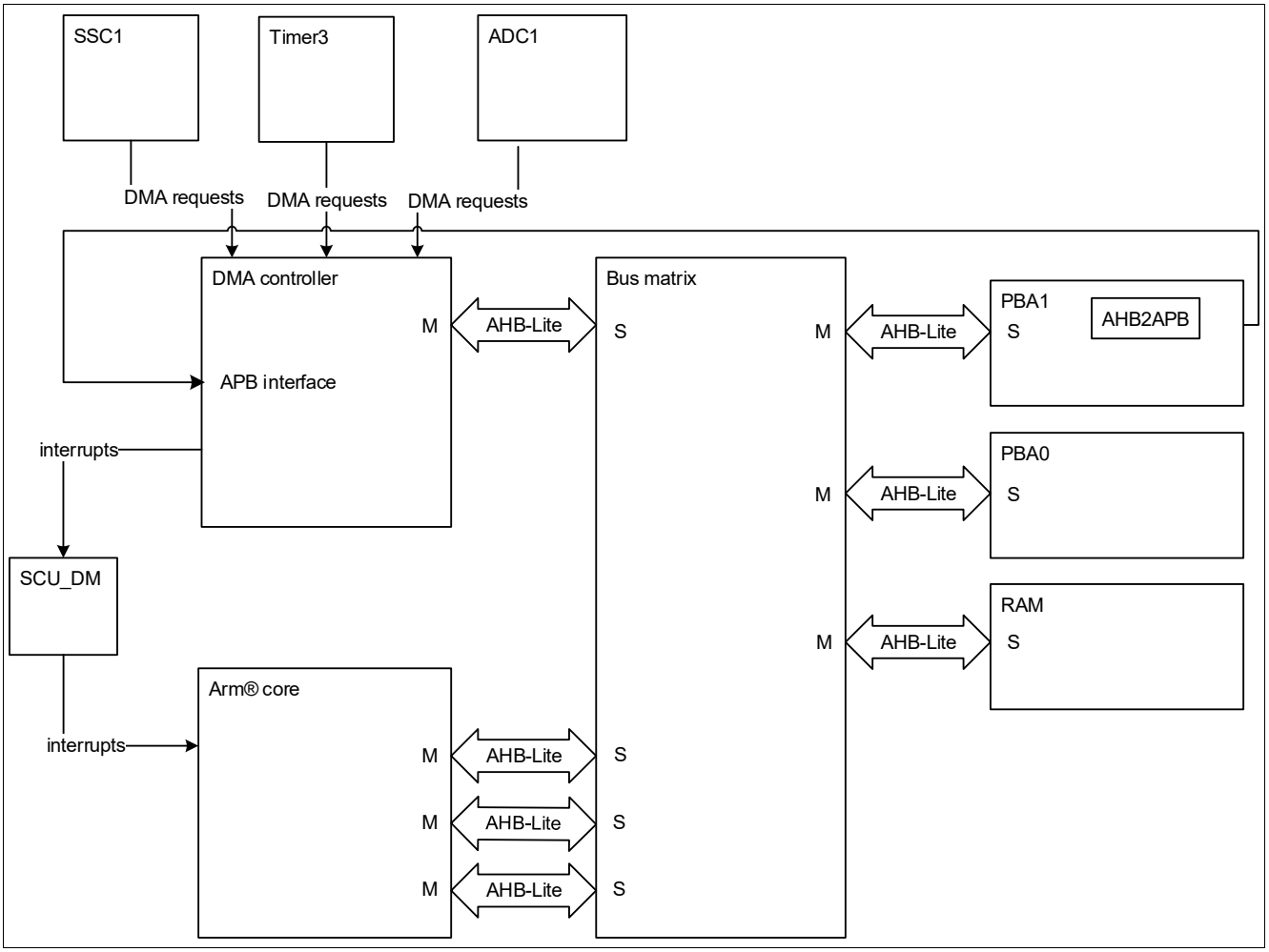


**Figure 12 DMA controller top level block diagram**

## 9.3 Functional description

### 9.3.1 DMA mode overview

The DMA controller implements the following 13 hardware DMA requests:

- ADC1 complete sequence 1 done: DMA transfer is requested on completion of the ADC1 channel conversion sequence.
- ADC1 exceptional sequence 2 (ESM) done: DMA transfer is requested on completion of the ADC1 conversion sequence triggered by an exceptional measurement request.
- SSC1/2 transmit byte: DMA transfer is requested upon the completion of data transmission via SSC1/2.
- SSC1/2: receive byte: DMA transfer is requested upon the completion of data reception via SSC1/2.
- ADC1 channel 0 conversion done: DMA transfer is requested on completion of the ADC1 channel 0 conversion.
- ADC1 channel 1 conversion done: DMA transfer is requested on completion of the ADC1 channel 1 conversion.
- ADC1 channel 2 conversion done: DMA transfer is requested on completion of the ADC1 channel 2 conversion.
- ADC1 channel 3 conversion done: DMA transfer is requested on completion of the ADC1 channel 3 conversion.
- ADC1 channel 4 conversion done: DMA transfer is requested on completion of the ADC1 channel 4 conversion.
- ADC1 channel 5 conversion done: DMA transfer is requested on completion of the ADC1 channel 5 conversion.
- ADC1 channel 6 conversion done: DMA transfer is requested on completion of the ADC1 channel 6 conversion.
- ADC1 channel 7 conversion done: DMA transfer is requested on completion of the ADC1 channel 7 conversion.
- Timer3 ccu6_int: DMA transfer is requested following a timer trigger.

# 10 Address space organization

The TLE9862QXA40 manipulates operands in the following memory spaces:

- 256 KB (incl. 4 KByte emulated EEPROM) of flash memory in code space
- 32 KB Boot ROM memory in code space (used for boot code and IP storage)
- 8 KB RAM memory in code space and data space (RAM can be read/written as program memory or external data memory)
- Special function registers (SFRs) in peripheral space

The figure below shows the detailed address alignment of the TLE9862QXA40:

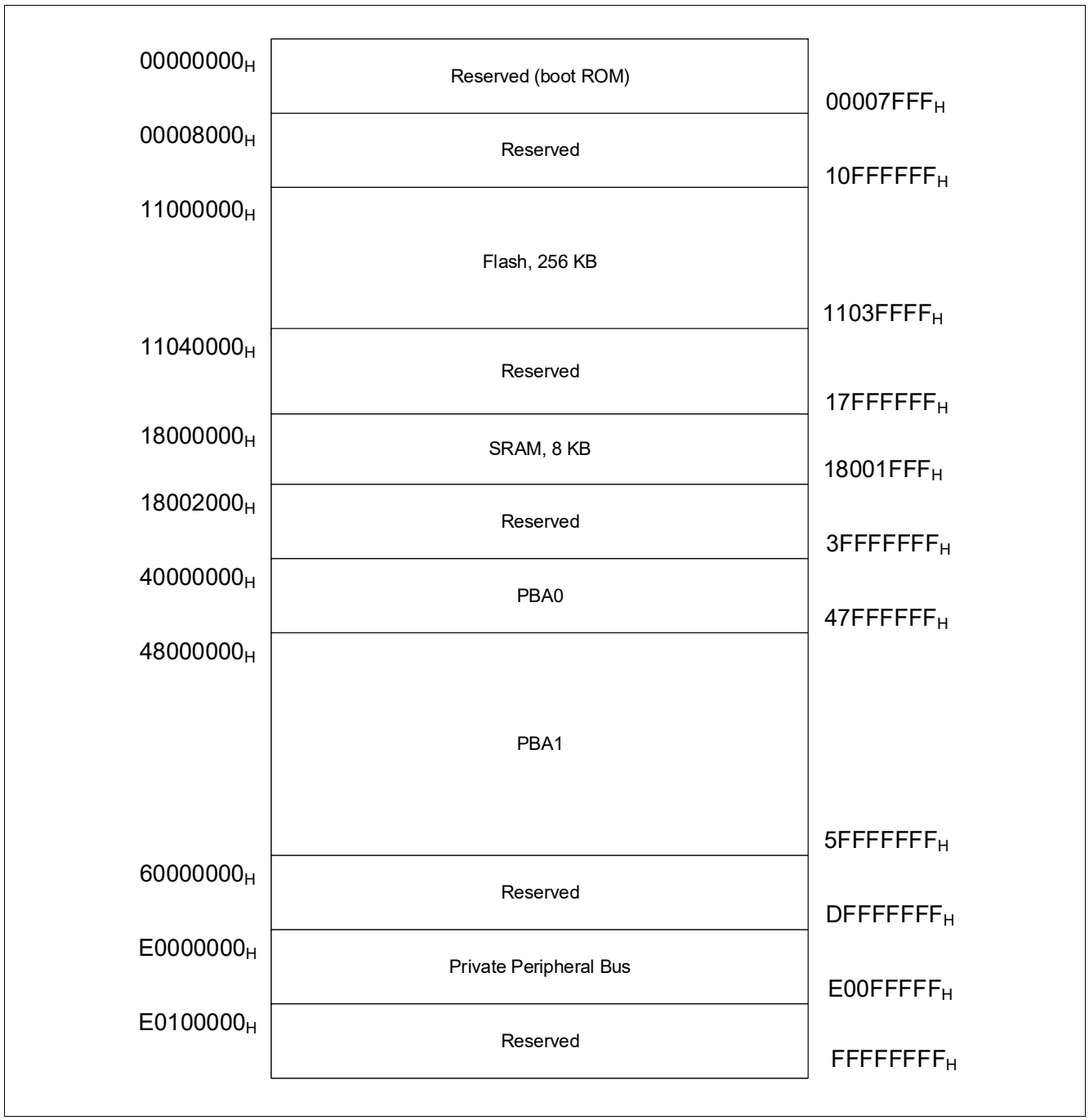


**Figure 13 Memory map**

# 11 Memory control unit

## 11.1 Features

- Handles all system memory types and their interaction with the CPU
- Memory protection functions for all system memory types (D-flash, P-flash, RAM)
- Address management with access violation detection including reporting
- Linear address range for all memory types (no paging)

## 11.2 Introduction

### 11.2.1 Block diagram

The memory control unit is divided into the following submodules:

- NVM memory module (embedded flash memory)
- RAM memory module
- BootROM memory module
- Memory protection unit (MPU) module
- Peripheral bridge PBA0

## Memory control unit

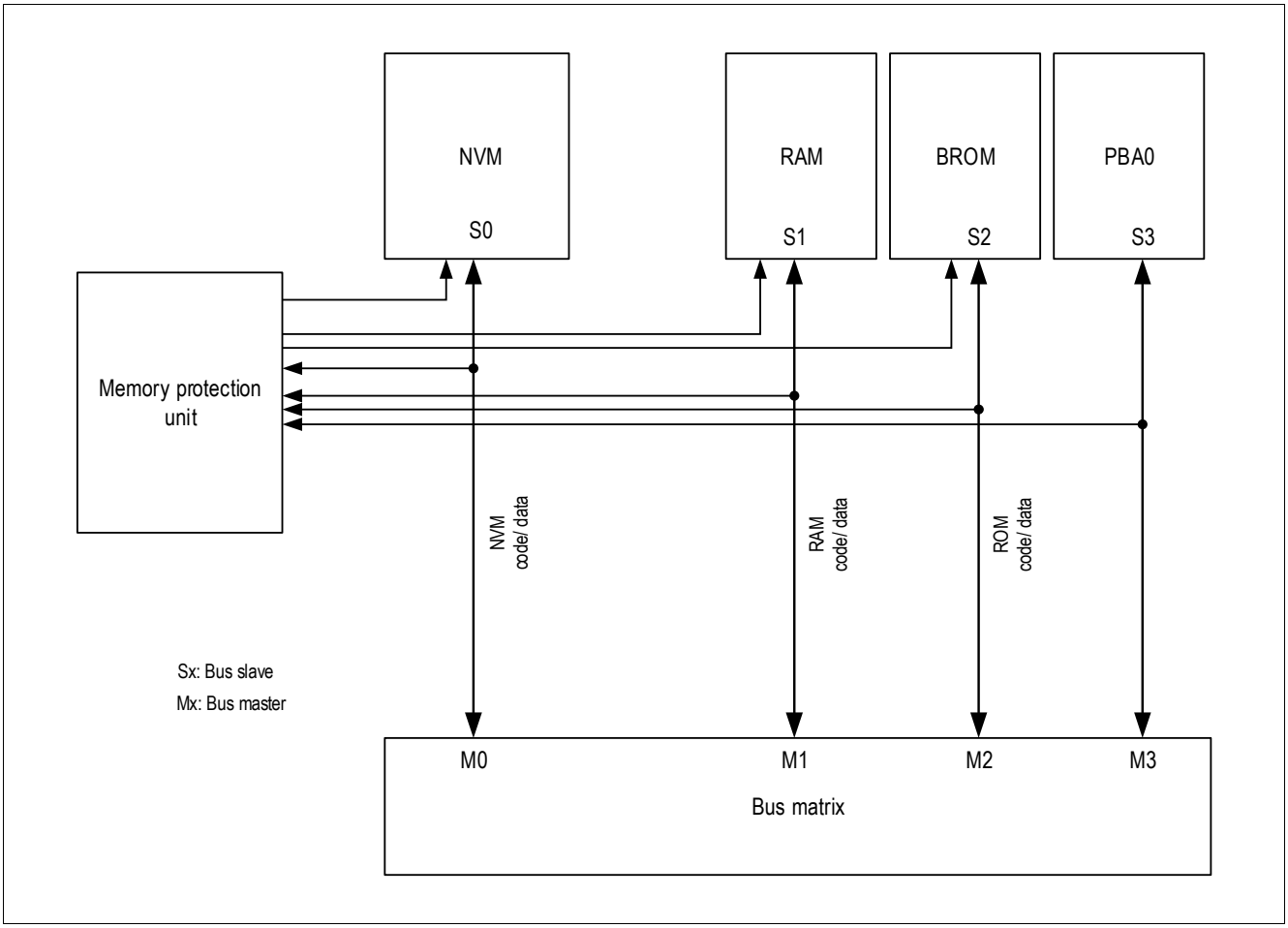


**Figure 14 Block diagram of the memory control unit**

## 11.3 NVM module (flash memory)

The flash memory provides embedded user-programmable non-volatile memory, allowing fast and reliable storage of user code and data.

**Features**

- In-system programming via LIN (flash mode) and SWD.
- Error correction code (ECC) for detection of single-bit and double-bit errors and dynamic correction of single-bit errors.
- Interrupts and signals double-bit errors by the NMI.
- Program width of 128 byte (page).
- Minimum erase width of 128 bytes (page).
- Integrated hardware support for EEPROM emulation.
- 8-byte read access.
- Physical read access time: 75 ns.
- Code-read access acceleration integrated; read buffer and automatic pre-fetch.
- Page-program time: $t_{PR}$ .
- Page-erase (128 bytes) and sector-erase (4 KB) time: $t_{ER}$.
- Erased bit (cell) is read as ‘1’, for code flash and 100TP.
- Erased bit (cell) is read as ‘0’ plus NMIMAP request, for data flash.

*Note: The user has to ensure that no flash operations which change the content of the flash get interrupted at any time.*

The clock for the NVM is supplied with the system frequency $f_{sys}$. Integrated firmware routines for erasing NVM, EEPROM emulation, and other operations are provided.

# 12 Interrupt system

## 12.1 Features

- Up to 16 interrupt nodes for on-chip peripherals
- Up to 8 NMI nodes for critical system events
- Maximum flexibility for all 16 interrupt nodes

## 12.2 Introduction

Before enabling an interrupt, all corresponding interrupt status flags must be cleared.

### 12.2.1 Overview

The TLE9862QXA40 supports 16 interrupt vectors with 16 priority levels. Fifteen of these interrupt vectors are assigned to the on-chip peripherals: GPT12, SSC, CCU6, DMA, bridge driver and A/D converter are each assigned to one dedicated interrupt vector; while UART1 and Timer2, as well as UART2, external interrupt 2 and Timer21 share interrupt vectors. Two vectors are dedicated for external interrupt 0 and 1.

**Table 6 Interrupt vector table**

| Service request | Node ID | Description |
|---|---|---|
| GPT12 | 0/1 | GPT interrupt (T2-T6, CAPIN) |
| MU-ADC2/T3 | 2 | Measurement unit, VBG, Timer3 |
| ADC1 | 3 | ADC1 interrupt / VREF5V overload / VREF5V OV/UV |
| CCU0 | 4 | CCU6 node 0 interrupt |
| CCU1 | 5 | CCU6 node 1 interrupt |
| CCU2 | 6 | CCU6 node 2 interrupt |
| CCU3 | 7 | CCU6 node 3 interrupt |
| SSC1 | 8 | SSC1 interrupt (receive, transmit, error) |
| SSC2 | 9 | SSC2 interrupt (receive, transmit, error) |
| UART1 | 10 | UART1 (ASC-LIN) interrupt (receive, transmit), Timer2, linsync1, LIN |
| UART2 | 11 | UART2 interrupt (receive, transmit), Timer21, external interrupt (EINT2) |
| EXINT0 | 12 | External interrupt (EINT0), MON |
| EXINT1 | 13 | External interrupt (EINT1) |
| BDRV/CP | 14 | Bridge driver / charge pump |
| DMA | 15 | DMA controller |

**Table 7 NMI interrupt table**

| Service request | Node | Description |
|---|---|---|
| Watchdog timer NMI | NMI | Watchdog timer overflow |
| PLL NMI | NMI | PLL loss-of-lock |
| NVM operation complete NMI | NMI | NVM operation complete |
| Overtemperature NMI | NMI | System overtemperature |
| Oscillator watchdog NMI | NMI | Oscillator watchdog / MI_CLK watchdog timer overflow |
| NVM map error NMI | NMI | NVM map error |
| ECC error NMI | NMI | RAM/NVM uncorrectable ECC error |
| Supply prewarning NMI | NMI | Supply prewarning |

# 13 Watchdog timer (WDT1)

## 13.1 Features

There are two watchdog timers in the system. The watchdog timer (WDT) within the system control unit – digital modules (see SCU_DM) and the Watchdog Timer (WDT1) located within the system control unit – power modules (see SCU_PM). The watchdog timer WDT1 is described in this section.

In Active mode, the WDT1 acts as a windowed watchdog timer, which provides a highly reliable and safe way to recover from software or hardware failures.

The WDT1 is always enabled in Active mode. In Sleep mode, Stop Mode and SWD mode (Debug mode), the WDT1 is automatically disabled.

**Functional Features**

- Windowed watchdog timer with programmable timing in Active mode.
- Long-open window (typ. 80 ms) after power-up, reset, wake-up.
- Short-open window (typ. 30 ms) to facilitate flash programming.
- Disabled during debugging.
- Safety shutdown to Sleep mode after 5 missed WDT1 services.

## 13.2 Introduction

The behavior of the watchdog timer in Active mode is illustrated in **Figure 15**.

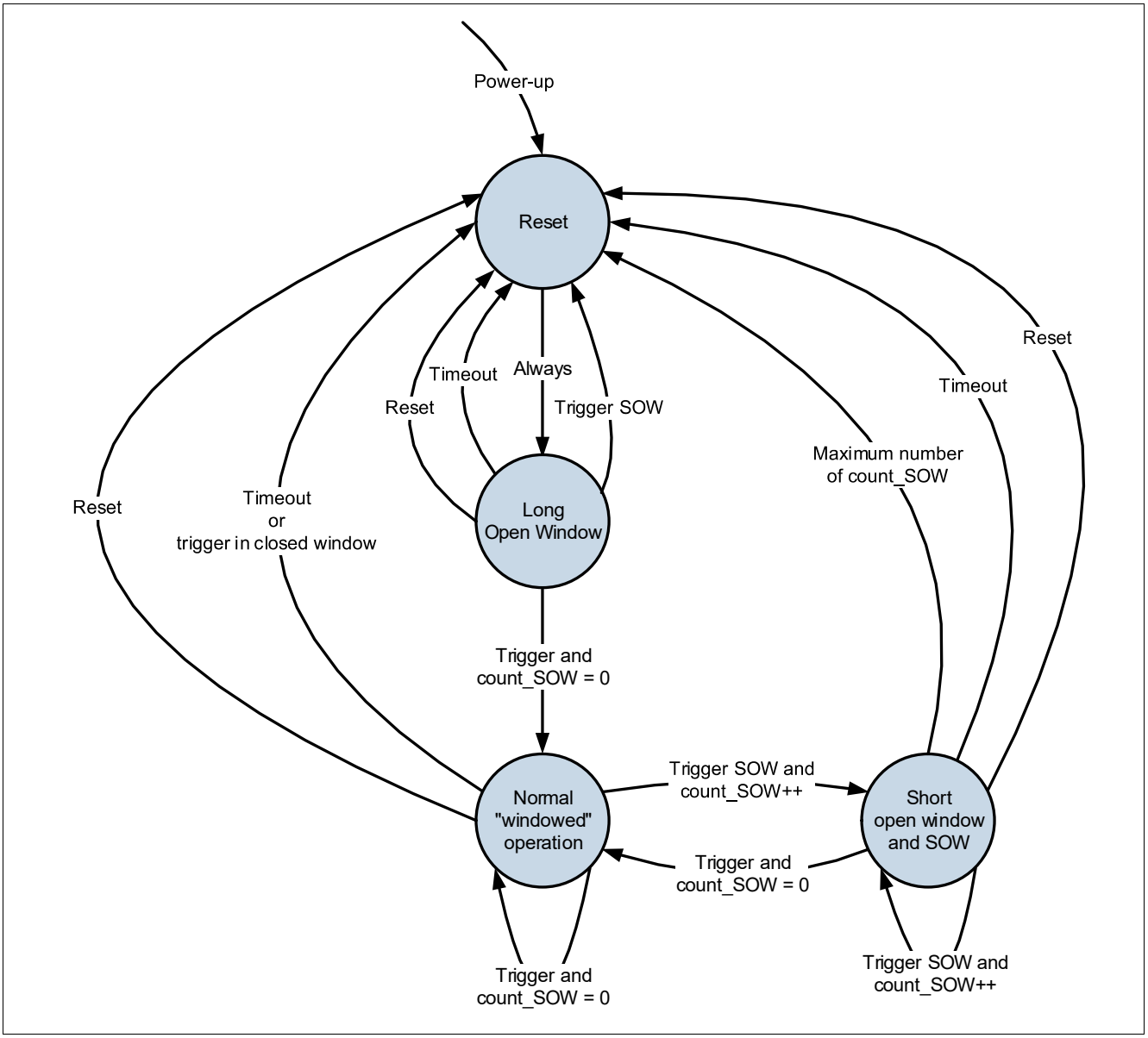


**Figure 15 Watchdog timer behavior**

# 14 GPIO ports and peripheral I/O

The TLE9862QXA40 has 15 port pins organized into three parallel ports: Port 0 (P0), port 1 (P1) and port 2 (P2). Each port pin has a pair of internal pull-up and pull-down devices that can be individually enabled or disabled. P0 and P1 are bidirectional and can be used as general-purpose input/output (GPIO) or to perform alternate input/output functions for the on-chip peripherals. For ports configured as an output, the open drain mode can be selected. On port 2 (P2), analog inputs are shared with general-purpose inputs.

## 14.1 Features

**Features of bidirectional ports (P0, P1)**

- Configurable pin direction
- Configurable pull-up/pull-down devices
- Configurable open-drain mode
- Configurable drive strength
- Transfer of data through digital inputs and outputs (general-purpose I/O)
- Alternate input/output for on-chip peripherals

**Features of the analog port (P2)**

- Configurable pull-up/pull-down devices
- Transfer of data through digital inputs
- Alternate inputs for on-chip peripherals

## 14.2 Introduction

### 14.2.1 Port 0 and port 1

**Figure 16** shows the block diagram of a TLE9862QXA40 bidirectional port pin. Each port pin is equipped with a number of control and data bits, thus enabling very flexible usage of the pin. By defining the contents of the control register, each individual pin can be configured as an input or an output. The user can also configure each pin as an open-drain pin with or without an internal pull-up/pull-down.

Each bidirectional port pin can be configured for input or output operation. Switching between input and output mode is accomplished through the register Px_DIR (x = 0 or 1), which enables or disables the output and input drivers. A port pin can only be configured as either input or output at any one time.

In input mode (default after reset), the output driver is switched off (high-impedance). The voltage level present at the port pin is translated into a logical 0 or 1 via a Schmitt trigger device and can be read via the register Px_DATA.

In output mode, the output driver is activated and drives the value supplied through the multiplexer to the port pin. In the output driver, each port line can be switched to open-drain mode or normal mode (push-pull mode) via the register Px_OD.

The output multiplexer in front of the output driver enables the port output function to be used for different purposes. If the pin is used for general-purpose output, the multiplexer is switched by software to the data register Px_DATA. Software can set or clear the bit in Px_DATA and therefore directly influence the state of the port pin. If an on-chip peripheral uses the pin for output signals, alternate output lines (AltDataOut) can be switched via the multiplexer to the output driver circuitry. Selection of the alternate output function is defined

in registers Px_ALTSEL0 and Px_ALTSEL1. When a port pin is used in an alternate function, its direction must be set accordingly in the register Px_DIR.

Each pin can also be programmed to activate an internal weak pull-up or pull-down device. Register Px_PUDSEL selects whether a pull-up or pull-down device is activated, while register Px_PUDEN enables or disables the pull device.

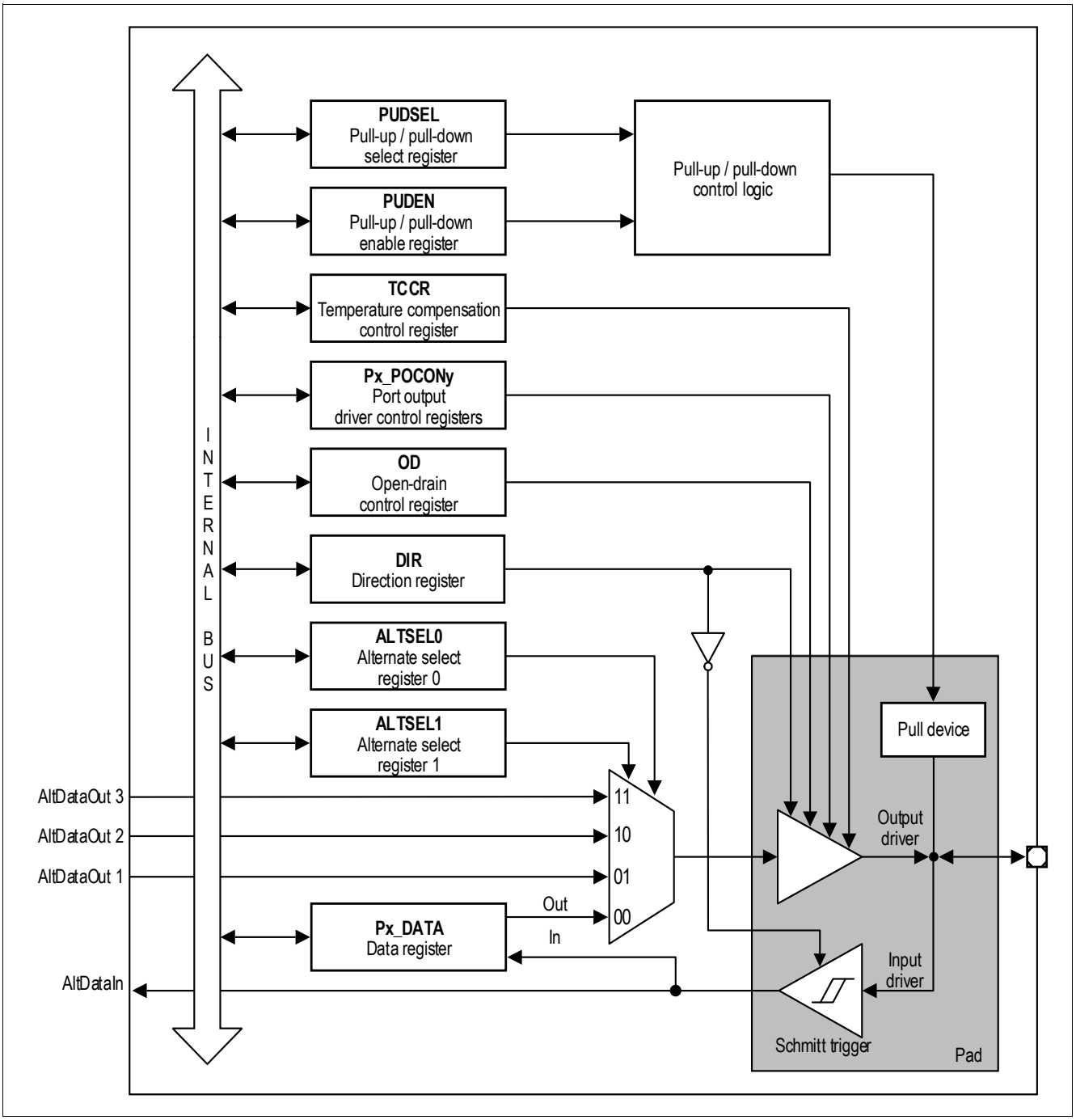


**Figure 16 General structure of a bidirectional port (P0, P1)**

### 14.2.2 Port 2

**Figure 17** shows the structure of an input-only port pin. Each P2 pin can only function in input mode. Register P2_DIR is provided to enable or disable the input driver. When the input driver is enabled, the actual voltage level present at the port pin is translated into a logic 0 or 1 via a Schmitt trigger device and can be read via register P2_DATA. Each pin can also be programmed to activate an internal weak pull-up or pull-down device. Register P2_PUDSEL selects whether a pull-up or the pull-down device is activated, while register P2_PUDEN enables or disables the pull device. The analog input (AnalogIn) bypasses the digital circuitry and Schmitt trigger device for direct feed-through to the ADC input channels.

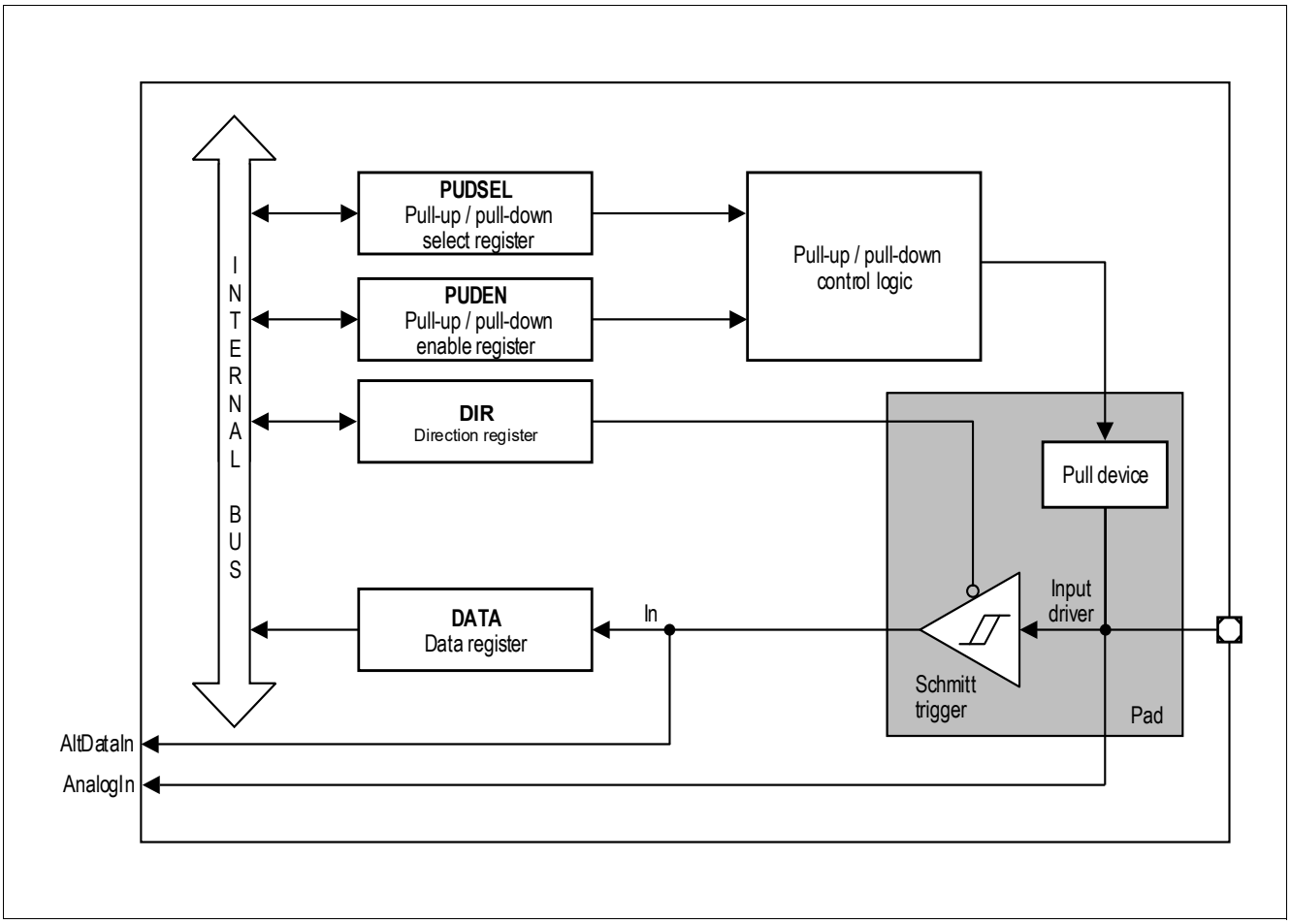


**Figure 17 General structure of input port (P2)**

## 14.3 TLE9862QXA40 port module

### 14.3.1 Port 0

#### 14.3.1.1 Port 0 functions

**Table 8 Port 0 input/output functions**

| Port pin | Input/output | Select | Connected signals | From/to module |
|---|---|---|---|---|
| P0.0 | Input | GPI | P0_DATA.P0 | – |
| | | INP1 | SWCLK / TCK_0 | SW |
| | | INP2 | T12HR_0 | CCU6 |
| | | INP3 | T4INA | GPT12T4 |
| | | INP4 | T2_0 | Timer2 |
| | | INP5 | – | – |
| | | INP6 | EXINT2_3 | SCU |
| | Output | GPO | P0_DATA.P0 | – |
| | | ALT1 | T3OUT | GPT12T3 |
| | | ALT2 | EXF21_0 | Timer 21 |
| | | ALT3 | RXDO_2 | UART2 |
| P0.1 | Input | GPI | P0_DATA.P1 | – |
| | | INP1 | T13HR_0 | CCU6 |
| | | INP2 | TxD1 | LIN_TxD |
| | | INP3 | CAPINA | GPT12CAP |
| | | INP4 | T21_0 | Timer21 |
| | | INP5 | T4INC | GPT12T4 |
| | | INP6 | MRST_1_2 | SSC1 |
| | | INP7 | EXINT0_2 | SCU |
| | Output | GPO | P0_DATA.P1 | – |
| | | ALT1 | TxD1 | UART1 / LIN_TxD |
| | | ALT2 | – | – |
| | | ALT3 | T6OUT | GPT12T6 |

**Table 8 Port 0 input/output functions** (cont'd)

| Port pin | Input/output | Select | Connected signals | From/to module |
|---|---|---|---|---|
| P0.2 | Input | GPI | P0_DATA.P2 | – |
| | | INP1 | CCPOS2_1 | CCU6 |
| | | INP2 | T2EUDA | GPT12T2 |
| | | INP3 | MTSR_1 | SSC1 |
| | | INP4 | T21EX_0 | Timer21 |
| | | INP5 | T6INA | GPT12T6 |
| | Output | GPO | P0_DATA.P2 | – |
| | | ALT1 | COUT60_0 | CCU6 |
| | | ALT2 | MTSR_1 | SSC1 |
| | | ALT3 | EXF2_0 | Timer2 |
| P0.3 | Input | GPI | P0_DATA.P3 | – |
| | | INP1 | SCK_1 | SSC1 |
| | | INP2 | CAPINB | GPT12 |
| | | INP3 | T5INA | GPT12T5 |
| | | INP4 | T4EUDA | GPT12T4 |
| | | INP5 | CCPOS0_1 | CCU6 |
| | Output | GPO | P0_DATA.P3 | – |
| | | ALT1 | SCK_1 | SSC1 |
| | | ALT2 | EXF21_2 | Timer21 |
| | | ALT3 | T6OUT | GPT12T6 |
| P0.4 | Input | GPI | P0_DATA.P4 | – |
| | | INP1 | MRST_1_0 | SSC1 |
| | | INP2 | CC60_0 | CCU6 |
| | | INP3 | T21_2 | Timer21 |
| | | INP4 | EXINT2_2 | SCU |
| | | INP5 | T3EUDA | GPT12T3 |
| | | INP6 | CCPOS1_1 | CCU6 |
| | Output | GPO | P0_DATA.P4 | – |
| | | ALT1 | MRST_1_0 | SSC1 |
| | | ALT2 | CC60_0 | CCU6 |
| | | ALT3 | CLKOUT_0 | SCU |

### 14.3.2 Port 1

#### 14.3.2.1 Port 1 functions

**Table 9 Port 1 input/output functions**

| Port pin | Input/output | Select | Connected signals | From/to module |
|---|---|---|---|---|
| P1.0 | Input | GPI | P1_DATA.P0 | – |
| | | INP1 | T3INC | GPT12T3 |
| | | INP2 | T4EUDB | GPT12T4 |
| | | INP3 | CC61_0 | CCU6 |
| | | INP4 | SCK_2 | SSC2 |
| | | INP5 | EXINT1_2 | SCU |
| | Output | GPO | P1_DATA.P0 | – |
| | | ALT1 | SCK_2 | SSC2 |
| | | ALT2 | CC61_0 | CCU6 |
| | | ALT3 | EXF21_3 | Timer21 |
| P1.1 | Input | GPI | P1_DATA.P1 | – |
| | | INP1 | – | – |
| | | INP2 | T6EUDA | GPT12T6 |
| | | INP3 | – | – |
| | | INP4 | MTSR_2 | SSC2 |
| | | INP5 | T21_1 | Timer21 |
| | | INP6 | EXINT1_0 | SCU |
| | Output | GPO | P1_DATA.P1 | – |
| | | ALT1 | MTSR_2 | SSC2 |
| | | ALT2 | COUT61_0 | CCU6 |
| | | ALT3 | TXD2_0 | UART2 |
| P1.2 | Input | GPI | P1_DATA.P2 | – |
| | | INP1 | T2INA | GPT12T2 |
| | | INP2 | T2EX_1 | Timer2 |
| | | INP3 | T21EX_3 | Timer21 |
| | | INP4 | MRST_2_0 | SSC2 |
| | | INP5 | RXD2_0 | UART2 |
| | | INP6 | CCPOS2_2 | CCU6 |
| | | INP7 | EXINT0_1 | SCU |
| | Output | GPO | P1_DATA.P2 | – |
| | | ALT1 | MRST_2_0 | SSC2 |
| | | ALT2 | COUT63_0 | CCU6 |
| | | ALT3 | T3OUT | GPT12T3 |

**Table 9 Port 1 input/output functions** (cont'd)

| Port pin | Input/output | Select | Connected signals | From/to module |
|---|---|---|---|---|
| P1.3 | Input | GPI | P1_DATA.P3 | – |
| | | INP1 | T6INB | GPT12T6 |
| | | INP2 | – | – |
| | | INP3 | CC62_0 | CCU6 |
| | | INP4 | T6EUDB | GPT12T6 |
| | | INP5 | – | – |
| | | INP6 | CCPOS0_2 | CCU6 |
| | | INP7 | EXINT1_1 | SCU |
| | Output | GPO | P1_DATA.P3 | – |
| | | ALT1 | EXF21_1 | Timer21 |
| | | ALT2 | CC62_0 | CCU6 |
| | | ALT3 | TXD2_1 | UART2 |
| P1.4 | Input | GPI | P1_DATA.P4 | – |
| | | INP1 | EXINT2_1 | SCU |
| | | INP2 | T21EX_1 | Timer21 |
| | | INP3 | T5EUDA | GPT12T5 |
| | | INP4 | RxD1 | UART1 |
| | | INP5 | T2INB | GPT12T2 |
| | | INP6 | CCPOS1_2 | CCU6 |
| | | INP7 | MRST_1_3 | SSC1 |
| | Output | GPO | P1_DATA.P4 | – |
| | | ALT1 | CLKOUT_1 | SCU |
| | | ALT2 | COUT62_0 | CCU6 |
| | | ALT3 | RxD1 | UART1 / LIN_RxD |

### 14.3.3 Port 2

#### 14.3.3.1 Port 2 functions

**Table 10 Port 2 input functions**

| Port pin | Input/output | Select | Connected signals | From/to module |
|---|---|---|---|---|
| P2.0 | Input | GPI | P2_DATA.P0 | – |
| | | INP1 | CCPOS0_3 | CCU6 |
| | | INP2 | - | – |
| | | INP3 | T12HR_2 | CCU6 |
| | | INP4 | EXINT0_0 | SCU |
| | | INP5 | CC61_2 | CCU6 |
| | | ANALOG | AN0 | ADC1 |
| | | | XTAL (in) | XTAL |
| P2.2 | Input | GPI | P2_DATA.P2 | – |
| | | INP1 | CCPOS2_3 | CCU6 |
| | | INP2 | T13HR_2 | CCU6 |
| | | INP3 | – | – |
| | | INP4 | CC62_2 | CCU6 |
| | | ANALOG | AN2 | ADC1 |
| | | OUT | XTAL (out) | XTAL |
| P2.3 | Input | GPI | P2_DATA.P3 | – |
| | | INP1 | CCPOS1_0 | CCU6 |
| | | INP2 | CTRAP#_1 | CCU6 |
| | | INP3 | T21EX_2 | Timer21 |
| | | INP4 | CC60_1 | CCU6 |
| | | INP5 | EXINT0_3 | SCU |
| | | ANALOG | AN3 | ADC1 |
| P2.4 | Input | GPI | P2_DATA.P4 | – |
| | | INP1 | $\overline{\text{CTRAP\#\_0}}$ | CCU6 |
| | | INP2 | T2EUDB | GPT12T2 |
| | | INP3 | MRST_1_1 | SSC1 |
| | | INP4 | EXINT1_3 | SCU |
| | | ANALOG | AN4 | ADC1 |

**Table 10 Port 2 input functions** (cont'd)

| Port pin | Input/output | Select | Connected signals | From/to module |
|---|---|---|---|---|
| P2.5 | Input | GPI | P2_DATA.P5 | – |
| | | INP1 | RXD2_1 | UART2 |
| | | INP2 | T3EUDB | GPT12T3 |
| | | INP3 | MRST_2_1 | SSC2 |
| | | INP4 | T2_1 | Timer 2 |
| | | ANALOG | AN5 | ADC1 |

# 15 General-purpose timer units (GPT12)

## 15.1 Features

### 15.1.1 Features of block GPT1

The following list summarizes the supported features:

- $f_{GPT}$ is derived from PCLK
- $f_{GPT}$/4 maximum resolution
- 3 independent timers/counters
- Timers/counters can be concatenated
- 4 Operating modes:
  - Timer mode
  - Gated Timer mode
  - Counter mode
  - Incremental Interface mode
- Reload and capture functionality
- Shared interrupt: node 0

### 15.1.2 Features of block GPT2

The following list summarizes the supported features:

- $f_{GPT}$ is derived from PCLK
- $f_{GPT}$/2 maximum resolution
- 2 independent timers/counters
- Timers/counters can be concatenated
- 3 Operating modes:
  - Timer mode
  - Gated Timer mode
  - Counter mode
- Extended capture/reload functions via 16-bit capture/reload register CAPREL
- Shared interrupt: node 1

## 15.2 Introduction

The general-purpose timer unit blocks GPT1 and GPT2 have very flexible multifunctional timer structures which may be used for timing, event counting, pulse-width measurement, pulse generation, frequency multiplication, and other purposes.

They incorporate five 16-bit timers that are grouped into the two timer blocks GPT1 and GPT2. Each timer in each block may operate independently in a number of different modes such as Gated Timer or Counter mode, or may be concatenated with another timer of the same block.

Each block has alternate input/output functions and specific interrupts associated with it. Input signals can be selected from several sources through the PISEL register.

The GPT module is clocked with clock $f_{GPT}$. $f_{GPT}$ is a clock derived from PCLK.

### 15.2.1 Block diagram of GPT1

**The GPT1 block** contains three timers/counters: The core timer T3 and the two auxiliary timers T2 and T4. The maximum resolution is $f_{GPT}/4$. The auxiliary timers of GPT1 may optionally be configured as reload or capture registers for the core timer.

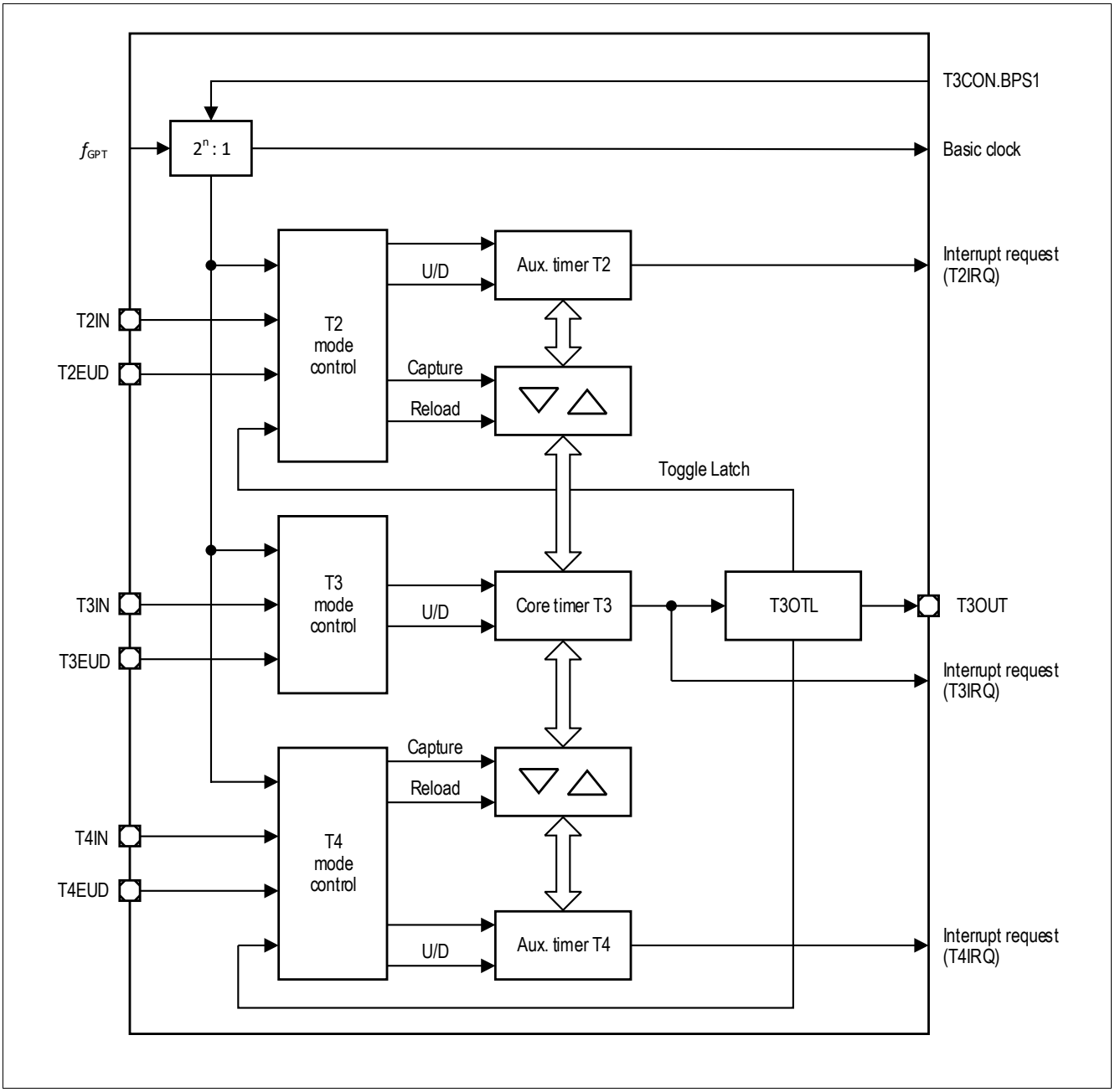


**Figure 18 GPT1 block diagram (n = 2 … 5)**

## 15.2.2 Block diagram of GPT2

**The GPT2 block** contains two timers/counters: The core timer T6 and the auxiliary timer T5. The maximum resolution is $f_{GPT}/2$. An additional capture/reload register (CAPREL) supports capture and reload operation with extended functionality.

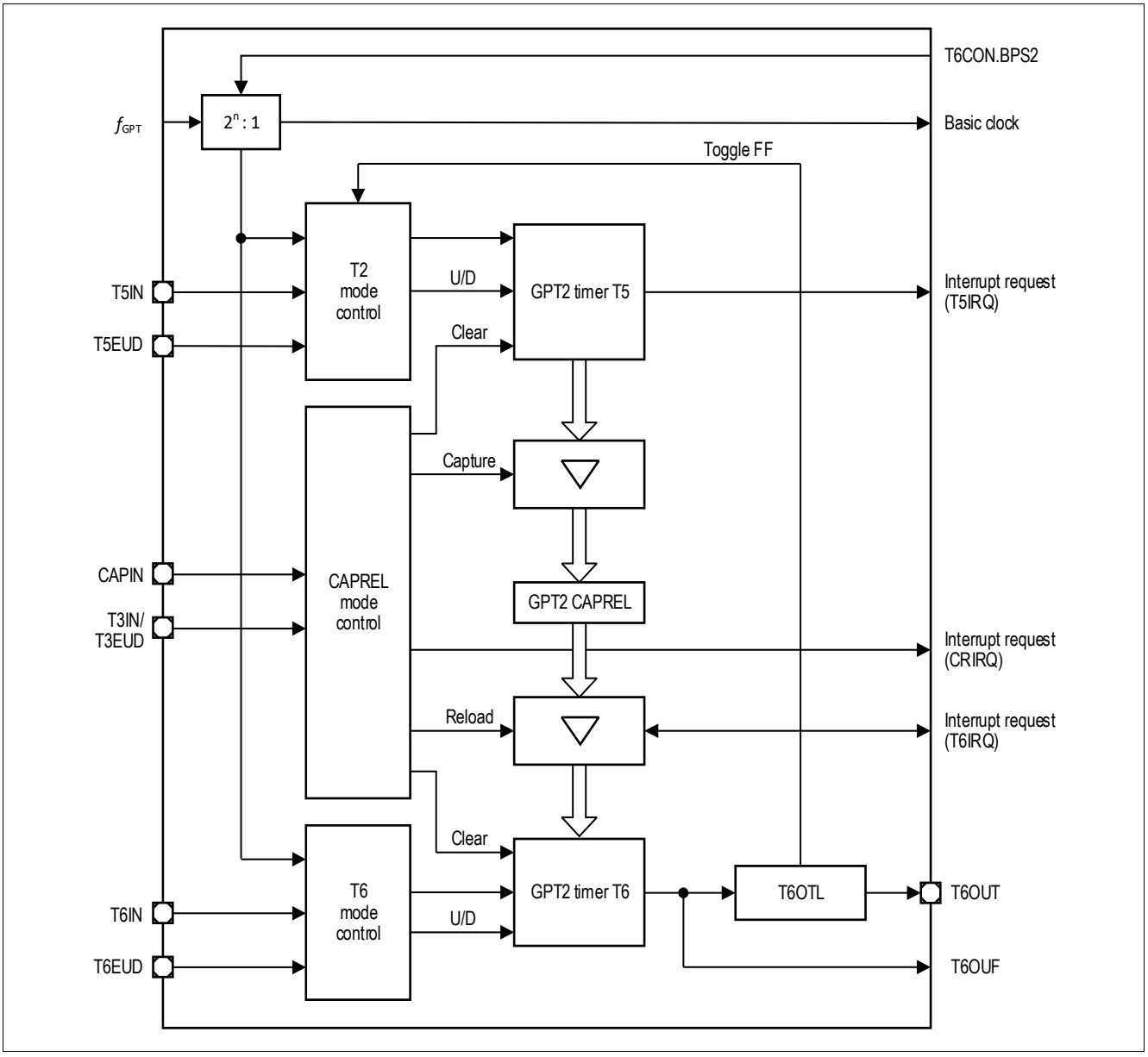


**Figure 19 GPT2 block diagram (n = 1 … 4)**

# 16 Timer2 and Timer21

## 16.1 Features

- 16-bit auto-reload mode
  - Selectable up- or down-counting
- One-channel 16-bit capture mode

## 16.2 Introduction

The timer modules are general-purpose 16-bit timers. Timer 2 and Timer 21 can function as timers or counters in each of their modes. As timers, they count with an input clock of $f_{PCLK}/12$ (if the prescaler is disabled). As a counter, Timer2 counts 1-to-0 transitions on pin T2. In the counter mode, the maximum resolution for counting is $f_{PCLK}/24$ (if the prescaler is disabled).

### 16.2.1 Timer2 and Timer21 mode overview

**Table 11 Timer2 and Timer21 modes**

| Mode | Description |
|---|---|
| **Auto-reload** | **Up/down-count-disabled**<br>• Counting up only.<br>• Counting starts from the 16-bit reload value, overflow at $FFFF_H$.<br>• The reload event can be configured to be triggered only by the overflow condition or by a negative or positive edge at the input pin T2EX as well.<br>• Programmable reload value in register RC2.<br>• Interrupt is generated with reload events. |

**Table 11 Timer2 and Timer21 modes** (cont'd)

| Mode | Description |
|---|---|
| **Auto-reload** | **Up/down-count-enabled**<br>• Counting up or down, direction determined by level at input pin T2EX.<br>• No interrupt is generated.<br>• Counting up<br>– Counting starts from the 16-bit reload value, overflow at $FFFF_H$.<br>– Reload event triggered by overflow condition.<br>– Programmable reload value in register RC2.<br>• Counting down<br>– Counting starts from $FFFF_H$, underflow at value defined in register RC2.<br>– Reload event triggered by underflow condition.<br>– Reload value fixed at $FFFF_H$. |
| **Channel capture** | • Counting up only.<br>• Counting starts from $0000_H$, overflow at $FFFF_H$.<br>• Reload event triggered by overflow condition.<br>• Reload value fixed at $0000_H$.<br>• Capture event triggered by falling/rising edge at pin T2EX.<br>• Captured timer value stored in register RC2.<br>• Reload or capture events generate interrupts. |

# 17 Timer3

## 17.1 Features

- 16-bit incremental timer/counter (counting up)
- Counting frequency up to $f_{sys}$
- Selectable clock prescaler
- Six operating modes
- Interrupt on overflow
- Interrupt on compare

## 17.2 Introduction

The possible applications for this timer include measuring the time interval between events, counting events, and generating a signal at regular intervals.

Timer3 can function as a timer or a counter. When functioning as a timer, Timer3 is incremented in periods based on the MI_CLK or LP_CLK clocks. When functioning as a counter, Timer3 is incremented in response to a 1-to-0 transition (falling edge) at its configured input. Timer3 can be configured in four different operating modes for a variety of applications (see **Table 12**).

The different operating modes allow the timer to be used for tasks such as:

- Simple measurements of the times between two events.
- Triggering the measuring unit upon PWM/CCU6 unit
- Measurement of the 100 kHz LP_CLK2

## 17.3 Functional description

Six modes of operation are provided to enable using this timer for various tasks. In every mode, the clocking source can be selected from MI_CLK and LP_CLK. In addition, a prescaler provides the capability to divide the selected clock source by 2, 4, or 8. The timer counts upwards, starting with the value in the timer count registers, up to the maximum count value, which depends on the selected mode of operation. Timer 3 provides two individual interrupts on counter overflow, one for the low-byte and one for the high-byte counter register.

### 17.3.1 Timer3 modes overview

The following table provides an overview of the timer modes together with the reasonable configuration options in **Table 12**.

**Table 12 Timer3 modes**

| Mode | Submode | Operation |
|---|---|---|
| **0** | **No submode** | **13-bit timer**<br>The timer essentially operates an 8-bit counter with a divide-by-32 prescaler. |
| **1** | **a** | **16-bit timer**<br>The timer registers, TL3 and TH3, are concatenated to form a 16-bit counter. |

**Table 12 Timer3 modes** (cont'd)

| Mode | Submode | Operation |
|---|---|---|
| **1** | **b** | **16-bit timer triggered by an event**<br>The timer registers, TL3 and TH3, are concatenated to form a 16-bit counter, which is triggered by an event to enable a single-shot measurement on a preset channel with the measurement unit. |
| **2** | **No submode** | **8-bit timer with auto-reload**<br>The timer register TL3 is reloaded with a user-defined 8-bit value in TH3 on overflow. |
| **3** | **a** | **Timer3 operating as two 8-bit timers**<br>The timer registers TL3 and TH3, operate as two separate 8-bit counters. |
| **3** | **b** | **Timer3 operating as two 8-bit timers for clock measurement**<br>The timer registers, TL3 and TH3, operate as two separate 8-bit counters. In this mode, the LP_CLK2 low power clock can be measured. TL3 acts as an edge counter for the clock edges and TH3 measures the interval between the edges. |

# 18 Capture/compare unit 6 (CCU6)

## 18.1 Feature set overview

This section gives an overview over the different building blocks and their main features.

**Timer 12 block features**

- Three capture/compare channels. Each channel can be used either as capture or as compare channel.
- Supports three-phase PWM (six outputs with separate signals for high-side and low-side switches).
- 16-bit resolution, maximum count frequency = peripheral clock.
- Dead-time control for each channel to avoid short-circuits in the power stage.
- Concurrent update of the T12 registers.
- Center-aligned and edge-aligned PWM can be generated.
- Single-shot mode is supported.
- Start can be controlled by external events.
- External events can be counted.
- Multiple interrupt request sources.
- Hysteresis-like control mode.

**Timer 13 block features**

- One independent compare channel with one output.
- 16-bit resolution, maximum count frequency = peripheral clock.
- Concurrent update of T13 registers.
- Can be synchronized to T12.
- Interrupt generation at period-match and compare-match.
- Single-shot mode is supported.
- Start can be controlled by external events.
- Capability of counting external events.

**Additional specific functions**

- Block commutation for brushless DC-drives implemented.
- Position detection via hall-sensor pattern.
- Noise filter for position input signals supported.
- Automatic rotational speed measurement and commutation control for block commutation.
- Integrated error handling.
- Fast emergency stop without CPU load via external signal ($\overline{\text{CTRAP}}$).
- Control modes for multi-channel AC drives.
- Output levels can be selected and adapted to the power stage.

## 18.2 Introduction

The CCU6 unit is made up of the T12 timer block with three capture/compare channels and the T13 timer block with one compare channel. The T12 channels can independently generate PWM signals or accept capture triggers, or they can jointly generate control signal patterns to drive DC motors or inverters.

A rich set of status bits, synchronized updating of parameter values via shadow registers, and flexible generation of interrupt request signals provide efficient software control.

*Note: The capture/compare module itself is referred to as CCU6 (capture/compare unit 6). A capture/compare channel inside this module is referred to as CC6x.*

The timer T12 can work in capture and/or compare mode for its three channels. The modes can also be combined (e.g., a channel works in compare mode, whereas another channel works in capture mode). The timer T13 can work only in compare mode. The multi-channel control unit generates output patterns which can be modulated by T12 and/or T13. The modulation sources can be selected and combined for modulating signals.

### 18.2.1 Block diagram

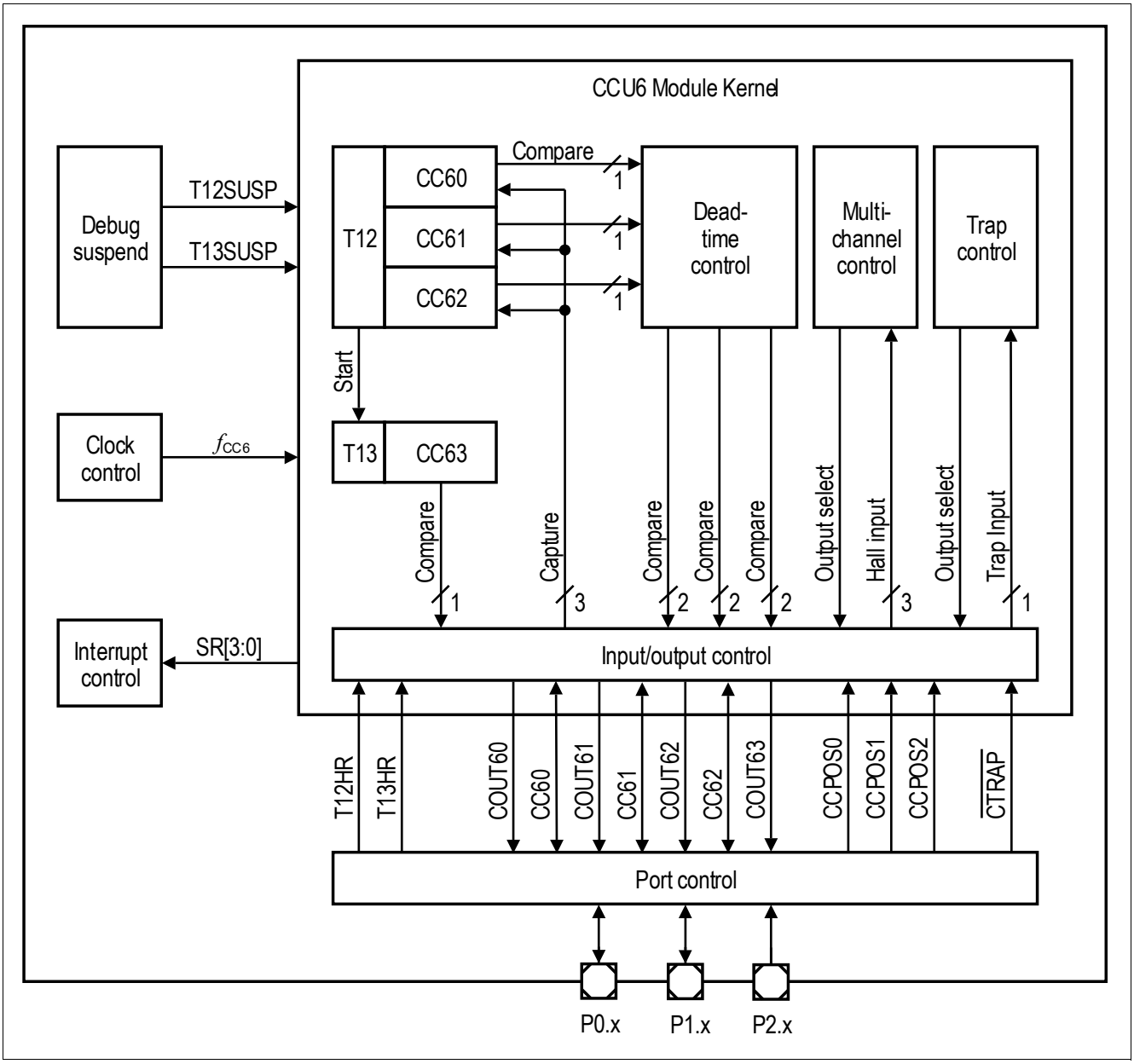


**Figure 20 CCU6 block diagram**

# 19 UART1/UART2

The description in this chapter applies to both UART1 and UART2.

## 19.1 Features

- Full-duplex asynchronous modes
  - 8-bit or 9-bit data frames, LSB first.
  - Fixed or variable baud rate.
- Receive-buffered.
- Multiprocessor communication.
- Interrupt are generated when data transmission or receptions are complete.
- Baud-rate generator with fractional divider for generating a wide range of baud rates.
- Hardware logic for break and synch byte detection.

## 19.2 Introduction

The UART provides a full-duplex asynchronous receiver/transmitter, i.e., it can transmit and receive simultaneously. It is also receive-buffered, i.e., it can commence reception of a second byte before a previously received byte has been read from the receive register. However, if the first byte still has not been read by the time when the reception of the second byte is complete, one of the bytes will be lost. The serial port receive and transmit registers are both accessed through the special function register (SFR) SBUF. Writing to SBUF loads the transmit register, and reading SBUF accesses a physically separate receive register.

### 19.2.1 Block diagram

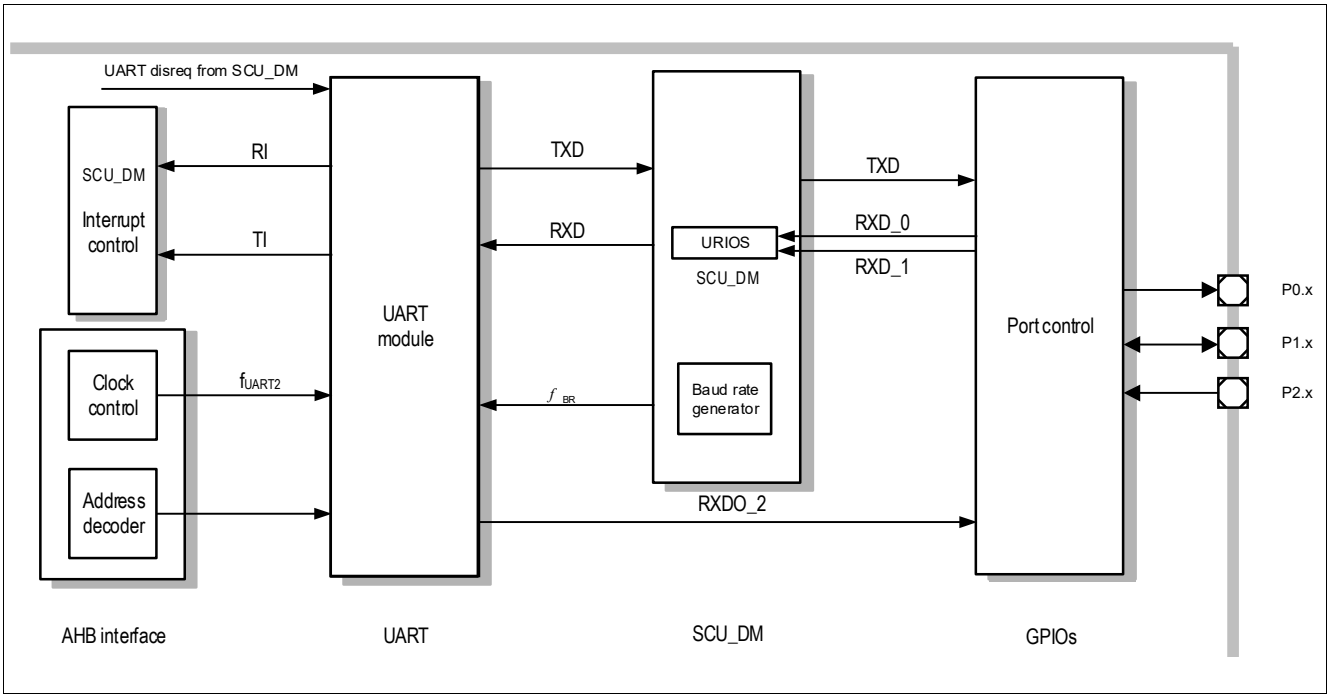


**Figure 21 UART block diagram**

## 19.3 UART modes

The UART can be used in four different modes. In mode 0, it operates as an 8-bit shift register. In mode 1, it operates as an 8-bit serial port. In modes 2 and 3, it operates as a 9-bit serial port. The only difference between mode 2 and mode 3 is the baud rate, which is fixed in mode 2 but variable in mode 3. The variable baud rate is set by the underflow rate on the dedicated baud-rate generator.

The different modes are selected by setting bits SM0 and SM1 to the appropriate values, as shown in **Table 13**.

**Table 13 UART modes**

| SM0 | SM1 | Operating mode | Baud rate |
|---|---|---|---|
| 0 | 0 | Mode 0: 8-bit shift register | $f_{PCLK}/2$ |
| 0 | 1 | Mode 1: 8-bit shift UART | Variable |
| 1 | 0 | Mode 2: 9-bit shift UART | $f_{PCLK}/64$ |
| 1 | 1 | Mode 3: 9-bit shift UART | Variable |

UART1 is connected to the integrated LIN transceiver, and to GPIO for test purposes. UART2 is connected to GPIO only.

# 20 LIN transceiver

## 20.1 Features

**General functional features**

- Compliant with the LIN2.2 standard, backward-compatible with LIN1.3, LIN2.0, and LIN 2.1
- Compliant with SAE J2602 (slew rate, receiver hysteresis)

**Special features**

- Measurement of the LIN master baudrate via Timer2
- LIN can be used as input/output with SFR bits
- TxD timeout feature (optional, on by default)

**Operation mode features**

- LIN Sleep mode (LSLM)
- LIN Receive-Only mode (LROM)
- LIN Normal mode (LNM)
- High voltage input/output mode (LHVIO)

**Supported baud rates**

- Mode for transmission with up to 10.4 kilobaud
- Mode for transmission with up to 20 kilobaud
- Mode for transmission with up to 40 kilobaud
- Mode for transmission with up to 115.2 kilobaud

**Slope mode features**

- Normal Slope mode (20 kbit/s)
- Low Slope mode (10.4 kbit/s)
- Flash mode (115.2 kbit/s)

**Wake-up features**

- LIN bus wake-up

## 20.2 Introduction

The LIN module is a transceiver for the Local Interconnect Network (LIN), compliant with the LIN2.2 standard and backward-compatible with LIN1.3, LIN2.0 and LIN2.1. It operates as a bus driver between the protocol controller and the physical network. The LIN bus is a single-wire, bidirectional bus typically used for in-vehicle networks, using baud rates between 2.4 kilobaud and 20 kilobaud. Additionally, baud rates up to 115.2 kilobaud are implemented.

The LIN module offers several different operation modes, including a LIN Sleep mode and the LIN Normal mode. The integrated slope control allows using several data transmission rates with optimized EMC performance. For data transfer at the end of line, a Flash mode up to 115.2 kilobaud is implemented. In

specific conditions, this Flash mode supports data rates of up to 250 kbit/s. (In production environments, in point-to-point communications with reduced wire lengths and limited supply voltages.).

### 20.2.1 Block diagram

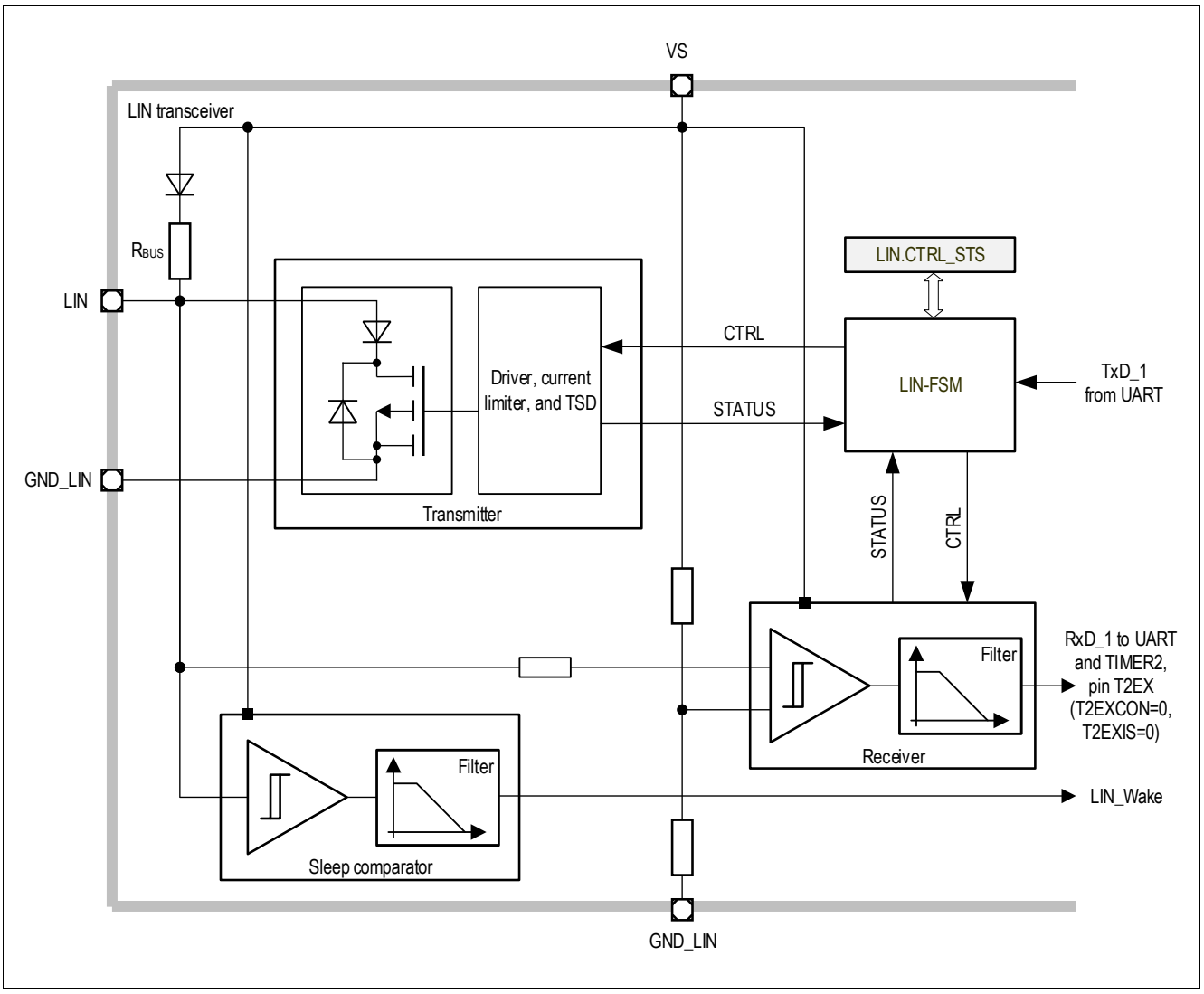


**Figure 22 LIN transceiver block diagram**

# 21 High-speed synchronous serial interface (SSC1/SSC2)

## 21.1 Features

- Master and Slave mode operation
  - Full-duplex or half-duplex operation
- Transmit- and receive-buffered
- Flexible data format
  - Programmable number of data bits: 2 to 16 bits
  - Programmable shift direction: least significant bit (LSB) or most significant bit (MSB) shift first
  - Programmable clock polarity: idle low or high state for the shift clock
  - Programmable clock/data phase: data shift with leading or trailing edge of the shift clock
- Variable baud rate
- Compatible with Serial Peripheral Interface (SPI)
- Interrupt generation
  - On a “transmitter empty” condition
  - On a “receiver full” condition
  - On an error condition (receive, phase, baud rate, or transmission error)

## 21.2 Introduction

The high-speed synchronous serial interface (SSC) supports both full-duplex and half-duplex serial synchronous communication. The serial clock signal can be generated by the SSC internally (Master mode), using its own 16-bit baud rate generator, or can be received from an external master (Slave mode). Data width, shift direction, clock polarity, and phase are programmable. This allows communication with SPI-compatible devices as well as devices using other synchronous serial interfaces.

Data is transmitted or received on the TXD and RXD lines, which are normally connected to the MTSR (Master Transmit, Slave Receive) and MRST (Master Receive, Slave Transmit) pins. The clock signal is output via the MS_CLK (Master Serial Shift Clock) line or input via the SS_CLK (Slave Serial Shift Clock) line. Both lines are normally connected to the SCLK pin. Transmission and reception of data are double-buffered.

### 21.2.1 Block diagram

**Figure 23** shows all functionally relevant interfaces associated with the SSC kernel.

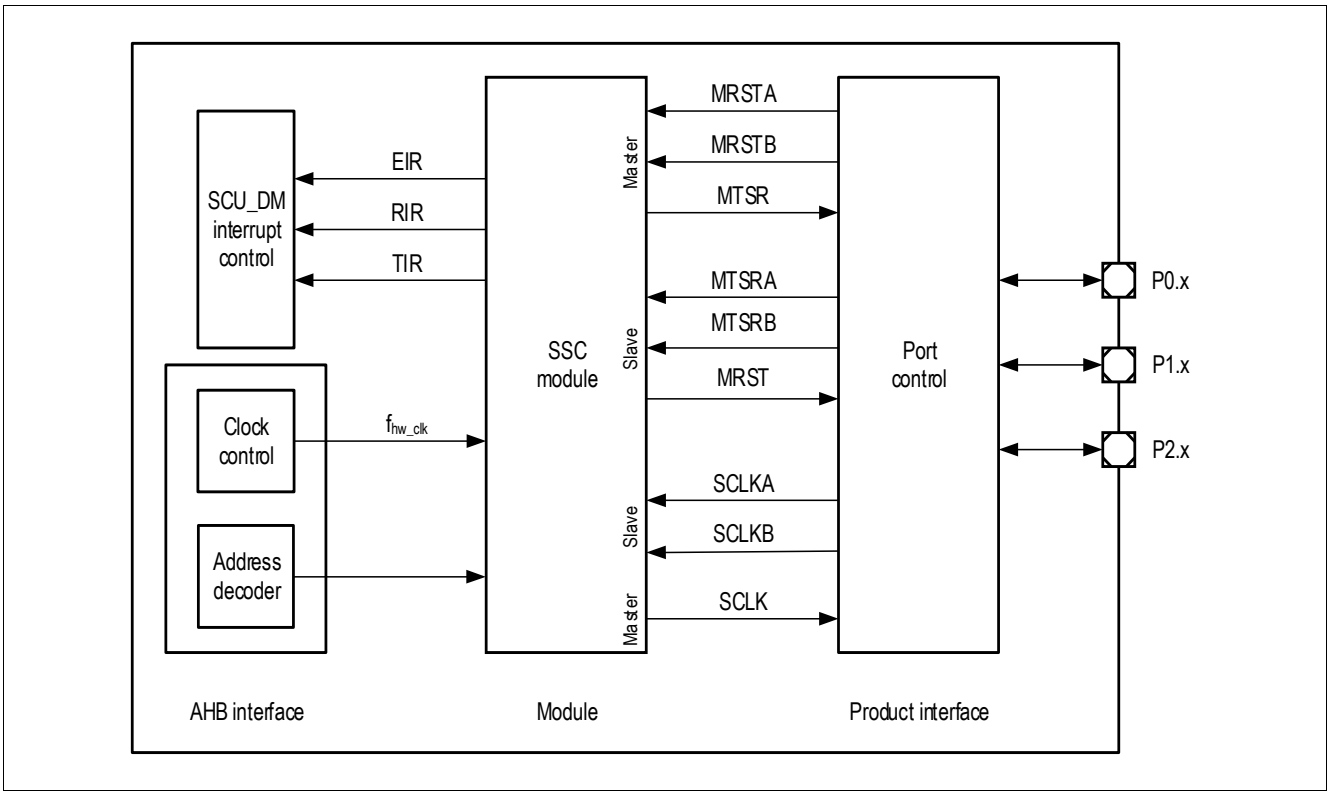


**Figure 23 SSC interface diagram**

# 22 Measurement unit

## 22.1 Features

- 1 x 8-bit ADC with 10 inputs. Attenuators allow measuring high-voltage input signals.
- Supply voltage attenuators for attenuating **VBAT_SENSE**, **VS**, **VDDP** and **VDDC**.
- VBG monitoring of the 8-bit ADC to guarantee functional safety requirements.
- Bridge driver diagnosis measurement (VDH, VCP).
- Temperature sensor for monitoring the chip temperature and PMU regulator temperature.
- Supplement block with reference voltage generation, bias current generation, voltage buffer for NVM reference voltage, voltage buffer for analog module reference voltage, and a test interface.

## 22.2 Introduction

The measurement unit is a functional unit that comprises the following submodules:

**Table 14 Measurement functions and associated modules**

| Module name | Module | Functions |
|---|---|---|
| Central function unit | Bandgap reference circuit | The bandgap reference submodule provides two reference voltages:<br>1. A trimmable reference voltage for the 8-bit ADC. A local dedicated bandgap circuit ensures that the reference voltage does not drop, e.g., because of crosstalk or ground voltage shift.<br>2. The reference voltage for the NVM module. |
| 8-bit ADC (ADC2) | 8-bit ADC module with 10 multiplexed inputs and including high-voltage input attenuators | • 5 high-voltage inputs supporting the full supply range (2.5 V...30.7 V(FS))<br>• 2 medium-voltage inputs (0..5 V/7 V FS).<br>• 3 low-voltage inputs (0..1.2 V/1.6 V FS)<br>(See the following figure for the allocation of the inputs). |
| 10-bit ADC (ADC1) | 10-bit ADC module with 8 multiplexed inputs | Five (5 V) analog inputs from port 2.x. |
| VDH input voltage attenuator | VDH input voltage attenuator | Scales down (VDH) to the input voltage range of ADC1.CH6. |

**Table 14 Measurement functions and associated modules** (cont'd)

| Module name | Module | Functions |
|---|---|---|
| Temperature sensor | Temperature sensor with two multiplexed sensing elements:<br>• Sensor located on the PMU<br>• Sensor located on the central chip | Generates an output voltage that is a linear function of the local chip (junction) temperature. |
| Core measurement module | Digital signal processing and ADC2 control unit | 1. Generates the control signal for the 8-bit ADC2 and the synchronous clock for the switched capacitor circuits.<br>2. Performs digital signal processing functions and provides status outputs for interrupt generation. |

## 22.2.1 Block diagram

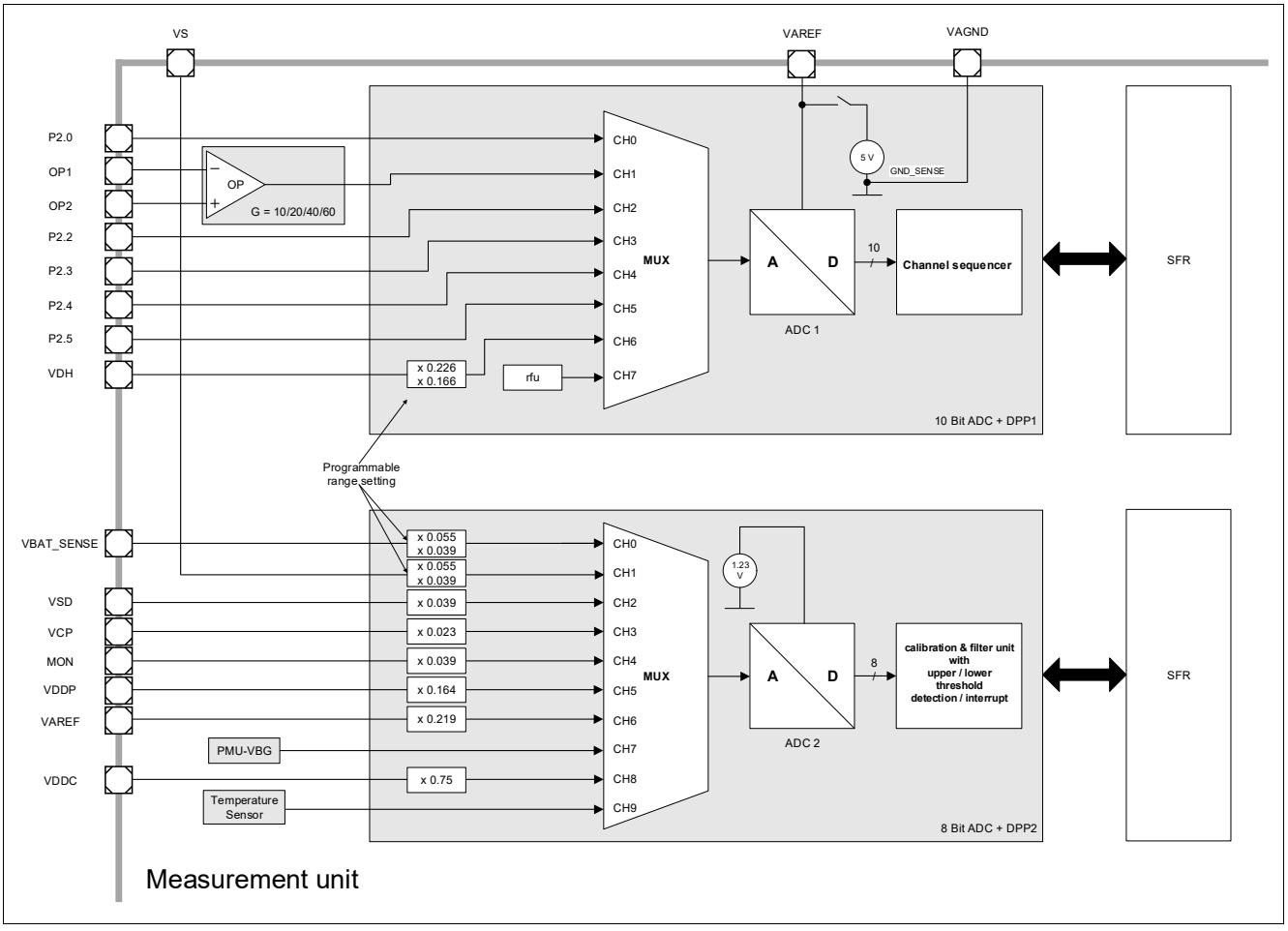


**Figure 24 Measurement unit, overview (with opamp)**

# 23 Core measurement module (incl. ADC2)

## 23.1 Features

- 10 individually programmable channels, split into two groups of user-configurable and non-configurable channels, respectively.
- Individually programmable channel prioritization scheme for the measurement unit.
- Two independent filter stages with programmable low-pass and time filter characteristics for each channel.
- Two channel configurations:
  - Programmable upper- and lower trigger thresholds comprising a fully programmable hysteresis.
  - Two individually programmable trigger thresholds with limit hysteresis settings.
- Individually programmable interrupts and statuses for all channel thresholds.

## 23.2 Introduction

The basic function of this block is the digital postprocessing of several digitized analog measurement signals by filtering, level comparison, and interrupt generation. The measurement postprocessing block consists of ten identical channel units attached to the outputs of the 10-channel 8-bit ADC (ADC2). It processes ten channels, where the channel sequence and prioritization is programmable within a wide range.

### 23.2.1 Block diagram

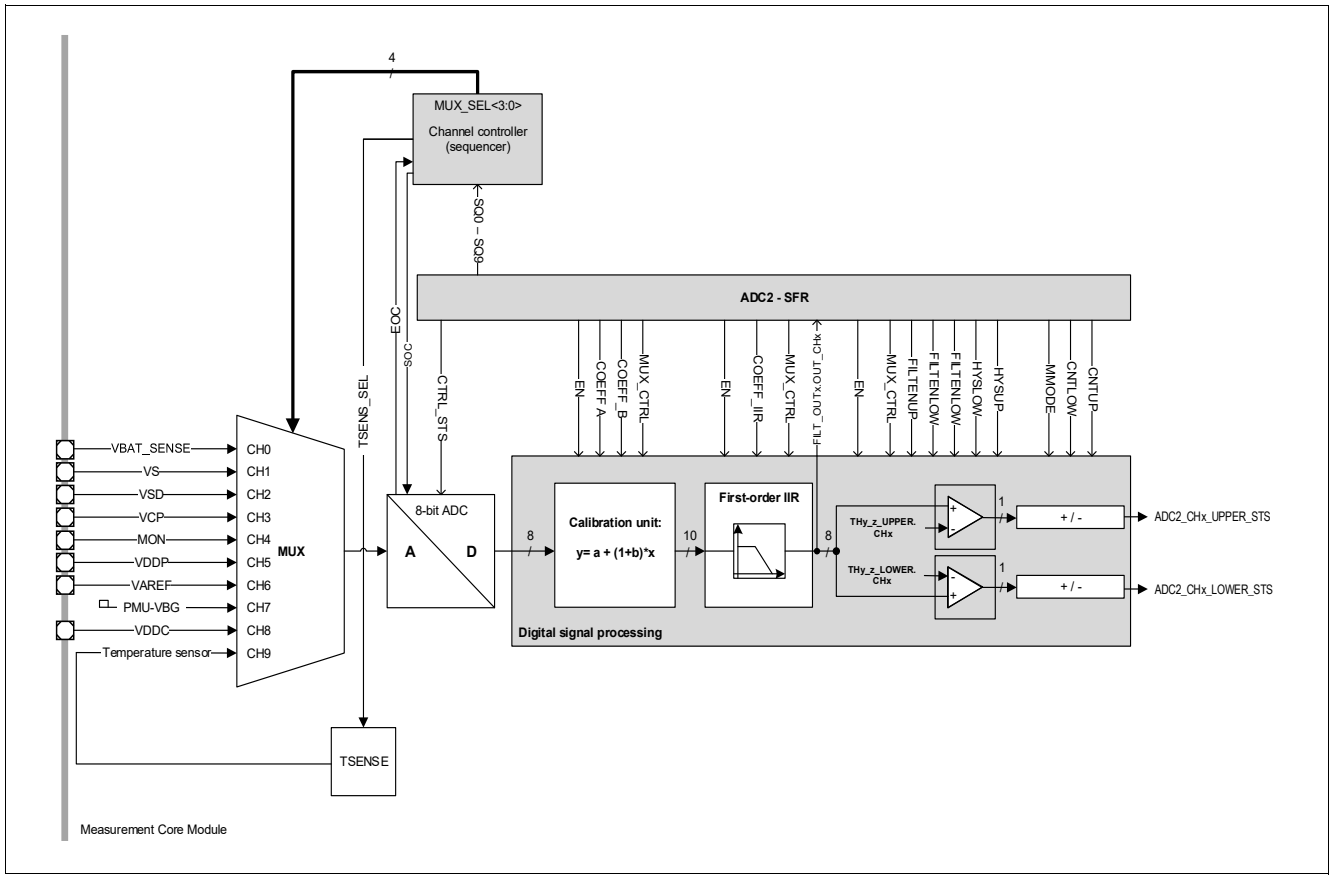


**Figure 25 Module block diagram**

### 23.2.2 Core measurement module mode overview

The basic function of this unit is the digital signal processing of several digitized analog measurement signals by filtering, level comparison, and interrupt generation. The core measurement module processes ten channels in a quasi-parallel process.

As shown in the figure above, the ADC2 postprocessing unit consists of a channel controller (sequencer), a 10-channel demultiplexer, and the signal-processing block, which filters and compares the sampled ADC2 values for each channel individually. The channel control block controls the multiplexer sequencing on the analog side, before the ADC2, and in the digital domain, behind the ADC2. The channel sequence can be controlled in a flexible way, which allows a certain degree of channel prioritization.

This capability can be used, e.g., to give supply voltage channels a higher priority than the other channel measurements. In addition, the core measurement module offers two different postprocessing measurement modes for over- and undervoltage detection and for two-level threshold detection.

The channel controller (sequencer) runs in one of the following modes:

- Normal Sequencer: Channels are selected according to the 10 sequence registers which contain individual enablers for each of the 10 channels.
- Exceptional Interrupt Measurement: Following a hardware event, a high-priority channel is inserted into the current sequence. The current actual measurement is not destroyed.
- Exceptional Sequence Measurement: Following a hardware event, a complete sequence is inserted after the current measurement is finished. The current sequence is interrupted by the exception sequence.

# 24 10-bit analog-to-digital converter (ADC1)

## 24.1 Features

The principal features of the ADC1 are:

- Up to 8 analog input channels (channel 7 reserved for future use).
- Flexible results handling
  - 10-bit resolution.
- Flexible source selection due to sequencer:
  - Insert one exceptional sequence (ESM).
  - Insert one interrupt measurement into the current sequence (EIM), single or up to 128 times.
  - Software mode.
- Conversion sample time (separate for each channel) adjustable to adapt to sensors and reference.
- Standard external reference (VAREF) to support ratiometric measurements and different signal scales.
- DMA support, transfer ADC conversion results via DMA into RAM.
- Support of suspended and power-saving modes.
- Result data protection for slow CPU access (Wait-for-Read mode).
- Programmable clock divider.
- Integrated sample and hold circuitry.

## 24.2 Introduction

The TLE9862QXA40 includes a high-performance 10-bit analog-to-digital converter (ADC1) with eight multiplexed analog input channels. The ADC1 uses a successive approximation technique to convert the analog voltage levels from up to eight different sources. The analog input channels of the ADC1 are available at AN0 and AN2 to AN5.

### 24.2.1 Block diagram

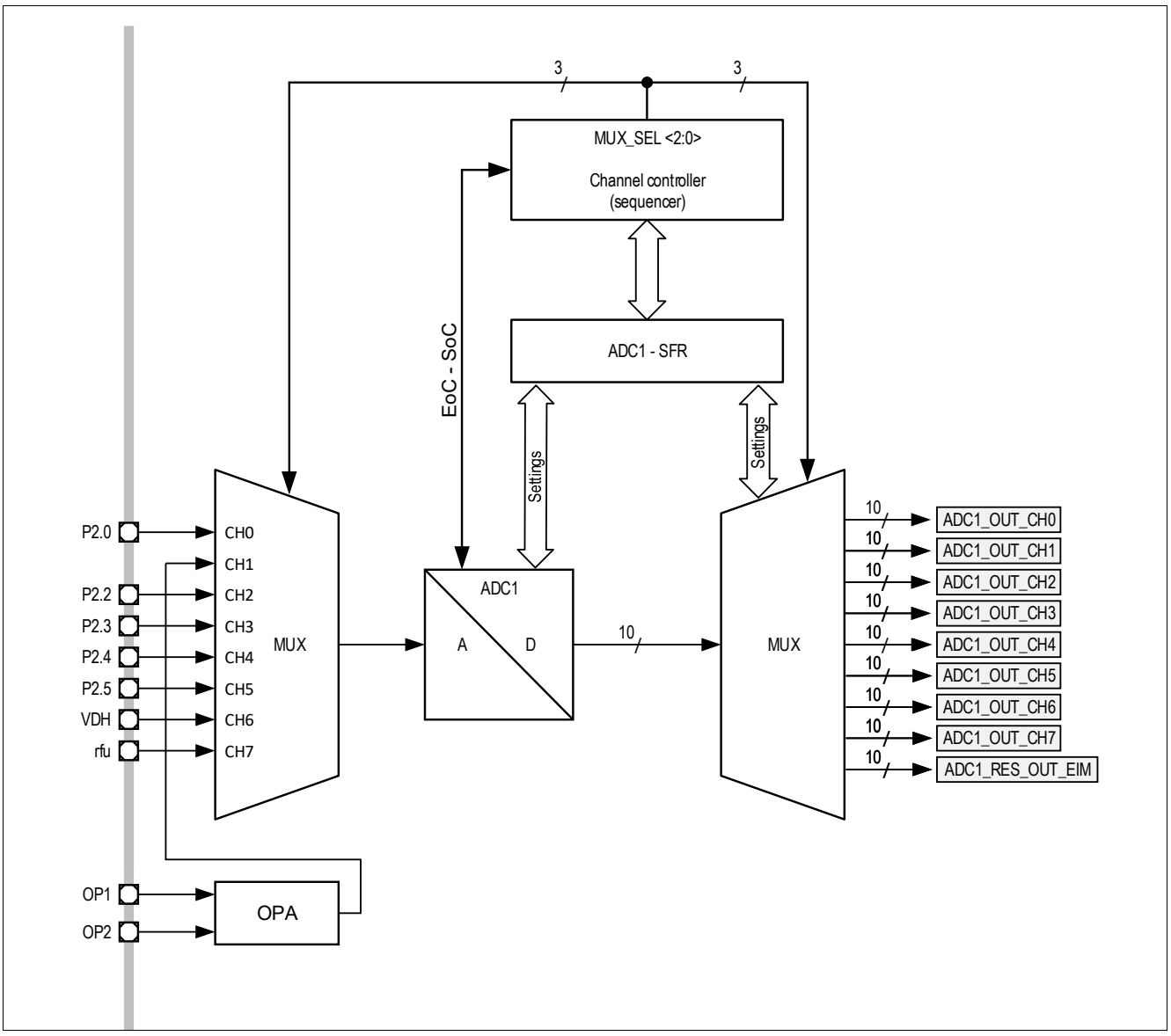


**Figure 26 ADC1 top-level block diagram**

As shown in the figure above, the ADC1 postprocessing block consists of a channel controller (Sequencer) and an 8-channel demultiplexer. The channel control block controls the multiplexer sequencing on the analog side, before the ADC1, and in the digital domain, behind the ADC1. The channel sequence can be controlled in a flexible way, which allows a certain degree of channel prioritization.

This capability can be used, e.g., to give supply voltage channels a higher priority than the other channel measurements.

# 25 High-voltage monitor input

## 25.1 Features

- High-voltage input with $V_{MONth}$ threshold voltage
- Integrated selectable pull-up and pull-down current sources
- Wake capability for power-saving modes
- Level change sensitivity configurable for transitions from low to high, high to low, or both directions

## 25.2 Introduction

This module is dedicated to monitor external voltage levels above or below a specified threshold or it can be used to detect a wake-up event at the high-voltage MON pin in low-power mode. The input level can be monitored if the module is enabled (PMU_MON_CNF).

To use the Wake function when the IC is in a low-power mode, the monitoring pin is switched to Sleep mode via the SFR bit EN.

### 25.2.1 Block diagram

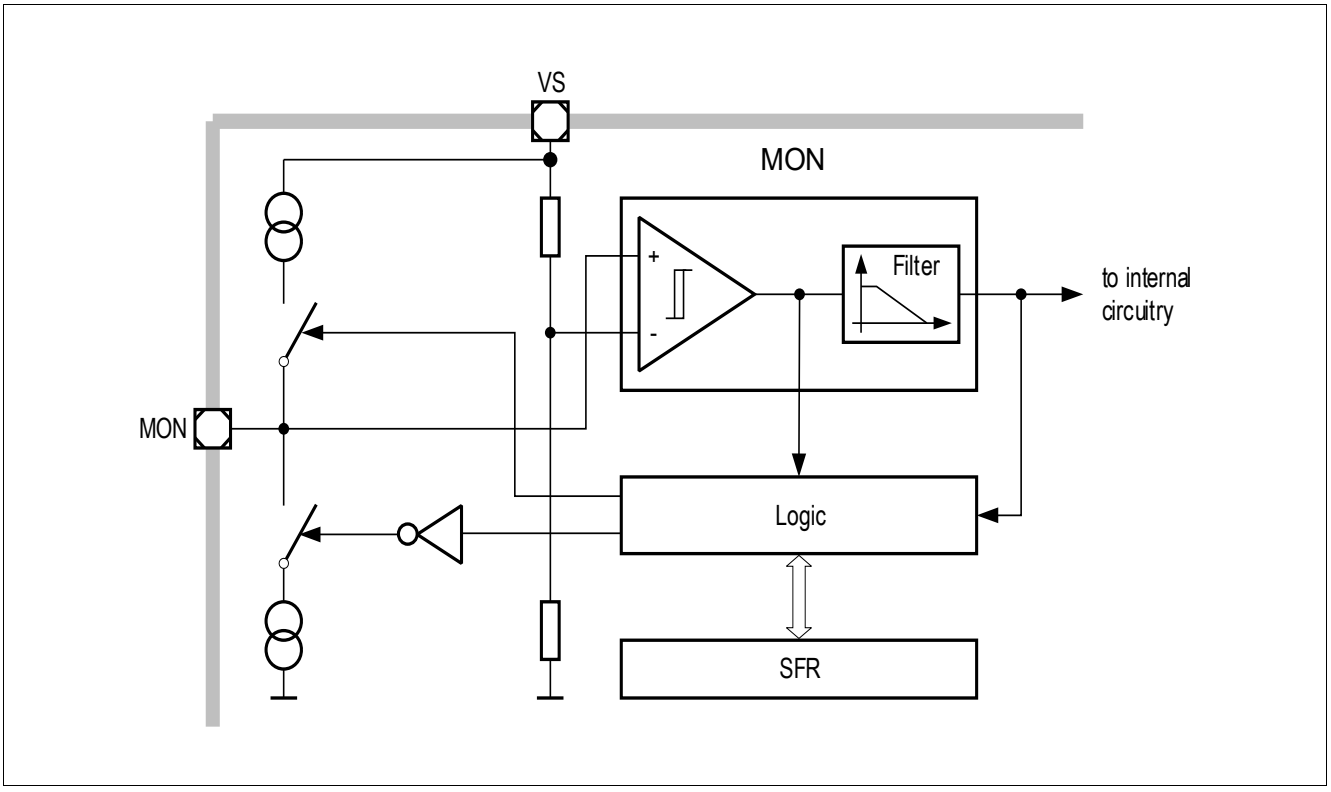


**Figure 27 High-voltage monitor input block diagram**

# 26 Bridge driver (incl. charge pump)

## 26.1 Features

The MOSFET driver is intended to drive external normal-level NFET transistors in bridge configurations. The driver provides many diagnostic functions for detecting faults.

**Functional features**

- External power NFET transistor driver stage with driver capability of $Q_{tot\_max}$.
- Adjustable cross-conduction protection.
- Supply voltage (VSD) monitoring incl. adjustable over- and undervoltage shutdown with configurable interrupt signalling.
- VSD operating range: $V_{SD\_AM}$.
- VDS comparators for short-circuit-detection in both on- and off-states.
- Open-load detection in the off-state.

## 26.2 Introduction

The MOSFET driver stage can be used for controlling external power NFET transistors (normal level). The module output is controlled by the SFR or the System PWM Machine (CCU6).

## 26.2.1 Block diagram

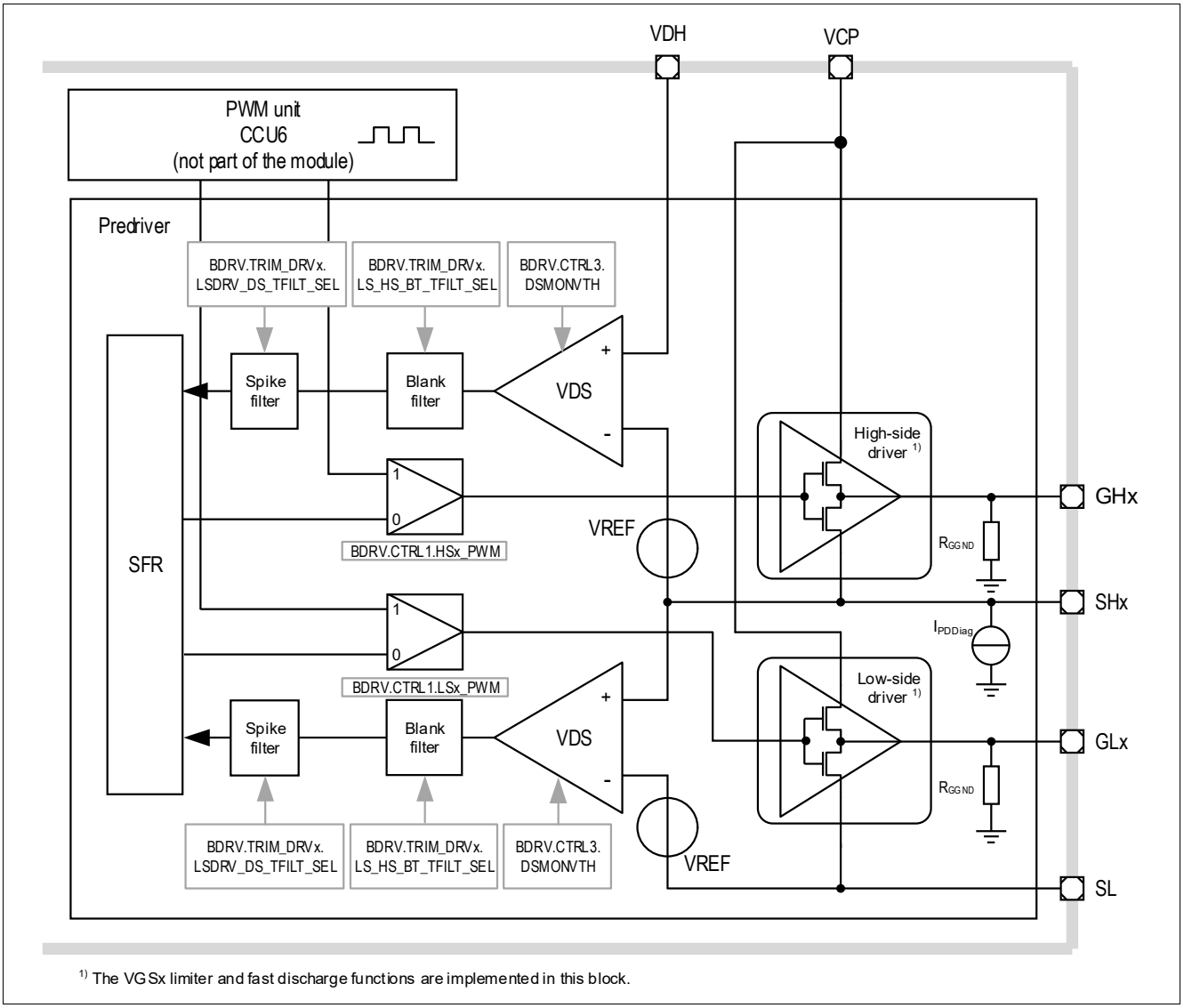


**Figure 28 Bridge driver module block diagram (incl. system connections)**

## 26.2.2 General

The bridge driver can be controlled in two different ways:

- In Normal mode, the output stage is fully controllable through the SFR registers CTRLx (x = 1,2,3). Protection functions such as overcurrent and open-load detection are available.
- The PWM mode can be enabled by setting the corresponding bit in CTRL1 and CTRL2. The PWM must be configured in the System PWM Module (CCU6). All protection functions are available in PWM mode as well.

### Protection functions

- Overcurrent detection and shutdown feature for external MOSFET based on drain-source measurements.
- Programmable minimum cross-current protection time.
- Open-load detection feature in the off-state for external MOSFET.

# 27 Current sense amplifier

## 27.1 Features

**Main features**

- Programmable gain settings: G
- Differential input voltage: $V_{IX}$
- Wide common-mode input range: $V_{CM}$
- Low setting time: $T_{SET}$

## 27.2 Introduction

The current sense amplifier in the following figure can be used to measure near-ground differential voltages via the 10-bit ADC. Its gain is digitally programmable through internal control registers.

Linear calibration has to be applied to achieve high gain accuracy, e.g., end-of-line calibration using the shunt resistor.

The following figure shows how the current sense amplifier can be used as a low-side current sense amplifier where the motor current is converted to a voltage by means of a shunt resistor $R_{SH}$. A differential amplifier input is used to eliminate measurement errors caused by a voltage drop across the stray resistance $R_{Stray}$ and differences between the external and internal grounds. If the voltage at one or both inputs is outside the operating range, the input circuit is overloaded and requires a certain specified **recovery time**.

In general, an external low-pass filter should suppress of EMI.

### 27.2.1 Block diagram

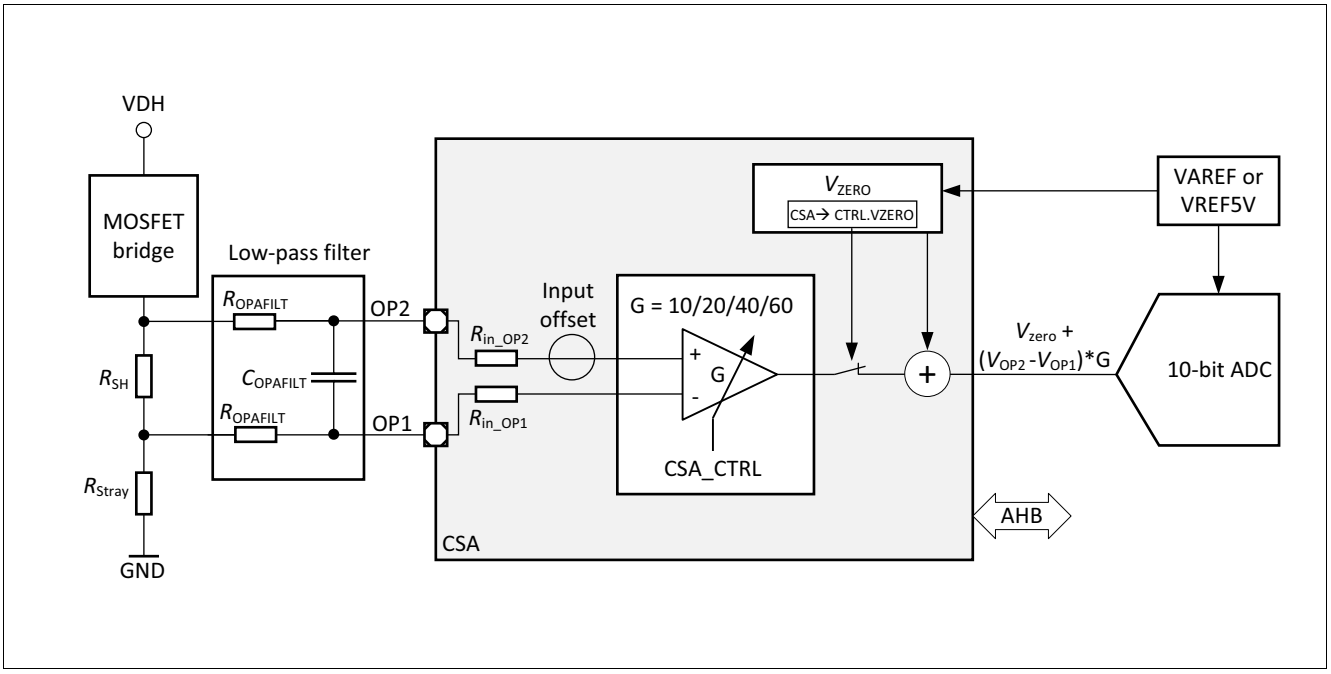


**Figure 29 Current sense amplifier block diagram**

# 28 Application information

## 28.1 H-Bridge driver

The following figure shows the TLE9862QXA40 in an electric drive application setup controlling an H-Bridge motor.

*Note: The following information is given as a hint for the implementation of the device only and shall not be regarded as a description or warranty of a certain functionality, condition or quality of the device.*

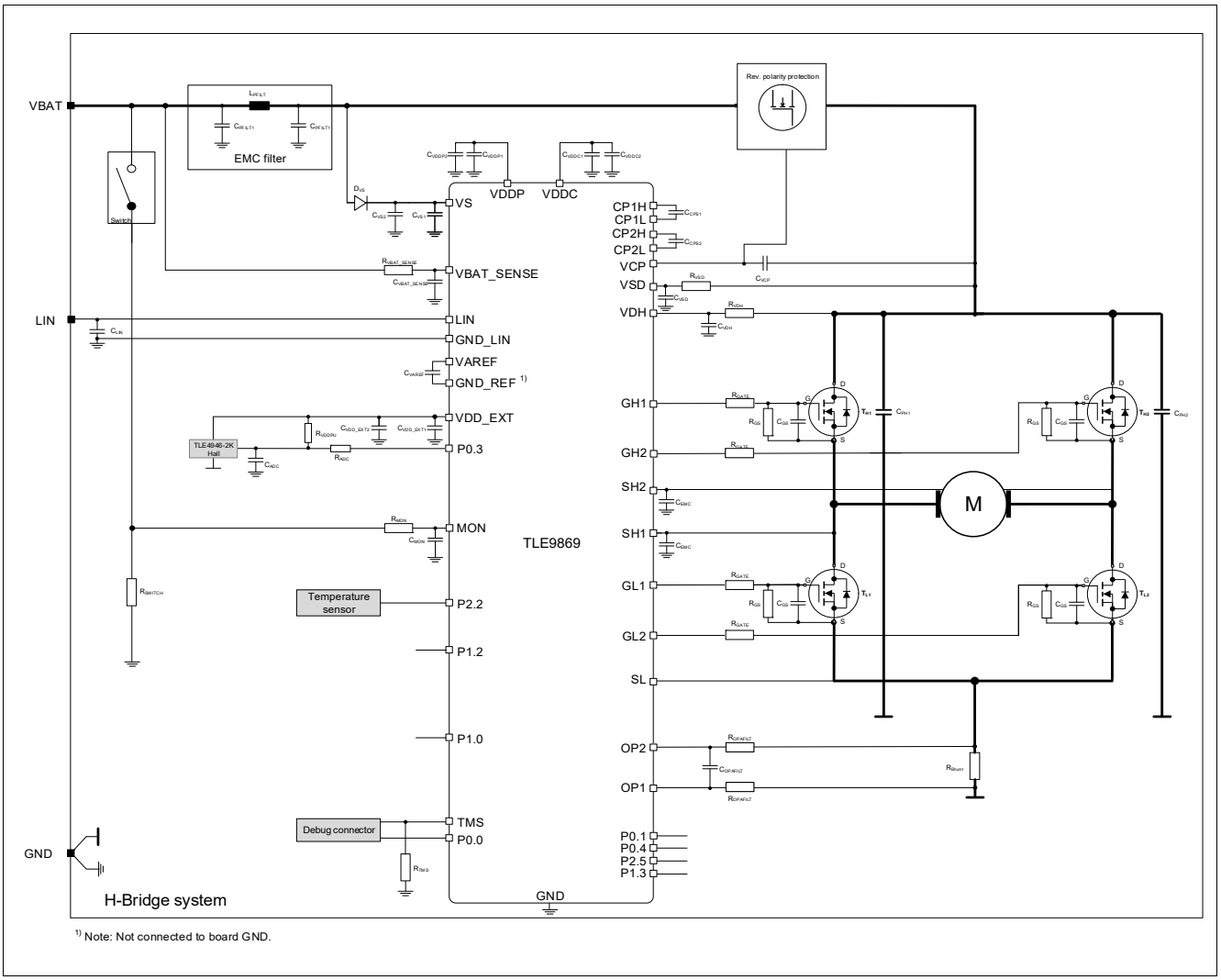


**Figure 30 Simplified sample application diagram**

*Note: This is a very simplified example of an application circuit and bill of materials. The function must be verified in the actual application.*

## Application information

**Table 15 External components (BOM)**

| Symbol | Function | Component |
|---|---|---|
| $C_{VS1}$ | Blocking capacitor at VS pin | ≥ 100 nF ceramic, ESR < 1 Ω |
| $C_{VS2}$ | Blocking capacitor at VS pin | > 2.2 µF Elco[1)] |
| $C_{VDDP}$ | Blocking capacitor at VDDP pin | See P_2.1.2 and P_2.1.20 |
| $C_{VDD\_EXT}$ | Blocking capacitor at VDDEXT pin | See P_2.3.22 and P_2.3.20 |
| $C_{VDDC}$ | Blocking capacitor at VDDC pin | See P_2.2.1 and P_2.2.17 |
| $C_{VAREF}$ | Blocking capacitor at VAREF pin | See P_9.1.1 |
| $C_{LIN}$ | Standard C for LIN slave | 220 pF |
| $C_{VSD}$ | Filter C for charge pump end driver | 1 µF |
| $C_{CPS1}$ | Charge pump capacitor | 220 nF |
| $C_{CP2S}$ | Charge pump capacitor | 220 nF |
| $C_{VCP}$ | Charge pump capacitor | 470 nF |
| $C_{MON1}$ | Filter C for ISO pulses | 10 nF |
| $C_{VDH}$ | Capacitor | 1 nF |
| $C_{PH1}$ | Capacitor | 220 µF |
| $C_{PH2}$ | Capacitor | 220 µF |
| $C_{OPAFILT}$ | Capacitor | 1 nF |
| $C_{EMCP1}$ | Capacitor | 1 nF |
| $C_{EMCP2}$ | Capacitor | 1 nF |
| $C_{PFILT1}$, $C_{PFILT2}$ | Capacitor | 10 µF |
| $C_{VBAT\_SENSE}$ | Capacitor | 10 nF |
| $R_{MON}$ | Resistor at MON pin | 1 kΩ |
| $R_{VSD}$ | Limitation of reverse current due to transient (-2 V, 8 ms).<br>Max. ratings of the VSD pin has to be met, alternatively the resistor shall be replaced by a diode. | 2 Ω |
| $R_{VDH}$ | Resistor | 1 kΩ |
| $R_{GATE}$ | Resistor | 2 Ω |
| $R_{OPAFILT}$ | Resistor | 12 Ω |
| $R_{VBAT\_SENSE}$ | Resistor | – |
| $R_{SH1}$ | Resistor | Optional |
| $R_{SH2}$ | Resistor | Optional |
| $L_{PFILT}$ | | – |
| $D_{VS}$ | Reverse-polarity protection diode | – |

1) The capacitor must be dimensioned so as to ensure that operations which modify the content of the flash are never interrupted (e.g., in case of power loss).

## 28.2 ESD immunity according to IEC61000-4-2

*Note: Tests for ESD immunity according to IEC61000-4-2 “gun test” (150 pF, 330 Ω) have been performed. The results and test conditions will be available in a test report.*

**Table 16 ESD “gun test”**

| Performed test | Result | Unit | Remarks |
|---|---|---|---|
| ESD at pin LIN, versus GND[1)] | > 6 | kV | Positive pulse |
| ESD at pin LIN, versus GND[1)] | < -6 | kV | Negative pulse |

1) ESD test “ESD GUN” is specified with external components; see application diagram: $C_{MON}$ = 100 nF, $R_{MON}$ = 1 kΩ, $C_{LIN}$ = 220 pF, $C_{VS}$ = > 20 µF ELCO + 100 nF ESR < 1 Ω, $C_{VSD}$ = 1 µF, $R_{VSD}$ = 2 Ω.

# 29 Electrical characteristics

This chapter includes all relevant electrical characteristics of the product TLE9862QXA40.

## 29.1 General characteristics

### 29.1.1 Absolute maximum ratings

**Table 17 Absolute maximum ratings[1)]**

$T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **Voltages – supply pins** | | | | | | | |
| Supply voltage VS | $V_S$ | -0.3 | – | 40 | V | Load dump | P_1.1.1 |
| Supply voltage VSD | $V_{SD}$ | -0.3 | – | 48 | V | – | P_1.1.2 |
| Supply voltage VSD | $V_{SD\_max\_extend}$ | -2.8 | – | 48 | V | Series resistor $R_{VSD}$ = 2.2 Ω, $t$ = 8 ms [2)] | P_1.1.32 |
| Voltage range VDDP | $V_{DDP}$ | -0.3 | – | 5.5 | V | – | P_1.1.3 |
| Voltage range VDDP | $V_{DDP\_max\_extend}$ | -0.3 | – | 7 | V | In case of voltage transients on $V_S$ with $\Delta V_S/\Delta t \geq 1$ V/µs; duration: $t \leq 150$ µs; $C_{VDDP} \leq 570$ nF | P_1.1.41 |
| Voltage range VDDEXT | $V_{DDEXT}$ | -0.3 | – | 5.5 | V | – | P_1.1.4 |
| Voltage range VDDEXT | $V_{DDEXT\_max\_extend}$ | -0.3 | – | 7 | V | In case of voltage transients on $V_S$ with $\Delta V_S/\Delta t \geq 1$ V/µs; duration: $t \leq 150$ µs; $C_{VDDEXT} \leq 570$ nF | P_1.1.42 |
| Voltage range – VDDC | $V_{DDC}$ | -0.3 | – | 1.6 | V | – | P_1.1.5 |
| **Voltages – high-voltage pins** | | | | | | | |
| Battery voltage VBAT_SENSE | $V_{BAT\_SENSE}$ | -28 | – | 40 | V | [3)] | P_1.1.6 |
| Input voltage at LIN | $V_{LIN}$ | -28 | – | 40 | V | – | P_1.1.7 |
| Input voltage at MON | $V_{MON\_maxrate}$ | -28 | – | 40 | V | [4)] | P_1.1.8 |
| Input voltage at VDH | $V_{VDH\_maxrate}$ | -2.8 | – | 40 | V | [5)] | P_1.1.38 |
| Voltage range at GHx | $V_{GH}$ | -8.0 | – | 48 | V | [6)] | P_1.1.9 |
| Voltage range at GHx vs. SHx | $V_{GHvsSH}$ | -0.3 | – | 14 | V | – | P_1.1.44 |
| Voltage range at SHx | $V_{SH}$ | -8.0 | – | 48 | V | – | P_1.1.11 |
| Voltage range at SLx | $V_{SL}$ | -8.0 | – | 48 | V | – | P_1.1.48 |
| Voltage range at GLx | $V_{GL}$ | -8.0 | – | 48 | V | [7)] | P_1.1.13 |
| Voltage range at GLx vs. SL | $V_{GLvsSL}$ | -0.3 | – | 14 | V | – | P_1.1.45 |

**Table 17 Absolute maximum ratings[1)]** (cont'd)

$T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Voltage range at charge pump pins CP1H, CP1L, CP2H, CP2L, VCP | $V_{CPx}$ | -0.3 | – | 48 | V | [8)] | P_1.1.15 |
| **Voltages – GPIOs** | | | | | | | |
| Voltage on any port pin[9)] | $V_{in}$ | -0.3 | – | $V_{DDP}$ +0.3 | V | $V_{IN} < V_{DDPmax}$ [10)] | P_1.1.16 |
| **Current at VCP pin** | | | | | | | |
| Max. current at VCP pin | $I_{VCP}$ | -15 | – | – | mA | – | P_1.1.35 |
| **Injection current at GPIOs** | | | | | | | |
| Injection current on any port pin | $I_{GPIONM}$ | -5 | – | 5 | mA | [11)] | P_1.1.34 |
| Sum of all injected currents in Normal mode | $I_{GPIOAM\_sum}$ | -50 | – | 50 | mA | [11)] | P_1.1.30 |
| Sum of all injected currents in Power-down mode (Stop mode) | $I_{GPIOPD\_sum}$ | -5000 | – | 50 | µA | [11)] | P_1.1.36 |
| Sum of all injected currents in Sleep mode | $I_{GPIOSleep\_sum}$ | -5 | – | 5 | mA | [11)] | P_1.1.37 |
| **Other voltages** | | | | | | | |
| Input voltage VAREF | $V_{AREF}$ | -0.3 | – | $V_{DDP}$ +0.3 | V | – | P_1.1.17 |
| Input voltage OP1, OP2 | $V_{OAI}$ | -7 | – | 7 | V | – | P_1.1.23 |
| **Temperatures** | | | | | | | |
| Junction temperature | $T_j$ | -40 | – | 150 | °C | – | P_1.1.18 |
| Storage temperature | $T_{stg}$ | -55 | – | 150 | °C | – | P_1.1.19 |
| **ESD susceptibility** | | | | | | | |
| ESD susceptibility all pins | $V_{ESD1}$ | -2 | – | 2 | kV | HBM [12)] | P_1.1.20 |
| ESD susceptibility pins MON, VS, VSD, VBAT_SENSE vs. GND | $V_{ESD2}$ | -4 | – | 4 | kV | HBM [13)] | P_1.1.21 |
| ESD susceptibility pins LIN vs. GND_LIN | $V_{ESD3}$ | -6 | – | 6 | kV | HBM [12)] | P_1.1.22 |

**Table 17 Absolute maximum ratings[1)]** (cont'd)

$T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| ESD susceptibility CDM all pins vs. GND | $V_{ESD\_CDM1}$ | -500 | – | 500 | V | 14) | P_1.1.28 |
| ESD susceptibility CDM pins 1, 12, 13, 24, 25, 36, 37, 48 (corner pins) vs. GND | $V_{ESD\_CDM2}$ | -750 | – | 750 | V | 14) | P_1.1.43 |

1) Not subject to production test, specified by design.
2) Conditions and minimum values are derived from application conditions for reverse polarity events.
3) The minimum voltage of -28 V applies only with an external 3.9 kΩ series resistor.
4) The minimum voltage of -28 V applies only with an external 3.9 kΩ series resistor.
5) The minimum voltage of -2.8 V applies only with an external 1 kΩ series resistor.
6) To achieve the maximum ratings on this pin, the following relationships with parameter P_1.1.44 have to be observed: $V_{GH} < V_{SH} + V_{GHvsSH\_min}$ and $V_{SH} < V_{GH} + 0.3$ V.
7) To achieve the maximum ratings on this pin, the following relationships with parameter P_1.1.45 have to be observed: $V_{GL} < V_{SL} + V_{GLvsSL\_min}$ and $V_{SL} < V_{GL} + 0.3$ V.
8) These limits can be kept if the maximum current drawn out of the pin does not exceed the limit of 200 µA.
9) See the XTAL parameter specification, when GPIOs (Port pins P2.0 and P2.2) are used as XTAL.
10) Includes TMS and RESET.
11) P_1.1.16 must not been exceeded in the injection current.
12) ESD susceptibility based on the HBM according to ANSI/ESDA/JEDEC JS-001 (1.5 kΩ, 100 pF).
13) MON with external circuitry of a series resistor with 3.9 kΩ and 10 nF (at connector); VS with an external ceramic capacitor with 100 nF; VSD with an external capacitor with 470 nF; VDH with external circuitry of a series resistor with 1 kΩ and 3.3 nF (at pin).
14) ESD susceptibility based on the HBM according to ANSI/ESDA/JEDEC JESD22-C101F.

**Notes**

1. *Stresses above the ones listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect the reliability of the device.*
2. *Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered to be outside the normal operating range. Protection functions are not designed for continuous repetitive operation.*

## 29.1.2 Functional range

**Table 18 Functional range**

$T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Supply voltage in Active mode | $V_{S\_AM}$ | 5.5 | – | 28 | V | – | P_1.2.1 |
| Extended supply voltage in Active mode | $V_{S\_AM\_extend}$ | 28 | – | 40 | V | 1)2) Extended supply range leads to parameter deviation. | P_1.2.16 |
| Supply voltage in Active mode for MOSFET driver supply | $V_{SD\_AM}$ | 5.4 | – | 28 | V | – | P_1.2.18 |
| Extended supply voltage in Active mode for MOSFET driver supply | $V_{SD\_AM\_extend}$ | 28 | – | 32 | V | 1)2)5) Extended supply range leads to parameter deviation. | P_1.2.17 |
| Specified supply voltage for LIN transceiver | $V_{S\_AM\_LIN}$ | 5.5 | – | 18 | V | Parameter specification. | P_1.2.2 |
| Extended supply voltage for LIN transceiver | $V_{S\_AM\_LIN}$ | 4.8 | – | 28 | V | 3) Extended supply range leads to parameter deviation. | P_1.2.14 |
| Supply voltage in Active mode with reduced functionality (retaining full operation for microcontroller and flash) | $V_{S\_AMmin}$ | 3.0 | – | 5.5 | V | 4) | P_1.2.3 |
| Supply voltage in Sleep mode | $V_{S\_Sleep}$ | 3.0 | – | 28 | V | – | P_1.2.4 |
| Supply voltage transients slew rate | $\Delta V_S/\Delta t$ | -1 | – | 1 | V/µs | 5) | P_1.2.5 |
| Output sum current for all GPIO pins | $I_{GPIO,sum}$ | -50 | – | 50 | mA | 5) | P_1.2.7 |
| Operating frequency | $f_{sys}$ | 5 | – | 40 | MHz | 6) | P_1.2.20 |
| Junction temperature | $T_j$ | -40 | – | 150 | °C | – | P_1.2.9 |

1) This operation voltage range is only allowed for a short duration: $t_{max} \leq 400$ ms (continuous operation at this voltage is not allowed), $f_{sys}$ = 24 MHz, $I_{VDDP}$ = 10 mA, $I_{VDDEXT}$ = 5 mA. In addition, the power dissipation caused by the charge pump and the MOSFET driver has to be considered.

2) Parameter deviations mean that the electrical parameters of the device may present values outside the range specified within the minimum and maximum values.

3) Parameter deviations mean that the electrical parameters of the device may present values outside the range specified within the minimum and maximum values.

4) Functionality is reduced (for example, cranking pulse); parameter deviations are possible: The electrical parameters of the device may present values outside the range specified within the minimum and maximum values.

5) Not subject to production test, specified by design.

6) Function not specified when limits are exceeded.

### 29.1.3 Current consumption

**Table 19 Electrical characteristics**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **Current consumption at VS pin** | | | | | | | |
| Current consumption in Active mode at VS pin | $I_{Vs}$ | – | 30 | 35 | mA | $f_{sys}$ = 20 MHz<br>No loads on pins,<br>LIN in recessive state [1] | P_1.3.1 |
| Current consumption in Active mode at VSD pin | $I_{VSD}$ | – | – | 40 | mA | 20 kHz<br>PWM on bridge driver | P_1.3.8 |
| Current consumption in Slow-down mode | $I_{SDM}$ | – | – | 30 | mA | $f_{sys}$ = 5 MHz;<br>LIN communication running;<br>charge pump on (reverse polarity FET on), external low-side FET static on (Motor Break mode);<br>VDDEXT on; all other modules set to power down;<br>$V_S$ = 13.5 V | P_1.3.6 |
| Current consumption in Sleep mode | $I_{Sleep}$ | – | 30 | 35 | µA | System in Sleep mode, microcontroller not powered, wake-capable via LIN and MON; MON connected to VS or GND; GPIOs open (no loads) or connected to GND:<br>-40°C ≤ $T_j$ ≤ 85°C;<br>$V_S$ = 5.5 V to 18 V [2] | P_1.3.3 |
| Current consumption in Sleep mode, extended range | $I_{Sleep\_extend}$ | – | 90 | 200 | µA | System in Sleep mode, microcontroller not powered, wake-capable via LIN and MON; MON connected to VS or GND; GPIOs open (no loads) or connected to GND:<br>-40°C ≤ $T_j$ ≤ 150°C;<br>$V_S$ = 5.5 V to 18 V [2] | P_1.3.15 |
| Current consumption in Sleep mode | $I_{Sleep}$ | – | – | 33 | µA | System in Sleep mode, microcontroller not powered, wake-capable via LIN and MON; MON connected to VS or GND; GPIOs open (no loads) or connected to GND:<br>-40°C ≤ $T_j$ ≤ 40°C;<br>$V_S$ = 5.5 V to 18 V [2] | P_1.3.9 |

**Table 19 Electrical characteristics** (cont'd)

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Current consumption in Sleep mode with cyclic wake | $I_{Cyclic}$ | – | – | 110 | µA | -40°C ≤ $T_j$ ≤ 85°C;<br>$V_S$ = 5.5 V to 18 V;<br>$t_{Cyclic\_ON}$ = 4 ms;<br>$t_{Cyclic\_OFF}$ = 2048 ms 2) | P_1.3.4 |
| Current consumption in Stop mode | $I_{Stop}$ | – | 110 | 160 | µA | System in Stop mode, microcontroller not clocked, wake-capable via LIN and MON; MON connected to VS or GND; GPIOs open (no loads) or connected to GND;<br>-40°C ≤ $T_j$ ≤ 85°C;<br>$V_S$ = 5.5 V to 18 V | P_1.3.10 |
| Current consumption in Stop mode, extended temperature range 1 | $I_{Stop\_extend}$ | – | 600 | 1800 | µA | System in Stop mode, microcontroller not clocked, wake-capable via LIN and MON; MON connected to VS or GND; GPIOs open (no loads) or connected to GND;<br>-40°C ≤ $T_j$ ≤ 150°C;<br>$V_S$ = 5.5 V to 18 V | P_1.3.20 |

1) Current on $V_S$, ADC1/2 active, timer running, LIN active (recessive).

2) Incl. leakage currents from VBAT_SENSE, VDH, VSD and MON.

*Note: Within the functional range, the IC operates as described in the circuit description. The electrical characteristics are specified under the conditions noted in the related electrical characteristics table.*

### 29.1.4 Thermal resistance

**Table 20 Thermal resistance**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Junction to soldering point | $R_{thJSP}$ | – | 6 | – | K/W | 1) Measured to exposed pad | P_1.4.1 |
| Junction to ambient | $R_{thJA}$ | – | 33 | – | K/W | 1)2) | P_1.4.2 |
| Junction to top | $\Psi_{JTOP\ 2s2p}$ | – | 8 | – | K/W | 1)2) | P_1.4.3 |

1) Not subject to production test, specified by design.

2) According to Jedec JESD51-2,-5,-7 with natural convection on an FR4 2s2p board. Board: 76.2 × 114.3 × 1.5 $mm^3$ with two inner copper layers (35 µm strong), with thermal dissipation via array under the exposed pad contacting the first inner copper layer and 300 $mm^2$ of cooling area on the bottom layer (70 µm).

### 29.1.5 Timing characteristics

The transition times between the system modes are specified here. Generally, the timings are defined from the time when the corresponding bits in register PMCON0 are set until the sequence is terminated.

**Table 21 System timing[1)]**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Wake-up time when running on battery | $t_{start}$ | – | – | 3 | ms | Battery ramp-up time until the start of code execution | P_1.5.6 |
| Wake-up time when running on battery | $t_{startSW}$ | – | – | 1.5 | ms | Battery ramp-up time until the MCU reset is released; $V_S$ > 3 V and RESET = 1 | P_1.5.1 |
| Time to exit sleep | $t_{sleep\ -\ exit}$ | – | – | 1.5 | ms | Rising/falling edge of any wake-up signal (LIN, MON) until the MCU reset is released; | P_1.5.2 |
| Time to enter sleep | $t_{sleep\ -\ entry}$ | – | – | 330 | µs | 2) | P_1.5.3 |

1) Not subject to production test, specified by design.

2) Wake events during sleep entry are stored and lead to wake-up after Sleep mode is reached.

## 29.2 Power management unit (PMU)

This chapter includes all electrical characteristics of the power management unit.

### 29.2.1 PMU I/O supply (VDDP) parameters

This chapter describes electrical parameters which are observable on the SoC level. The pad-supply VDDP and the transition times between the system modes are specified in the following table.

**Table 22 Electrical characteristics**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Specified output current | $I_{VDDP}$ | 0 | – | 50 | mA | 1) | P_2.1.1 |
| Specified output current | $I_{VDDP}$ | 0 | – | 30 | mA | 1)2) | P_2.1.22 |
| Required decoupling capacitance | $C_{VDDP1}$ | 0.47 | – | 2.2 | µF | 3)4)5) ESR < 1 Ω | P_2.1.2 |
| Required buffer capacitance for stability (load jumps) | $C_{VDDP2}$ | 1 | – | 2.2 | µF | 3)4)5) | P_2.1.20 |
| Output voltage including line and load regulation in Active mode | $V_{DDPOUT}$ | 4.9 | 5.0 | 5.1 | V | 6) $I_{load}$ < 90 mA; $V_S$ > 5.5 V | P_2.1.3 |
| Output voltage including line and load regulation in Active mode | $V_{DDPOUT}$ | 4.9 | 5.0 | 5.1 | V | 2)6) $I_{load}$ < 70 mA; $V_S$ > 5.5 V | P_2.1.23 |
| Output voltage including line and load regulation in Stop mode | $V_{DDPOUTSTOP}$ | 4.5 | 5.0 | 5.5 | V | 6) $I_{load}$ is only internal; $V_S$ > 5.5 V | P_2.1.21 |
| Output drop in Active mode | $V_{SVDDPout}$ | – | 50 | 400 | mV | $I_{VDDP}$ = 30 mA7); 3.5 V < $V_S$ < 5.0 V | P_2.1.4 |
| Load regulation in Active mode | $V_{VDDPLOR}$ | -50 | – | 50 | mV | 2 mA … 90 mA; $C$ = 570 nF | P_2.1.5 |
| Line regulation in Active mode | $V_{VDDPLIR}$ | -50 | – | 50 | mV | $V_S$ = 5.5 V … 28 V | P_2.1.6 |
| Overvoltage detection | $V_{DDPOV}$ | 5.14 | – | 5.4 | V | $V_S$ > 5.5 V; Overvoltage leads to SUPPLY_NMI | P_2.1.7 |
| Overvoltage detection filter time | $t_{FILT\_VDDPOV}$ | – | 735 | – | µs | 3)8) | P_2.1.24 |
| Voltage OK detection threshold | $V_{DDPOK}$ | – | 3 | – | V | 3) | P_2.1.25 |
| Voltage stable detection range9) | $\Delta V_{DDPSTB}$ | -220 | – | 220 | mV | 3) | P_2.1.26 |
| Undervoltage reset | $V_{DDPUV}$ | 2.5 | 2.6 | 2.7 | V | – | P_2.1.8 |
| Overcurrent diagnostic | $I_{VDDPOC}$ | 91 | – | 220 | mA | – | P_2.1.9 |

**Table 22 Electrical characteristics** (cont'd)

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Overcurrent diagnostic filter time | $t_{FILT\_VDDPOC}$ | – | 27 | – | µs | 3)8) | P_2.1.27 |
| Overcurrent diagnostic shutdown time | $t_{FILT\_VDDPOC\_SD}$ | – | 100 | – | µs | 3)8)10) | P_2.1.28 |

1) Specified output current for port supply and additional other external loads, already excluding VDDC current.
2) This use case applies when the output current on VDDEXT does not exceed 40 mA.
3) Not subject to production test, specified by design.
4) Ceramic capacitor.
5) Ranges of P_2.1.2 and P_2.1.20 can be added to one ceramic capacitor with ESR < 1 Ω.
6) Load current includes internal supply.
7) Output drop for IVDDP without internal supply current.
8) This filter time is derived from the time base $t_{LP\_CLK} = 1 / f_{LP\_CLK}$.
9) The absolute voltage value is the sum of parameters $V_{DDP} + \Delta V_{DDPSTB}$.
10) When $t_{FILT\_VDDCOC\_SD}$ is passed and the overcurrent condition is still present, the device will enter Sleep mode.

## 29.2.2 PMU core supply (VDDC) parameters

This chapter describes electrical parameters which are observable on the SoC level. The core-supply VDDC and the transition times between the system modes are specified in the following table.

**Table 23 Electrical characteristics**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Required decoupling capacitance | $C_{VDDC1}$ | 0.1 | – | 1 | µF | 1)2)3) ESR < 1 Ω | P_2.2.1 |
| Required buffer capacitance for stability (load jumps) | $C_{VDDC2}$ | 0.33 | – | 1 | µF | 2)3) | P_2.2.17 |
| Output voltage including line regulation in Active mode | $V_{DDCOUT}$ | 1.44 | 1.5 | 1.56 | V | $I_{load}$ < 40 mA | P_2.2.2 |
| Reduced output voltage including line regulation in Stop mode | $V_{DDCOUT\_Stop\_Red}$ | 0.95 | 1.1 | 1.3 | V | With internal VDDC load only: $I_{load\_internal}$ < 1.5 mA | P_2.2.23 |
| Load regulation in Active mode | $V_{DDCLOR}$ | -50 | – | 50 | mV | 2 mA … 40 mA; $C$ = 430 nF | P_2.2.3 |
| Line regulation in Active mode | $V_{DDCLIR}$ | -25 | – | 25 | mV | $V_{DDP}$ = 2.5 V … 5.5 V | P_2.2.4 |
| Overvoltage detection | $V_{DDCOV}$ | 1.59 | 1.62 | 1.68 | V | Overvoltage leads to SUPPLY_NMI | P_2.2.5 |
| Overvoltage detection filter time | $t_{FILT\_VDDCOV}$ | – | 735 | – | µs | 1)4) | P_2.2.18 |
| Voltage OK detection range[5)] | $\Delta V_{DDCOK}$ | -280 | – | 280 | mV | 1) | P_2.2.19 |
| Voltage stable detection range[6)] | $\Delta V_{DDCSTB}$ | -110 | – | 110 | mV | 1) | P_2.2.20 |
| Undervoltage reset | $V_{DDVUV}$ | 1.136 | 1.20 | 1.264 | V | – | P_2.2.6 |
| Overcurrent diagnostic | $I_{VDDCOC}$ | 45 | – | 100 | mA | – | P_2.2.7 |
| Overcurrent diagnostic filter time | $t_{FILT\_VDDCOC}$ | – | 27 | – | µs | 1)4) | P_2.2.21 |
| Overcurrent diagnostic shutdown time | $t_{FILT\_VDDCOC\_SD}$ | – | 290 | – | µs | 1)4)7) | P_2.2.22 |

1) Not subject to production test, specified by design.
2) Ceramic capacitor.
3) Ranges of P_2.2.1 and P_2.2.17 can be added to one ceramic capacitor with ESR < 1 Ω.
4) This filter time is derived from the time base $t_{LP\_CLK} = 1 / f_{LP\_CLK}$.
5) This absolute voltage value is the sum of parameters $V_{DDC} + \Delta V_{DDCSTB}$.
6) This absolute voltage value is the sum of parameters $V_{DDC} + \Delta V_{DDCOK}$.
7) When $t_{FILT\_VDDCOC\_SD}$ is passed and the overcurrent condition is still present the device will enter Sleep mode.

### 29.2.3 VDDEXT voltage regulator (5.0 V) parameters

**Table 24 Electrical characteristics**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Specified output current | $I_{VDDEXT}$ | 0 | – | 20 | mA | – | P_2.3.1 |
| Specified output current | $I_{VDDEXT}$ | 0 | – | 40 | mA | 1) | P_2.3.21 |
| Required decoupling capacitance | $C_{VDDEXT1}$ | 0.1 | – | 2.2 | µF | 2)3)4) ESR < 1 Ω | P_2.3.22 |
| Required buffer capacitance for stability (load jumps) | $C_{VDDEXT2}$ | 1 | – | 2.2 | µF | 2)3)4) | P_2.3.20 |
| Output voltage including line and load regulation | $V_{DDEXT}$ | 4.9 | 5.0 | 5.1 | V | 4) $I_{load}$ < 20 mA; $V_S$ > 5.5 V | P_2.3.3 |
| Output voltage including line and load regulation | $V_{DDEXT}$ | 4.8 | 5.0 | 5.2 | V | $I_{load}$ < 40 mA; $V_S$ > 5.5 V | P_2.3.23 |
| Output drop in Active mode | $V_S$-$V_{DDEXT}$ | | 50 | 300 | mV | 4) $I_{load}$ < 20 mA; 3 V < $V_S$ < 5.0 V | P_2.3.4 |
| Output drop in Active mode | $V_S$-$V_{DDEXT}$ | | – | 400 | mV | $I_{load}$ < 40 mA; 3 V < $V_S$ < 5.0 V | P_2.3.14 |
| Load regulation in Active mode | $V_{DDEXTLOR}$ | -50 | – | 50 | mV | 2 mA … 40 mA; $C$ = 200 nF | P_2.3.5 |
| Line regulation in Active mode | $V_{VDDEXTLIR}$ | -50 | – | 50 | mV | $V_S$ = 5.5 V … 28 V | P_2.3.6 |
| Power supply ripple rejection in Active mode | $P_{SSRVDDEXT}$ | 50 | – | – | dB | 4) $V_S$ = 13.5 V; $f$ = 0 kHz … 1 kHz; $V_r$ = 2 Vpp | P_2.3.7 |
| Overvoltage detection | $V_{VDDEXTOV}$ | 5.18 | – | 5.4 | V | $V_S$ > 5.5 V | P_2.3.8 |
| Overvoltage detection filter time | $t_{FILT\_VDDEXTOV}$ | – | 735 | – | µs | 4)5) | P_2.3.24 |
| Voltage OK detection threshold | $V_{VDDEXTOK}$ | – | 3 | – | V | 4) | P_2.3.25 |
| Voltage stable detection range6) | $\Delta V_{VDDEXTSTB}$ | -220 | – | 220 | mV | 4) | P_2.3.26 |
| Undervoltage trigger | $V_{VDDEXTUV}$ | 2.6 | 2.8 | 3.0 | V | 7) | P_2.3.9 |
| Overcurrent diagnostic | $I_{VDDEXTOC}$ | 50 | – | 160 | mA | – | P_2.3.10 |
| Overcurrent diagnostic filter time | $t_{FILT\_VDDEXTOC}$ | – | 27 | – | µs | 4)5) | P_2.3.27 |
| Overcurrent diagnostic shutdown time | $t_{FILT\_VDDEXTOC\_SD}$ | – | 100 | – | µs | 4)5) | P_2.3.28 |

1) This use case requires the reduced utilization of VDDP output current by 20 mA, see P_2.1.22.
2) Ceramic capacitor.
3) Ranges of P_2.3.22 and P_2.3.20 can be added to one ceramic capacitor with ESR < 1 Ω.
4) Not subject to production test, specified by design.
5) This filter time is derived from the time base $t_{LP\_CLK} = 1 / f_{LP\_CLK}$.
6) The absolute voltage value is the sum of parameters $V_{DDEXT} + \Delta V_{DDEXTSTB}$.
7) When the undervoltage condition is met, the VDDEXT_CTRL.bit.SHORT bit is set.

### 29.2.4 VPRE voltage regulator (PMU subblock) parameters

The PMU VPRE regulator acts as a supply for the VDDP and VDDEXT voltage regulators.

**Table 25 Functional range**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Specified output current | $I_{VPRE}$ | – | – | 110 | mA | 1) | P_2.4.1 |

1) Not subject to production test, specified by design.

#### 29.2.4.1 Load-sharing scenario for the VPRE regulator

The figure below shows the load-sharing scenario for VPRE regulator.

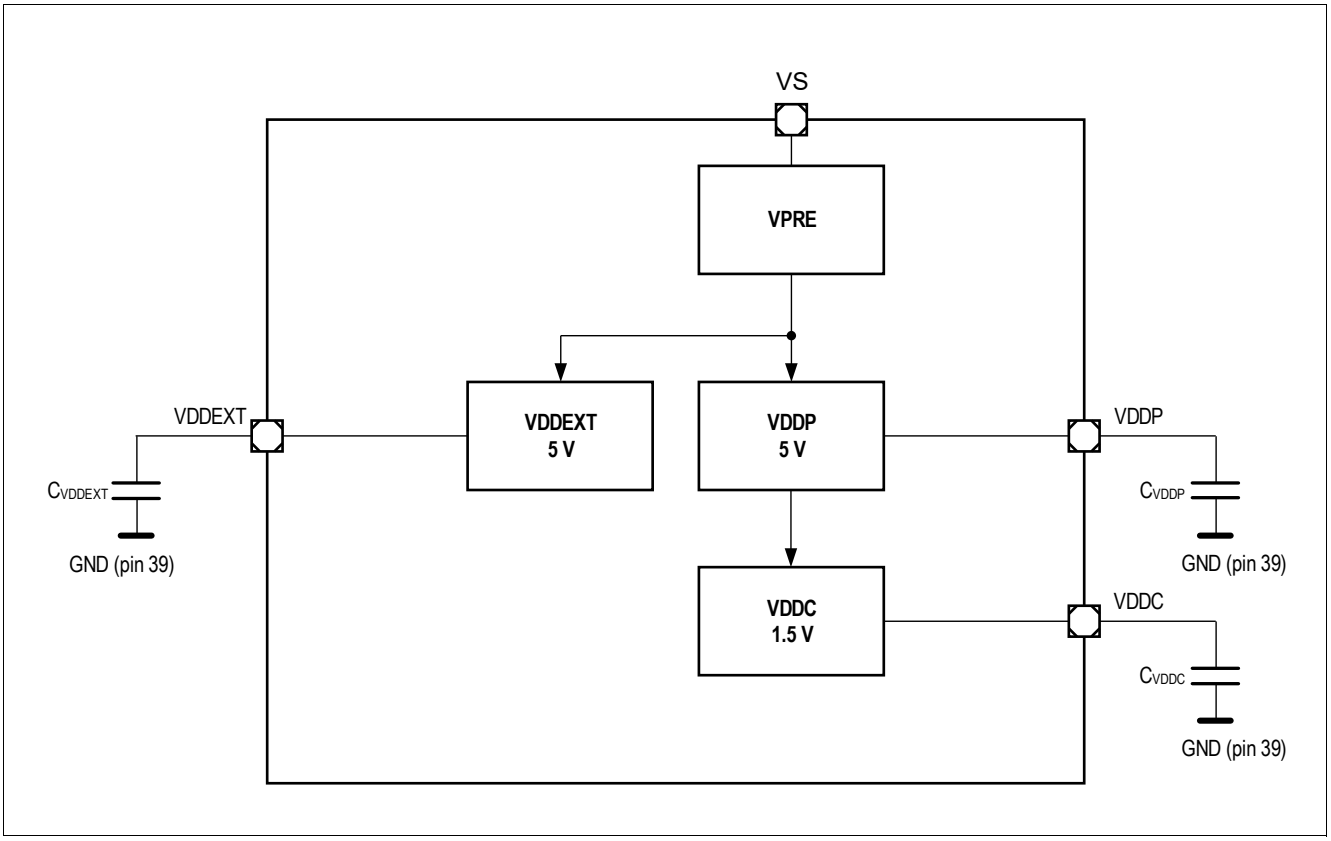


**Figure 31 Load-sharing scenario for the VPRE regulator**

### 29.2.5 Power-down voltage regulator (PMU subblock) parameters

The PMU power-down voltage regulator consists of two subblocks:

- Power-down preregulator: VDD5VPD
- Power-down core regulator: VDD1V5_PD (Supply used for the GPUDATAxy registers)

Both regulators are used as purely internal supplies. The following table contains all relevant parameters.

**Table 26 Functional range**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **VDD1V5_PD** | | | | | | | |
| Power-on reset threshold | $V_{DD1V5\_PD\_RSTTH}$ | 1.2 | – | 1.5 | V | 1) | P_2.5.1 |

1) Not subject to production test, specified by design.

## 29.3 System clocks

### 29.3.1 Parameters of oscillators and PLLs

**Table 27 Electrical characteristics of the system clocks**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **PMU oscillators (power management unit)** | | | | | | | |
| Frequency of LP_CLK | $f_{LP\_CLK}$ | 14 | 18 | 22 | MHz | This clock is used during startup and can be used when the PLL fails. | P_3.1.1 |
| Frequency of LP_CLK2 | $f_{LP\_CLK2}$ | 70 | 100 | 130 | kHz | This clock is used for cyclic wakes. | P_3.1.2 |
| **CGU oscillator (clock generation unit microcontroller)** | | | | | | | |
| Short-term frequency deviation[1)] | $f_{TRIMST}$ | -0.4 | – | 0.4 | % | [2)3)] Within any 10 ms, e.g., after synchronization to a LIN frame. (The PLL settings must not change in these 10 ms.) | P_3.1.3 |
| Absolute accuracy | $f_{TRIMABSA}$ | -1.5 | – | 1.5 | % | Including temperature and lifetime deviation | P_3.1.4 |
| CGU-OSC start-up time | $t_{OSC}$ | – | – | 10 | µs | [3)] Start-up time OSC from Sleep mode, power supply stable | P_3.1.5 |
| **PLL (clock generation unit microcontroller) [3)]** | | | | | | | |
| VCO frequency range mode 0 | $f_{VCO-0}$ | 48 | – | 112 | MHz | VCOSEL = ”0” | P_3.1.6 |
| VCO frequency range mode 1 | $f_{VCO-1}$ | 96 | – | 160 | MHz | VCOSEL = ”1” | P_3.1.7 |
| Input frequency range | $f_{OSC}$ | 4 | – | 16 | MHz | – | P_3.1.8 |
| XTAL1 input frequency range | $f_{OSC}$ | 4 | – | 16 | MHz | – | P_3.1.9 |
| Output frequency range | $f_{PLL}$ | 0.04687 | – | 80 | MHz | – | P_3.1.10 |
| Free-running frequency mode 0 | $f_{VCOfree\_0}$ | – | – | 38 | MHz | VCOSEL = ”0” | P_3.1.11 |
| Free-running frequency mode 1 | $f_{VCOfree\_1}$ | – | – | 76 | MHz | VCOSEL = ”1” | P_3.1.12 |
| Input clock high/low time | $t_{high/low}$ | 10 | – | – | ns | – | P_3.1.13 |
| Peak period jitter | $t_{jp}$ | -500 | – | 500 | ps | [4)] for K = 1 | P_3.1.14 |

**Table 27 Electrical characteristics of the system clocks** (cont'd)

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Accumulated jitter | jacc | – | – | 5 | ns | [4] for K = 1 | P_3.1.15 |
| Lock-in time | $t_L$ | – | – | 200 | µs | – | P_3.1.16 |

1) The typical oscillator frequency is 5 MHz.

2) $V_{DDC}$ = 1.5 V, $T_j$ = 25°C.

3) Not subject to production test, specified by design.

4) This parameter is valid for PLL operation with an external clock source and thus reflects the real PLL performance.

## 29.3.2 External clock parameters XTAL1, XTAL2

**Table 28 Functional range**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).[1)]

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Input voltage range limits for signal on XTAL1 | $V_{IX1\_SR}$ | -1.7 + $V_{DDC}$ | – | 1.7 | V | [2)] | P_3.2.1 |
| Input voltage (amplitude) on XTAL1 | $V_{AX1\_SR}$ | 0.3 × $V_{DDC}$ | – | – | V | [3)] Peak-to-peak voltage | P_3.2.2 |
| XTAL1 input current | $I_{IL}$ | – | – | ±20 | µA | 0 V < $V_{IN}$ < $V_{DDI}$ | P_3.2.3 |
| Oscillator frequency | $f_{OSC}$ | 4 | – | 24 | MHz | Clock signal | P_3.2.4 |
| Oscillator frequency | $f_{OSC}$ | 4 | – | 16 | MHz | Crystal or resonator | P_3.2.5 |
| High time | $t_1$ | 6 | – | – | ns | – | P_3.2.6 |
| Low time | $t_2$ | 6 | – | – | ns | – | P_3.2.7 |
| Rise time | $t_3$ | – | 8 | 8 | ns | – | P_3.2.8 |
| Fall time | $t_4$ | – | 8 | 8 | ns | – | P_3.2.9 |

1) This parameter table is not subject to production test, specified by design.

2) Overload conditions must not occur on pin XTAL1.

3) The amplitude voltage $V_{AX1}$ refers to the offset voltage $V_{OFF}$. This offset voltage must be stable during the operation and the resulting voltage peaks must remain within the limits defined by $V_{IX1}$.

## 29.4 Flash memory

This chapter includes the parameters for the 256 kByte embedded flash module.

### 29.4.1 Flash parameters

**Table 29 Flash characteristics[1)]**

$V_S$ = 3.0 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Programming time per 128 byte page | $t_{PR}$ | – | 3[2)] | 3.5 | ms | [3)] 3 V ≤ $V_S$ ≤ 28 V | P_4.1.1 |
| Erase time per sector or page | $t_{ER}$ | – | 4[2)] | 4.5 | ms | [3)] 3 V ≤ $V_S$ ≤ 28 V | P_4.1.2 |
| Data retention time | $t_{RET}$ | 20 | – | – | year | 1,000 erase/program cycles | P_4.1.3 |
| Data retention time | $t_{RET}$ | 50 | – | – | year | 1,000 erase/program cycles<br>$T_j$ = 30°C [4)] | P_4.1.9 |
| Flash erase endurance for pages in user sectors | $N_{ER}$ | 30 | – | – | kilocycles | Data retention time 5 years | P_4.1.4 |
| Flash erase endurance for security pages | $N_{SEC}$ | 10 | – | – | cycles | [5)] Data retention time 20 years | P_4.1.5 |
| Drain disturb limit | $N_{DD}$ | 32 | – | – | kilocycles | [6)] | P_4.1.6 |

1) Not subject to production test, specified by design.

2) Programming and erase times depend on the internal flash clock source. The control state machine needs a few system clock cycles. The requirement is only relevant for extremely low system frequencies.

3) While the flash memory is being programmed or erased, flash read operation is not possible to be performed.

4) Determined by extrapolating of lifetime tests.

5) $T_j$ = 25°C.

6) This parameter limits the number of subsequent programming operations within a physical sector without a given page in this sector being (re-)programmed. The drain disturb limit is applicable if wordline erase is used repeatedly. For normal sector erase/program cycles, this limit will not be violated. For data sectors, the integrated EEPROM emulation firmware routines handle this limit automatically. For wordline erases in code sectors (without EEPROM emulation), it is recommended to execute a software-based refresh, which use the integrated NVMBRNG random number generator to statistically start a refresh.

## 29.5 Parallel ports (GPIO)

### 29.5.1 Description of the keep and force currents

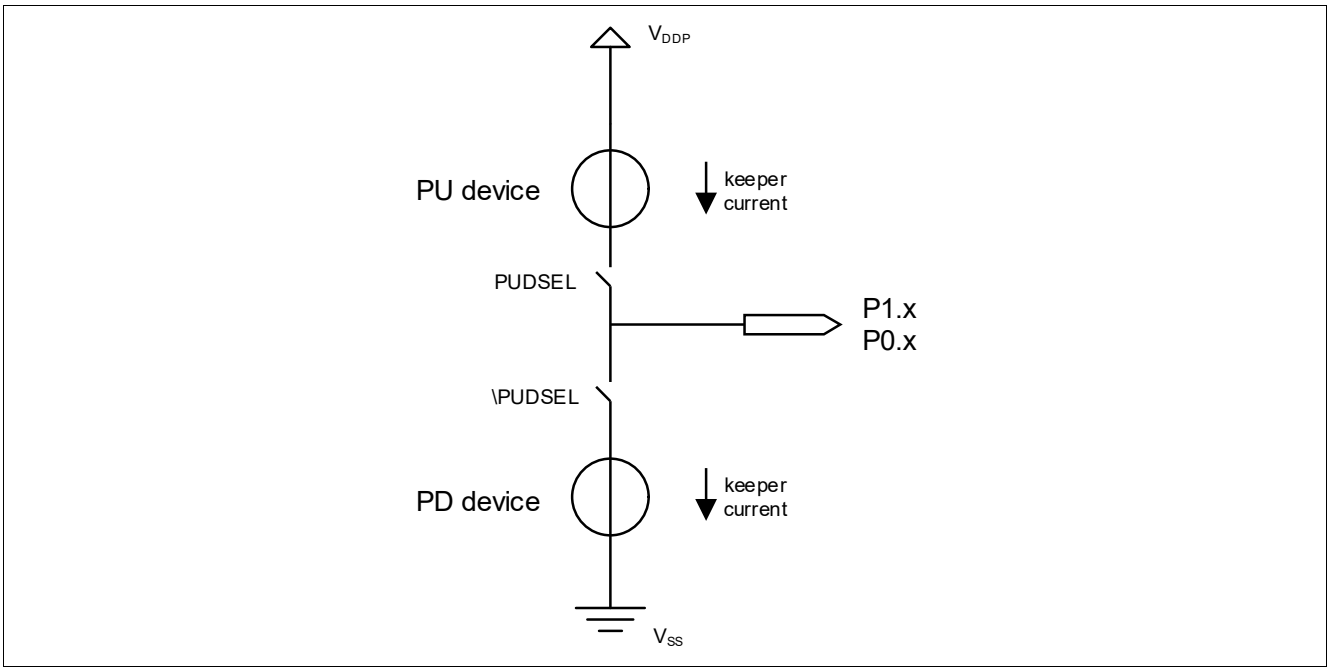


**Figure 32 Pull-up/down device**

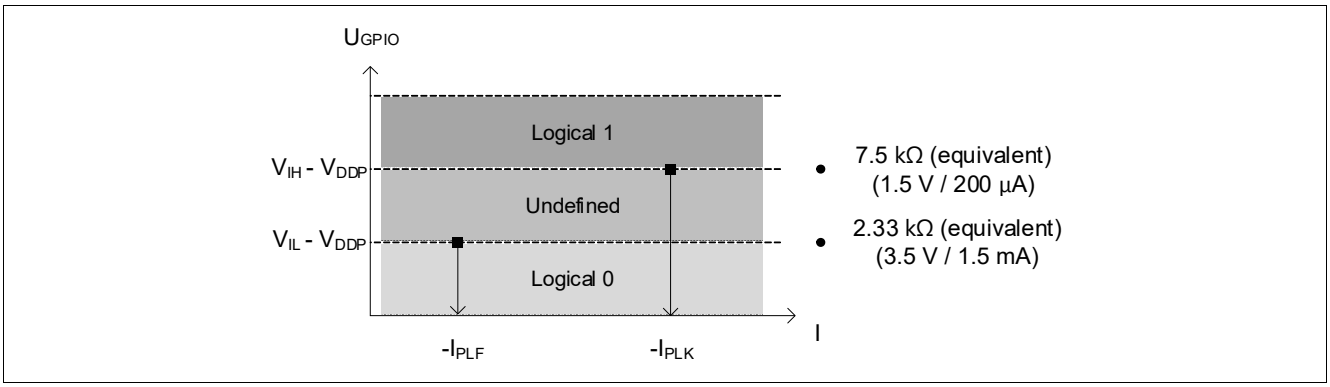


**Figure 33 Pull-up keep and force currents**

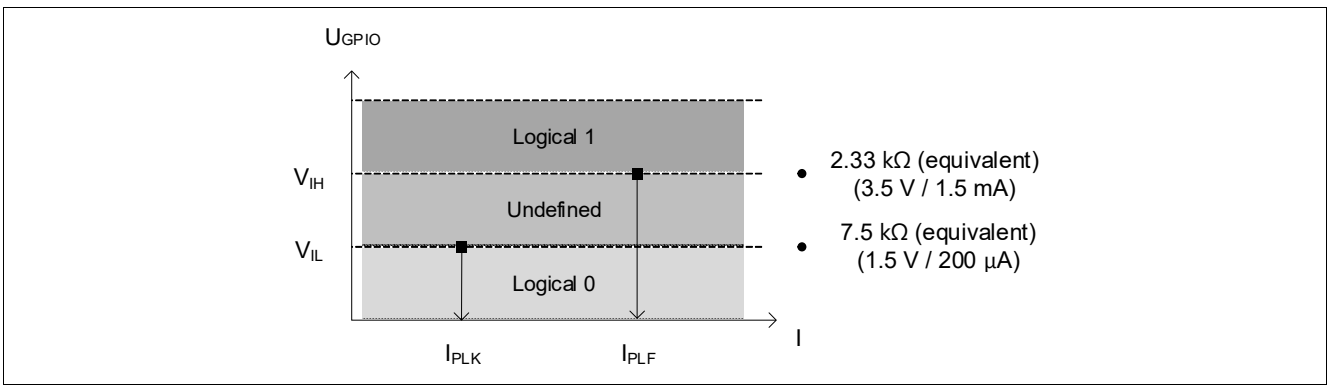


**Figure 34 Pull-down keep and force currents**

## 29.5.2 DC parameters of port 0, port 1, TMS, and reset

*Note: Operating conditions apply.*
*Keeping signal levels within the limits specified in this table ensures operation without overload conditions. For signal levels outside these specifications, also refer to the specification of the maximum allowed current that can be taken out of VDDP.*

**Table 30 Current limits for port output drivers[1)]**

| Port output driver mode | Maximum output current ($I_{OLmax}$, - $I_{OHmax}$) | | Maximum output current ($I_{OLnom}$, - $I_{OHnom}$) | | Number |
|---|---|---|---|---|---|
| | $V_{DDP} \geq 4.5$ V | 2.6 V < $V_{DDP}$ < 4.5 V | $V_{DDP} \geq 4.5$ V | 2.6 V < $V_{DDP}$ < 4.5 V | |
| Strong driver[2)] | 5 mA | 3 mA | 1.6 mA | 1.0 mA | P_5.1.15 |
| Medium driver[3)] | 3 mA | 1.8 mA | 1.0 mA | 0.8 mA | P_5.1.1 |
| Weak driver[3)] | 0.5 mA | 0.3 mA | 0.25 mA | 0.15 mA | P_5.1.2 |

1) Not subject to production test, specified by design.
2) Not available for port pins P0.4, P1.0, P1.1, and P1.2.
3) All P0.x and P1.x pins.

**Table 31 DC characteristics of port0 and port1**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Input hysteresis | $HYS_{P0\_P1}$ | 0.11 × $V_{DDP}$ | – | – | V | [1)] Series resistance = 0 Ω; 4.5 V ≤ $V_{DDP}$ ≤ 5.5 V | P_5.1.5 |
| Input hysteresis | $HYS_{P0\_P1\_exend}$ | – | 0.09 × $V_{DDP}$ | – | V | [1)] Series resistance = 0 Ω; 2.6 V ≤ $V_{DDP}$ ≤ 4.5 V | P_5.1.16 |
| Input low voltage | $V_{IL}$ | -0.3 | – | 0.3 × $V_{DDP}$ | V | [2)] 4.5 V ≤ $V_{DDP}$ ≤ 5.5 V | P_5.1.3 |
| Input low voltage | $V_{IL\_extend}$ | -0.3 | 0.42 × $V_{DDP}$ | – | V | [1)] 2.6 V ≤ $V_{DDP}$ ≤ 4.5 V | P_5.1.17 |
| Input high voltage | $V_{IH}$ | 0.7 × $V_{DDP}$ | – | $V_{DDP}$ + 0.3 | V | [2)] 4.5 V ≤ $V_{DDP}$ ≤ 5.5 V | P_5.1.4 |
| Input high voltage | $V_{IH\_extend}$ | – | 0.52 × $V_{DDP}$ | $V_{DDP}$ + 0.3 | V | [1)] 2.6 V ≤ $V_{DDP}$ ≤ 4.5 V | P_5.1.18 |
| Output low voltage | $V_{OL}$ | – | – | 1.0 | V | [3)4)] $I_{OL} \leq I_{OLmax}$ | P_5.1.6 |
| Output low voltage | $V_{OL}$ | – | – | 0.4 | V | [3)5)] $I_{OL} \leq I_{OLnom}$ | P_5.1.7 |
| Output high voltage | $V_{OH}$ | $V_{DDP}$ - 1.0 | – | – | V | [3)4)] $I_{OH} \geq I_{OHmax}$ | P_5.1.8 |
| Output high voltage | $V_{OH}$ | $V_{DDP}$ - 0.4 | – | – | V | [3)5)] $I_{OH} \geq I_{OHnom}$ | P_5.1.9 |
| Input leakage current | $I_{OZ\_extend1}$ | -500 | – | 500 | nA | -40°C ≤ $T_j$ ≤ 25°C, 0.45 V < $V_{IN}$ < $V_{DDP}$ | P_5.1.20 |
| Input leakage current | $I_{OZ1}$ | -5 | – | 5 | µA | [6)] 25°C < $T_J$ ≤ 85°C, 0.45 V < $V_{IN}$ < $V_{DDP}$ | P_5.1.10 |
| Input leakage current | $I_{OZ\_extend2}$ | -15 | – | 15 | µA | 85°C < $T_J$ ≤ 150°C, 0.45 V < $V_{IN}$ < $V_{DDP}$ | P_5.1.21 |

**Table 31 DC characteristics of port0 and port1** (cont'd)

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Pull level keep current | $I_{PLK}$ | -200 | – | 200 | µA | 7) $V_{PIN} \geq V_{IH}$ (up)<br>$V_{PIN} \leq V_{IL}$ (down) | P_5.1.12 |
| Pull level force current | $I_{PLF}$ | -1.5 | – | 1.5 | mA | 7) $V_{PIN} \leq V_{IL}$ (up)<br>$V_{PIN} \geq V_{IH}$ (down) | P_5.1.13 |
| Pin capacitance | $C_{IO}$ | – | – | 10 | pF | 1) | P_5.1.14 |
| **Reset pin timing** | | | | | | | |
| Reset pin input filter time | $t_{filt\_RESET}$ | – | 5 | – | µs | 1) | P_5.1.19 |

1) Not subject to production test, specified by design.

2) Tested at $V_{DDP}$ = 5 V, specified for 4.5 V < $V_{DDP}$ < 5.5 V.

3) The maximum deliverable output current of a port driver depends on the selected output driver mode. The limit for pin groups must be respected.

4) Tested at 4.9 V < $V_{DDP}$ < 5.1 V, $I_{OL}$ = 4 mA, $I_{OH}$ = -4 mA, specified for 4.5 V < $V_{DDP}$ < 5.5 V.

5) As a rule, with decreasing output current the output levels approach the respective supply level ($V_{OL}$→*GND*, $V_{OH}$→$V_{DDP}$). Tested at 4.9 V < $V_{DDP}$ < 5.1 V, $I_{OL}$ = 1 mA, $I_{OH}$ = -1 mA.

6) The given values are worst-case values. In production tests, this leakage current is only tested at 150°C; other values are ensured by correlation. For derating, please refer to the following descriptions:
Leakage derating depending on temperature ($T_J$ = junction temperature [°C]):
$I_{OZ} = 0.05 \times e^{(1.5 + 0.028 \times Tj)}$ [µA]. For example, at a temperature of 95°C, the resulting leakage current is 3.2 µA.
Leakage derating depending on the voltage level (DV = $V_{DDP}$ - $V_{PIN}$ [V]):
$I_{OZ} = I_{OZtempmax}$ - (1.6 × DV) [µA]
This voltage derating formula is an approximation which applies for the maximum temperature.

7) Keep current: Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level: $V_{PIN} \geq V_{IH}$ for a pull-up; $V_{PIN} \leq V_{IL}$ for a pull-down.
Force current: Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device: $V_{PIN} \leq V_{IL}$ for a pull-up; $V_{PIN} \geq V_{IH}$ for a pull-down.
These values apply to the fixed pull devices in dedicated pins and to the user-selectable pull devices in general-purpose IO pins.

### 29.5.3 DC parameters of port 2

These parameters apply to the IO voltage range 4.5 V ≤ $V_{DDP}$ ≤ 5.5 V.

*Note: Operating conditions apply.*
*Keeping signal levels within the limits specified in this table ensures operation without overload conditions. For signal levels outside these specifications, also refer to the specification of the overload current $I_{OV}$.*

**Table 32 DC characteristics of port 2**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Input low voltage | $V_{IL}$ | -0.3 | – | 0.3 × $V_{DDP}$ | V | 1) 4.5 V ≤ $V_{DDP}$ ≤ 5.5 V | P_5.2.1 |
| Input low voltage | $V_{IL\_extend}$ | -0.3 | 0.42 × $V_{DDP}$ | – | V | 2) 2.6 V ≤ $V_{DDP}$ ≤ 4.5 V | P_5.2.10 |
| Input high voltage | $V_{IH}$ | 0.7 × $V_{DDP}$ | – | $V_{DDP}$ + 0.3 | V | 1) 4.5 V ≤ $V_{DDP}$ ≤ 5.5 V | P_5.2.2 |
| Input high voltage | $V_{IH\_extend}$ | – | 0.52 × $V_{DDP}$ | $V_{DDP}$ + 0.3 | V | 2) 2.6 V ≤ $V_{DDP}$ ≤ 4.5 V | P_5.2.11 |
| Input hysteresis | $HYS_{P2}$ | 0.11 × $V_{DDP}$ | – | – | V | 2) Series resistance = 0 Ω; 4.5 V ≤ $V_{DDP}$ ≤ 5.5 V | P_5.2.3 |
| Input hysteresis | $HYS_{P2\_extend}$ | – | 0.09 × $V_{DDP}$ | – | V | 2) Series resistance = 0 Ω; 2.6 V ≤ $V_{DDP}$ < 4.5 V | P_5.2.12 |
| Input leakage current | $I_{OZ2}$ | -400 | – | 400 | nA | $T_j$ ≤ 85°C, 0 V < $V_{IN}$ < $V_{DDP}$ | P_5.2.4 |
| Pull-level keep current | $I_{PLK}$ | -30 | – | 30 | µA | 3) $V_{PIN}$ ≥ $V_{IH}$ (up) $V_{PIN}$ ≤ $V_{IL}$ (down) | P_5.2.5 |
| Pull-level force current | $I_{PLF}$ | -750 | – | 750 | µA | 3) $V_{PIN}$ ≤ $V_{IL}$ (up) $V_{PIN}$ ≥ $V_{IH}$ (down) | P_5.2.6 |
| Pin capacitance (digital inputs/outputs) | $C_{IO}$ | – | – | 10 | pF | 2) | P_5.2.7 |

1) Tested at $V_{DDP}$ = 5 V, specified for 4.5 V < $V_{DDP}$ < 5.5 V.
2) Not subject to production test, specified by design.
3) Keep current: Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level: $V_{PIN}$ ≥ $V_{IH}$ for a pull-up; $V_{PIN}$ ≤ $V_{IL}$ for a pull-down.
Force current: Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device: $V_{PIN}$ ≤ $V_{IL}$ for a pull-up; $V_{PIN}$ ≥ $V_{IH}$ for a pull-down.

## 29.6 LIN transceiver

### 29.6.1 Electrical characteristics

**Table 33 Electrical characteristics of the LIN transceiver**

$V_s$ = 5.5 V to 18 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **Bus receiver interface** | | | | | | | |
| Receiver threshold voltage, recessive to dominant edge | $V_{th\_dom}$ | 0.4 × $V_S$ | 0.45 × $V_S$ | 0.53 × $V_S$ | V | SAE J2602 | P_6.1.1 |
| Receiver dominant state | $V_{BUSdom}$ | -27 | – | 0.4 × $V_S$ | V | LIN spec 2.2 (par. 17) | P_6.1.2 |
| Receiver threshold voltage, dominant to recessive edge | $V_{th\_rec}$ | 0.47 × $V_S$ | 0.55 × $V_S$ | 0.6 × $V_S$ | V | SAE J2602 | P_6.1.3 |
| Receiver recessive state | $V_{BUSrec}$ | 0.6 × $V_S$ | – | 1.15 × $V_S$ | V | [1] LIN spec 2.2 (par. 18) | P_6.1.4 |
| Receiver center voltage | $V_{BUS\_CNT}$ | 0.475 × $V_S$ | 0.5 × $V_S$ | 0.525 × $V_S$ | V | [2] LIN spec 2.2 (par. 19) | P_6.1.5 |
| Receiver hysteresis | $V_{HYS}$ | 0.07 × $V_S$ | 0.12 × $V_S$ | 0.175 × $V_S$ | V | [3] LIN spec 2.2 (par. 20) | P_6.1.6 |
| Wake-up threshold voltage | $V_{BUS,wk}$ | 0.4 × $V_S$ | 0.5 × $V_S$ | 0.6 × $V_S$ | V | – | P_6.1.7 |
| Dominant time for bus wake-up (internal analog filter delay) | $t_{WK,bus}$ | 3 | – | 15 | µs | The overall dominant time for bus wake-up is the sum of $t_{WK,bus}$ and the adjustable digital filter time. The digital filter time can be adjusted by setting the PMU.CNF_WAKE_FILTER.CNF_LIN_FT register | P_6.1.8 |
| **Bus transmitter interface** | | | | | | | |
| Bus recessive output voltage | $V_{BUS,ro}$ | 0.8 × $V_S$ | – | $V_S$ | V | $V_{TxD}$ = high level | P_6.1.9 |
| Bus dominant output voltage | $V_{BUS,do}$ | – | – | 0.22 × $V_S$ | V | Driver dominant voltage $R_L$ = 500 Ω | P_6.1.78 |

**Table 33 Electrical characteristics of the LIN transceiver** (cont'd)

$V_S$ = 5.5 V to 18 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Bus short circuit current | $I_{BUS,sc}$ | 40 | 100 | 150 | mA | Current limitation for driver-dominant state driver on $V_{BUS}$ = 18 V; LIN spec 2.2 (par. 12) | P_6.1.10 |
| Bus short circuit filter time | $t_{BUS,sc}$ | – | 5 | – | µs | [6] The overall bus short circuit filter time is the sum of $t_{BUS,sc}$ and the digital filter time. The digital filter time is 4 µs (typ.) | P_6.1.71 |
| Leakage current (loss of ground) | $I_{BUS\_NO\_GND}$ | -1000 | -450 | 1000 | µA | $V_S$ = 12 V; 0 < $V_{BUS}$ < 18 V; LIN spec 2.2 (par. 15) | P_6.1.11 |
| Leakage current | $I_{BUS\_NO\_BAT}$ | – | 10 | 20 | µA | $V_S$ = 0 V; $V_{BUS}$ = 18 V; LIN spec 2.2 (par. 16) | P_6.1.12 |
| Leakage current | $I_{BUS\_PAS\_dom}$ | -1 | – | – | mA | $V_S$ = 18 V; $V_{BUS}$ = 0 V; LIN spec 2.2 (par. 13) | P_6.1.13 |
| Leakage current | $I_{BUS\_PAS\_rec}$ | – | – | 20 | µA | $V_S$ = 8 V; $V_{BUS}$ = 18 V; LIN spec 2.2 (par. 14) | P_6.1.14 |
| Bus pull-up resistance | $R_{BUS}$ | 20 | 30 | 47 | kΩ | Normal mode, LIN spec 2.2 (par. 26) | P_6.1.15 |
| **AC characteristics - transceiver Normal Slope mode** | | | | | | | |
| Propagation delay bus dominant to RxD LOW | $t_{d(L),R}$ | 0.1 | – | 6 | µs | LIN spec 2.2 (par. 31) | P_6.1.16 |
| Propagation delay bus recessive to RxD HIGH | $t_{d(H),R}$ | 0.1 | – | 6 | µs | LIN spec 2.2 (par. 31) | P_6.1.17 |
| Receiver delay symmetry | $t_{sym,R}$ | -2 | – | 2 | µs | $t_{sym,R} = t_{d(L),R} - t_{d(H),R}$; LIN spec 2.2 (par. 32) | P_6.1.18 |
| Duty cycle D1 Normal Slope mode (for worst case at 20 kbit/s) | $t_{duty1}$ | 0.396 | – | – | | [4] Duty cycle D1 $TH_{Rec}(max) = 0.744 \times V_S$; $TH_{Dom}(max) = 0.581 \times V_S$; $V_S$ = 5.5 V … 18 V; $t_{bit}$ = 50 µs; D1 = $t_{bus\_rec(min)}$ / 2 $t_{bit}$; LIN spec 2.2 (par. 27) | P_6.1.19 |
| Duty cycle D2 Normal Slope mode (for worst case at 20 kbit/s) | $t_{duty2}$ | – | – | 0.581 | | [4] Duty cycle D2 $TH_{Rec}(min) = 0.422 \times V_S$; $TH_{Dom}(min) = 0.284 \times V_S$; $V_S$ = 5.5 V … 18 V; $t_{bit}$ = 50 µs; D2 = $t_{bus\_rec(max)}$ / 2 $t_{bit}$; LIN spec 2.2 (par. 28) | P_6.1.20 |

**Table 33 Electrical characteristics of the LIN transceiver** (cont'd)

$V_s$ = 5.5 V to 18 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **AC characteristics - transceiver Low Slope mode** | | | | | | | |
| Propagation delay bus dominant to RxD LOW | $t_{d(L),R}$ | 0.1 | – | 6 | µs | LIN spec 2.2 (par. 31) | P_6.1.21 |
| Propagation delay bus recessive to RxD HIGH | $t_{d(H),R}$ | 0.1 | – | 6 | µs | LIN spec 2.2 (par. 31) | P_6.1.22 |
| Receiver delay symmetry | $t_{sym,R}$ | -2 | – | 2 | µs | $t_{sym,R} = t_{d(L),R} - t_{d(H),R}$; LIN spec 2.2 (par. 32) | P_6.1.23 |
| Duty cycle D3 (for worst case at 10.4 kbit/s) | $t_{duty1}$ | 0.417 | – | – | | [4] Duty cycle D3 $TH_{Rec}(max) = 0.778 \times V_S$; $TH_{Dom}(max) = 0.616 \times V_S$; $V_S$ = 5.5 V … 18 V; $t_{bit}$ = 96 µs; D3 = $t_{bus\_rec(min)}$ / 2 $t_{bit}$; LIN spec 2.2 (par. 29) | P_6.1.24 |
| Duty cycle D4 (for worst case at 10.4 kbit/s) | $t_{duty2}$ | – | – | 0.590 | | [4] Duty cycle D4 $TH_{Rec}(min) = 0.389 \times V_S$; $TH_{Dom}(min) = 0.251 \times V_S$; $V_S$ = 5.5 V … 18 V; $t_{bit}$ = 96 µs; D4 = $t_{bus\_rec(max)}$ / 2 $t_{bit}$; LIN spec 2.2 (par. 30) | P_6.1.25 |
| **AC characteristics - transceiver Fast Slope mode** | | | | | | | |
| Propagation delay bus dominant to RxD LOW | $t_{d(L),R}$ | 0.1 | – | 6 | µs | – | P_6.1.26 |
| Propagation delay bus recessive to RxD HIGH | $t_{d(H),R}$ | 0.1 | – | 6 | µs | – | P_6.1.27 |
| Receiver delay symmetry | $t_{sym,R}$ | -1.5 | – | 1.5 | µs | $t_{sym,R} = t_{d(L),R} - t_{d(H),R}$ | P_6.1.28 |
| **AC characteristics - Flash mode** | | | | | | | |
| Propagation delay bus dominant to RxD LOW | $t_{d(L),R}$ | 0.1 | – | 6 | µs | – | P_6.1.31 |
| Propagation delay bus recessive to RxD HIGH | $t_{d(H),R}$ | 0.1 | – | 6 | µs | – | P_6.1.32 |
| Receiver delay symmetry | $t_{sym,R}$ | -1.0 | – | 1.5 | µs | $t_{sym,R} = t_{d(L),R} - t_{d(H),R}$ | P_6.1.33 |

**Table 33 Electrical characteristics of the LIN transceiver** (cont'd)

$V_s$ = 5.5 V to 18 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Duty cycle D7 (for worst case at 115 kbit/s) for +1 µs receiver delay symmetry | $t_{duty1}$ | 0.399 | – | – | | [5] Duty cycle D7 $TH_{Rec}(max) = 0.744 \times V_S$; $TH_{Dom}(max) = 0.581 \times V_S$; $V_S$ = 13.5 V; $t_{bit}$ = 8.7 µs; D7 = $t_{bus\_rec(min)}$ / 2 $t_{bit}$ | P_6.1.34 |
| Duty cycle D8 (for worst case at 115 kbit/s) for +1 µs receiver delay symmetry | $t_{duty2}$ | – | – | 0.578 | | [5] Duty cycle D8 $TH_{Rec}(min) = 0.422 \times V_S$; $TH_{Dom}(min) = 0.284 \times V_S$; $V_S$ = 13.5 V; $t_{bit}$ = 8.7 µs; D8 = $t_{bus\_rec(max)}$ / 2 $t_{bit}$ | P_6.1.35 |
| LIN input capacity | $C_{LIN\_IN}$ | – | 15 | 30 | pF | [6] | P_6.1.69 |
| TxD dominant time out | $t_{timeout}$ | 6 | 12 | 20 | ms | $V_{TxD}$ = 0 V | P_6.1.36 |
| **Thermal shutdown (junction temperature)** | | | | | | | |
| Thermal shutdown temperature | $T_{jSD}$ | 190 | 200 | 215 | °C | [6] | P_6.1.65 |
| Thermal shutdown hysteresis | $\Delta T$ | – | 10 | – | K | [6] | P_6.1.66 |

1) Maximum limit specified by design.
2) $V_{BUS\_CNT} = (V_{th\_dom} + V_{th\ rec})/ 2$.
3) $V_{HYS} = V_{BUSrec} - V_{BUSdom}$.
4) Bus load concerning LIN spec 2.2:
   Load 1 = 1 nF / 1 kΩ = $C_{BUS}$ / $R_{BUS}$
   Load 2 = 6.8 nF / 660 Ω = $C_{BUS}$ / $R_{BUS}$
   Load 3 = 10 nF / 500 Ω = $C_{BUS}$ / $R_{BUS}$
5) Bus load
   Load 1 = 1 nF / 500 Ω = $C_{BUS}$ / $R_{BUS}$.
6) Not subject to production test, specified by design.

## 29.7 High-speed synchronous serial interface

### 29.7.1 SSC timing parameters

The table below provides the SSC timing in the TLE9862QXA40.

**Table 34 SSC master mode timing (operating conditions apply; CL = 50 pF)**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| SCLK clock period | $t_0$ | 1) $2 \times T_{SSC}$ | – | – | | 2) $V_{DDP} > 2.7$ V | P_7.1.1 |
| MTSR delay from SCLK | $t_1$ | 10 | – | – | ns | 2) $V_{DDP} > 2.7$ V | P_7.1.2 |
| MRST setup to SCLK | $t_2$ | 10 | – | – | ns | 2) $V_{DDP} > 2.7$ V | P_7.1.3 |
| MRST hold from SCLK | $t_3$ | 15 | – | – | ns | 2) $V_{DDP} > 2.7$ V | P_7.1.4 |

1) $T_{SSCmin} = T_{CPU} = 1/f_{CPU}$. If $f_{CPU}$ = 20 MHz, $t_0$ = 100 ns. $T_{CPU}$ is the CPU clock period.
2) Not subject to production test, specified by design.

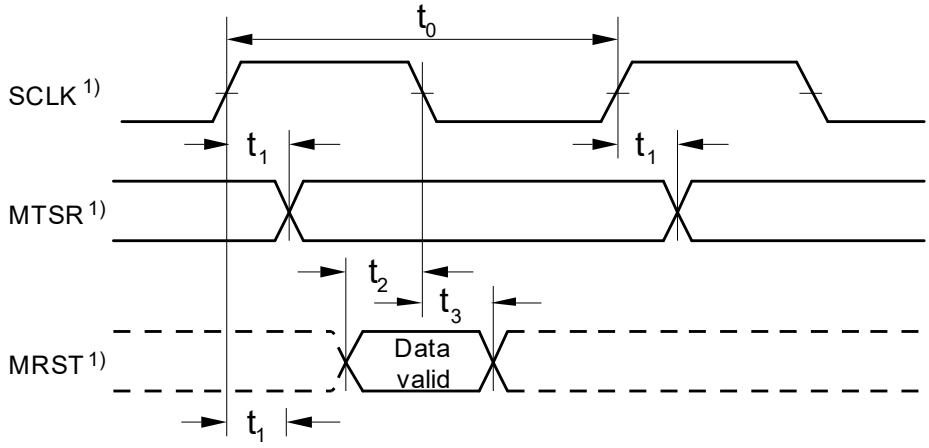


**Figure 35 SSC master mode timing**

## 29.8 Measurement unit

### 29.8.1 System voltage measurement parameters

**Table 35 Supply voltage signal conditioning**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Measurement output voltage range at VAREF5 | $V_{A5}$ | 0 | – | 5 | V | – | P_8.1.15 |
| Measurement output voltage range at VAREF1V2 | $V_{A1V2}$ | 0 | – | 1.23 | V | – | P_8.1.16 |
| **Battery/supply voltage measurement $V_{BAT\_SENSE}/V_S$** | | | | | | | |
| Input to output voltage attenuation: $V_S$ | $ATT_{VS\_1}$ | – | 0.055 | – | | SFR setting 1 | P_8.1.41 |
| Input to output voltage attenuation: $V_{BAT\_SENSE}$ | $ATT_{VBAT\_SENSE\_1}$ | – | 0.055 | – | | SFR setting 1 | P_8.1.60 |
| Nominal operating input voltage range $V_{BAT\_SENSE}$ and $V_S$ | $V_{BAT\_SENSE,range1}$, $V_{S,range1}$ | 3 | – | 22 | V | [1] SFR setting 1; max. value corresponds to typ. ADC full scale input; 3 V < $V_{BAT\_SENSE}/V_S$ < 28 V | P_8.1.1 |
| Accuracy of $V_{BAT\_SENSE}/V_S$ after calibration | $\Delta V_{BAT\_SENSE,range1}$, $V_{S,range1}$ | -220 | – | 220 | mV | SFR setting 1, $V_S$ = 5.5 V to 18 V | P_8.1.70 |
| Input to output voltage attenuation: $V_S$ | $ATT_{VS\_2}$ | – | 0.039 | – | | SFR setting 2 | P_8.1.42 |
| Input to output voltage attenuation: $V_{BAT\_SENSE}$ | $ATT_{VBAT\_SENSE\_2}$ | – | 0.039 | – | | SFR setting 2 | P_8.1.61 |
| Nominal operating input voltage range $V_{BAT\_SENSE}$ and $V_S$ | $V_{BAT\_SENSE,range2}$, $V_{S,range2}$ | 3 | – | 31 | V | [1] SFR setting 2; max. value corresponds to typ. ADC full scale input 3 V < $V_{BAT\_SENSE}/V_S$ < 28 V | P_8.1.40 |
| Accuracy of $V_{BAT\_SENSE}$ / $V_S$ after calibration | $\Delta V_{BAT\_SENSE,range2}$, $V_{S,range2}$ | -440 | – | 440 | mV | SFR setting 2, $V_S$ = 5.5 V to 18 V | P_8.1.44 |
| Measurement input leakage current for $V_{BAT\_SENSE}$ | $I_{leak\_VBAT\_SENSE,measure}$ | 0 | – | 4.0 | µA | PD_N=0 (off-state), $V_{BAT\_SENSE}$ = 13.5 V | P_8.1.72 |
| **Driver supply voltage measurement $V_{SD}$** | | | | | | | |
| Input to output voltage attenuation: $V_{SD}$ | $ATT_{VSD}$ | – | 0.039 | – | | – | P_8.1.21 |

**Table 35 Supply voltage signal conditioning** (cont'd)

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Nominal operating input voltage range $V_{SD}$ | $V_{SD,range}$ | 2.5 | – | 31 | V | 1) | P_8.1.2 |
| Accuracy of $V_{SD}$ sense after calibration | $\Delta V_{SD}$ | -440 | – | 440 | mV | $V_S$ = 5.5 V to 18 V | P_8.1.47 |
| **Charge pump voltage measurement $V_{CP}$** | | | | | | | |
| Input to output voltage attenuation: $V_{CP}$ | $ATT_{VCP}$ | – | 0.023 | – | | – | P_8.1.56 |
| Nominal operating input voltage range $V_{CP}$ | $V_{CP,range}$ | 2.5 | – | 52 | V | 1) | P_8.1.7 |
| Accuracy of $V_{CP}$ sense after calibration | $\Delta V_{CP}$ | -747 | – | 747 | mV | $V_S$ = 5.5 V to 18 V | P_8.1.62 |
| **Monitoring input voltage measurement $V_{MON}$** | | | | | | | |
| Input to output voltage attenuation: $V_{MON}$ | $ATT_{VMON}$ | – | 0.039 | – | | – | P_8.1.49 |
| Nominal operating input voltage range $V_{MON}$ | $V_{MON,range}$ | 2.5 | – | 31 | V | 1) | P_8.1.8 |
| Accuracy of $V_{MON}$ sense after calibration | $\Delta V_{MON}$ | -440 | – | 440 | mV | $V_S$ = 5.5 V to 18 V | P_8.1.68 |
| **Pad supply voltage measurement $V_{VDDP}$** | | | | | | | |
| Input-to-output voltage attenuation: $V_{DDP}$ | $ATT_{VDDP}$ | – | 0.164 | – | | – | P_8.1.33 |
| Nominal operating input voltage range $V_{DDP}$ | $V_{DDP,range}$ | 0 | – | 7.50 | V | 1) | P_8.1.50 |
| Accuracy of $V_{DDP}$ sense after calibration | $\Delta V_{DDP\_SENSE}$ | -105 | – | 105 | mV | 2) $V_S$ = 5.5 V to 18 V | P_8.1.5 |
| **10-bit ADC reference voltage measurement $V_{AREF}$** | | | | | | | |
| Input to output voltage attenuation: $V_{AREF}$ | $ATT_{VAREF}$ | – | 0.219 | – | | – | P_8.1.22 |
| Nominal operating input voltage range $V_{AREF}$ | $V_{AREF,range}$ | 0 | – | 5.62 | V | 1) | P_8.1.51 |
| Accuracy of $V_{AREF}$ sense after calibration | $\Delta V_{AREF}$ | -79 | – | 79 | mV | $V_S$ = 5.5 V to 18 V | P_8.1.48 |
| **8-bit ADC reference voltage measurement $V_{BG}$** | | | | | | | |
| Input-to-output voltage attenuation: $V_{BG}$ | $ATT_{VBG}$ | – | 0.75 | – | | – | P_8.1.57 |
| Nominal operating input voltage range $V_{BG}$ | $V_{BG,range}$ | 0.8 | – | 1.64 | V | 1) | P_8.1.52 |

**Table 35 Supply voltage signal conditioning** (cont'd)

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Value of ADC2-$V_{BG}$ measurement after calibration | $V_{BG\_PMU}$ | 1.01 | 1.07 | 1.18 | V | – | P_8.1.73 |
| **Core supply voltage measurement $V_{DDC}$** | | | | | | | |
| Input-to-output voltage attenuation: $V_{DDC}$ | $ATT_{VDDC}$ | – | 0.75 | – | | – | P_8.1.34 |
| Nominal operating input voltage range $V_{DDC}$ | $V_{DDC,range}$ | 0.8 | – | 1.64 | V | 1) | P_8.1.53 |
| Accuracy of $V_{DDC}$ sense after calibration | $\Delta V_{DDC\_SENSE}$ | -22 | – | 22 | mV | $V_S$ = 5.5 V to 18 V | P_8.1.6 |
| **VDH input voltage measurement $V_{VDH10BITADC}$** | | | | | | | |
| VDH input to output voltage attenuation | $ATT_{VDH\_1}$ | – | 0.166 | – | | SFR setting 1 | P_8.1.64 |
| VDH input to output voltage attenuation | $ATT_{VDH\_2}$ | – | 0.224 | – | | SFR setting 2 | P_8.1.65 |
| VDH input to output voltage attenuation | $ATT_{VDH\_3}$ | – | 0.226 | – | | 1) SFR setting 2, -40°C ≤ $T_j$ ≤ 85°C | P_8.1.75 |
| Nominal operating input voltage range $V_{VDH}$, attenuation range 1 | $V_{VDH,range1}$ | – | – | 30 | V | SFR setting 1 | P_8.1.66 |
| Nominal operating input voltage range $V_{VDH}$, attenuation range 2 | $V_{VDH,range2}$ | – | – | 20 | V | SFR setting 2 | P_8.1.67 |
| $V_{VDH}$ 10-bit ADC, range 1 | $\Delta V_{VDHADC10B}$ | -300 | – | 300 | mV | $V_{VDH}$ = 5.5 V to 17.5 V, -40°C ≤ $T_j$ ≤ 150°C | P_8.1.39 |
| $V_{VDH}$ 10-bit ADC, range 3 | $\Delta V_{VDHADC10B}$ | -200 | – | 200 | mV | 1) $V_{VDH}$= 5.5 V to 17.5 V, -40°C ≤ $T_j$ ≤ 85°C $ATT_{VDH\_3}$ | P_8.1.71 |
| $V_{VDH}$ 10-bit ADC, range 2 | $\Delta V_{VDHADC10B\_extend\_T}$ | -400 | – | 400 | mV | $V_{VDH}$ = 5.5 V to 17.5 V, -40°C ≤ $T_j$ ≤ 150°C | P_8.1.74 |
| 10-bit ADC measurement input resistance for VDH | $R_{in\_VDH,measure}$ | 200 | 390 | 470 | kΩ | PD_N = 1 (on-state) | P_8.1.3 |
| Measurement input leakage current for $V_{VDH}$ | $I_{leak\_VDH,\ measure}$ | -0.05 | – | 2.0 | µA | PD_N = 0 (off-state), $V_{VDH}$ = 13.5 V | P_8.1.10 |

1) Not subject to production test, specified by design.

2) Accuracy is valid for a calibrated device.

### 29.8.2 Central temperature sensor parameters

**Table 36 Electrical characteristics of the temperature sensor module**

$V_S$ = 3.0 V to 28 V, $T_j$ = -40°C to +150°C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Output voltage $V_{TEMP}$ at $T_0$ = 273 K (0°C) | *a* | – | 0.666 | – | V | 1) $T_0$ = 273 K (0°C) | P_8.2.2 |
| Temperature sensitivity b | *b* | – | 2.31 | – | mV/K | 1) | P_8.2.4 |
| Accuracy_1 | *Acc_1* | -10 | – | 10 | °C | 1)2) -40°C ≤ $T_j$ ≤ 85°C | P_8.2.5 |
| Accuracy_2 | *Acc_2* | -10 | – | 10 | °C | 1)2) 125°C < $T_j$ ≤ 150°C | P_8.2.6 |
| Accuracy_3 | *Acc_3* | -5 | – | 5 | °C | 1)2) 85°C < $T_j$ ≤ 125°C | P_8.2.7 |

1) Not subject to production test, specified by design.

2) Accuracy with reference to on-chip temperature calibration measurement, valid for Mode1 .

### 29.8.3 ADC2 VBG

#### 29.8.3.1 ADC2 reference voltage VBG

**Table 37 DC specifications**

$V_S$ = 3.0 V to 28 V, $T_j$ = -40°C to +150°C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Reference voltage | $V_{BG}$ | 1.199 | 1.211 | 1.223 | V | 1) | P_8.3.1 |

1) Not subject to production test, specified by design.

#### 29.8.3.2 ADC2 specifications

**Table 38 DC specifications**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Resolution | *RES* | – | 8 | – | bit | Full | P_8.3.18 |
| Guaranteed offset error | $EA_{OFF\_8Bit}$ | -2.0 | ±0.3 | 2.0 | LSB | Not calibrated | P_8.3.19 |
| Gain error | $EA_{Gain\_8Bit}$ | -2.0 | ±0.5 | 2.0 | %FSR | Not calibrated | P_8.3.20 |
| Differential non-linearity (DNL) | $EA_{DNL\_8Bit}$ | -0.8 | ±0 | 0.8 | LSB | Full | P_8.3.21 |
| Integral non-linearity (INL) | $EA_{INL\_8Bit}$ | -1.2 | ±0 | 1.2 | LSB | – | P_8.3.22 |

## 29.9 ADC1 reference voltage - VAREF

### 29.9.1 Electrical characteristics of VAREF

**Table 39 Electrical characteristics of VAREF**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Required buffer capacitance | $C_{VAREF}$ | 0.1 | – | 1 | µF | ESR < 1 Ω | P_9.1.1 |
| Reference output voltage | $V_{AREF}$ | 4.95 | 5 | 5.05 | V | $V_S$ > 5.5 V | P_9.1.2 |
| DC supply voltage rejection | $DC_{PSRVAREF}$ | 30 | – | – | dB | 1) | P_9.1.3 |
| Supply voltage ripple rejection | $AC_{PSRVAREF}$ | 26 | – | – | dB | 1) $V_S$ = 13.5 V; $f$ = 0 kHz … 1 kHz; $V_r$ = 2 Vpp | P_9.1.4 |
| Turn-on time | $t_{so}$ | – | – | 200 | µs | 1) $C_{ext}$ = 100 nF PD_N to 99.9% of final value | P_9.1.5 |
| Input resistance at VAREF pin | $R_{IN,VAREF}$ | – | 100 | – | kΩ | 1) Input impedance in case of VAREF is applied from external input | P_9.1.20 |

1) Not subject to production test, specified by design.

## 29.9.2 Electrical characteristics of the ADC1 (10-Bit)

These parameters describe the conditions for optimum ADC performance.

*Note: Operating conditions apply.*

**Table 40 A/D converter characteristics**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Analog reference supply | $V_{AREF}$ | $V_{AGND}$ + 1.0 | – | $V_{DDPA}$ + 0.05 | V | 1) | P_9.2.1 |
| Analog reference ground | $V_{AGND}$ | $V_{SS}$ - 0.05 | – | 1.5 | V | – | P_9.2.2 |
| Analog input voltage range | $V_{AIN}$ | $V_{AGND}$ | – | $V_{AREF}$ | V | 2) | P_9.2.3 |
| Analog clock frequency | $f_{ADCI}$ | 5 | – | 24 | MHz | 3) | P_9.2.4 |
| Conversion time for 10-bit result | $t_{C10}$ | (13 + STC) × $t_{ADCI}$ + 2 × $t_{SYS}$ | (13 + STC) × $t_{ADCI}$ + 2 × $t_{SYS}$ | (13 + STC) × $t_{ADCI}$ + 2 × $t_{SYS}$ | – | 1)4) | P_9.2.5 |
| Conversion time for 8-bit result | $t_{C8}$ | (11 + STC) × $t_{ADCI}$ + 2 × $t_{SYS}$ | (11 + STC) × $t_{ADCI}$ + 2 × $t_{SYS}$ | (11 + STC) × $t_{ADCI}$ + 2 × $t_{SYS}$ | – | 1) | P_9.2.6 |
| Wake-up time from analog power-down, fast mode | $t_{WAF}$ | – | – | 4 | µs | 1) | P_9.2.7 |
| Wake-up time from analog power-down, slow mode | $t_{WAS}$ | – | – | 15 | µs | 1)5) | P_9.2.8 |
| Total unadjusted error (8 bit) | $TUE_{8B}$ | -2 | ±1 | 2 | counts | 6)7) Reference is internal $V_{AREF}$ | P_9.2.9 |
| Total unadjusted error (10 bit) | $TUE_{10B}$ | -12 | ±6 | 12 | counts | 8)9) Reference is internal $V_{AREF}$ | P_9.2.22 |
| DNL error | $EA_{DNL}$ | -3 | ±0.8 | 3 | counts | – | P_9.2.10 |
| INL error | $EA_{INL\_int\_VAREF}$ | -5 | ±0.8 | 5 | counts | Reference is internal $V_{AREF}$ | P_9.2.11 |
| Gain error | $EA_{GAIN\_int\_VAREF}$ | -10 | ±0.4 | 10 | counts | Reference is internal $V_{AREF}$ | P_9.2.12 |
| Offset error | $EA_{OFF}$ | -2 | ±0.5 | 2 | counts | – | P_9.2.13 |
| Total capacitance of an analog input | $C_{AINT}$ | – | – | 10 | pF | 1)5)10) | P_9.2.14 |
| Switched capacitance of an analog input | $C_{AINS}$ | – | – | 4 | pF | 1)5)10) | P_9.2.15 |

**Table 40 A/D converter characteristics** (cont'd)

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Resistance of the analog input path | $R_{AIN}$ | – | – | 2 | kΩ | 1)5)10) | P_9.2.16 |
| Total capacitance of the reference input | $C_{AREFT}$ | – | – | 15 | pF | 1)5)10) | P_9.2.17 |
| Switched capacitance of the reference input | $C_{AREFS}$ | – | – | 7 | pF | 1)5)10) | P_9.2.18 |
| Resistance of the reference input path | $R_{AREF}$ | – | – | 2 | kΩ | 1)5)10) | P_9.2.19 |

1) Not subject to production test, specified by design.
2) $V_{AIN}$ may exceed $V_{AGND}$ or $V_{AREFx}$ up to the absolute maximum ratings. However, the conversion results in these cases will be $0000_H$ or $03FF_H$, respectively.
3) The limit values for $f_{ADCI}$ must not be exceeded when selecting the peripheral frequency and the prescaler setting.
4) This parameter includes the sample time (and the additional sample time specified by STC), the time to determine the digital results and the time to load the result register with the conversion result.
5) The broken wire detection delay against $V_{AGND}$ is measured in numbers of consecutive precharge cycles at a conversion rate of not more than 500 µs.
6) The total unadjusted error TUE is the maximum deviation from the ideal ADC transfer curve, not the sum of individual errors.
   All error specifications are based on measurement methods standardized by IEEE 1241.2000.
7) The specified TUE is valid only if the absolute sum of input overload currents (see $I_{OV}$ specification) does not exceed 10 mA, and if $V_{AREF}$ and $V_{AGND}$ remain stable during the measurement time.
8) The specified TUE is valid only if the absolute sum of input overload currents (see $I_{OV}$ specification) does not exceed 10 mA, and if $V_{AREF}$ and $V_{AGND}$ remain stable during the measurement time.
9) The total unadjusted error TUE is the maximum deviation from the ideal ADC transfer curve, not the sum of individual errors.
   All error specifications are based on measurement methods standardized by IEEE 1241.2000.
10) These parameter values cover the complete operating range. Under relaxed operating conditions (temperature, supply voltage), typical values can be used for the calculation. At room temperature and nominal supply voltage, the following typical values can be used:
    $C_{AINTtyp}$ = 12 pF, $C_{AINStyp}$ = 5 pF, $R_{AINtyp}$ = 1.0 kΩ, $C_{AREFTtyp}$ = 15 pF, $C_{AREFStyp}$ = 10 pF, $R_{AREFtyp}$ = 1.0 kΩ.

## 29.10 Reserved

## 29.11 High-voltage monitoring input

### 29.11.1 Electrical characteristics

**Table 41 Electrical characteristics od the monitoring input**

$T_j$ = -40°C to +150°C; $V_S$ = 5.5 V to 28 V, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **MON input pin characteristics** | | | | | | | |
| Wake-up/monitoring threshold voltage | $V_{MONth}$ | 0.4 × $V_S$ | 0.5 × $V_S$ | 0.6 × $V_S$ | V | Without external serial resistor $R_s$ (with $R_s$: DV = $I_{PD/PU}$ × $R_s$); $V_S$ = 5.5 V to 18 V; -40°C ≤ $T_j$ ≤ 85°C | P_11.1.1 |
| Wake-up/monitoring threshold voltage extended range | $V_{MONth\_extend}$ | 0.44 × $V_S$ | 0.53 × $V_S$ | 0.64 × $V_S$ | V | Without external serial resistor $R_s$ (with $R_s$: DV = $I_{PD/PU}$ × $R_s$) | P_11.1.11 |
| Threshold hysteresis | $V_{MONth,hys}$ | 0.015 × $V_S$ | 0.05 × $V_S$ | 0.1 × $V_S$ | V | In all modes; without external serial resistor $R_s$ (with $R_s$: $dV$ = $I_{PD/PU}$ × $R_s$); $V_S$ = 5.5 V to 18 V | P_11.1.12 |
| Threshold hysteresis | $V_{MONth,hys}$ | 0.02 × $V_S$ | 0.06 × $V_S$ | 0.12 × $V_S$ | V | In all modes; without external serial resistor $R_s$ (with $R_s$: $dV$ = $I_{PD/PU}$ × $R_s$); $V_S$ = 18 V to 28 V | P_11.1.2 |
| Pull-up current | $I_{PU, MON}$ | -20 | -10 | -1 | µA | 0.6 × $V_S$ | P_11.1.3 |
| Pull-down current | $I_{PD, MON}$ | 3 | 10 | 20 | µA | 0.4 × $V_S$ | P_11.1.4 |
| Input leakage current | $I_{LK,MON}$ | -2.5 | – | 2.5 | µA | [1] 0 V < $V_{MON\_IN}$ < 28 V | P_11.1.5 |
| **Timing** | | | | | | | |
| Wake-up filter time (internal analog filter delay) | $t_{FT,MON}$ | – | 500 | – | ns | [2] The overall filter time for MON wake-up is the sum of $t_{FT,MON}$ and the adjustable digital filter time. The digital filter time can be adjusted by setting the PMU.CNF_WAKE_FILTER. CNF_MON_FT register | P_11.1.6 |

1) Input leakage is valid for the disabled state.

2) With pull-up, pull-down current disabled.

## 29.12 MOSFET driver

### 29.12.1 Electrical characteristics

**Table 42 Electrical characteristics of the MOSFET driver**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **MOSFET driver output** | | | | | | | |
| Maximum total charge driver capability | $Q_{tot\_max}$ | – | – | 100 | nC | [1] Due to charge pump current capability, six MOSFETs and additional external capacitors with a total charge of maximal 100 nC can be driven simultaneously at a PWM frequency of 25 kHz | P_12.1.20 |
| Maximum total charge driver capability (three-phase PWM) | $Q_{tot\_max,20kHz}$ | – | – | 150 | nC | [1] Due to charge pump current capability, six MOSFETs and additional external capacitors with a total charge of maximal 150 nC can be driven simultaneously at a PWM frequency of 20 kHz. $V_{SD,min} \geq 6.5$ V for $V_{GS,min} \geq 7$ V | P_12.1.120 |
| Source current - charge current - high-side driver | $I_{Soumax\_HS}$ | 230 | 345 | 450 | mA | $V_{SD} \geq 8$ V, $C_{Load}$ = 10 nF, $I_{Sou} = C_{Load} \times$ slew rate (= 20% to 50% of $V_{GHx1}$), $I_{CHARGE} = I_{DISCHG}$ = 31(max) | P_12.1.78 |
| Sink current - discharge current - high-side driver | $I_{Sinkmax\_HS}$ | 230 | 330 | 450 | mA | $V_{SD} \geq 8$ V, $C_{Load}$ = 10 nF, $I_{Sink} = C_{Load} \times$ slew rate (from 80% to 50% of $V_{GHx1}$), $I_{CHARGE} = I_{DISCHG}$ = 31(max) | P_12.1.79 |
| Source current - charge current - low-side driver | $I_{Soumax\_LS}$ | 200 | 295 | 375 | mA | $V_{SD} \geq 8$ V, $C_{Load}$ = 10 nF, $I_{Sou} = C_{Load} \times$ slew rate (= 20% to 50% of $V_{GLx1}$), $I_{CHARGE} = I_{DISCHG}$ = 31(max) | P_12.1.80 |
| Sink current - discharge current - low-side driver | $I_{Sinkmax\_LS}$ | 200 | 314 | 375 | mA | $V_{SD} \geq 8$ V, $C_{Load}$ = 10 nF, $I_{Sink} = C_{Load} \times$ slew rate (from 80% to 50% of $V_{GLx1}$), $I_{CHARGE} = I_{DISCHG}$ = 31(max) | P_12.1.81 |

**Table 42 Electrical characteristics of the MOSFET driver** (cont'd)

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| High-level output voltage Gxx vs. Sxx | $V_{Gxx1}$ | 10 | – | 14 | V | $V_{SD} \geq 8$ V, $C_{Load}$ = 10 nF, $I_{CP}$ = 2.5 mA[2] | P_12.1.3 |
| High-level output voltage GHx vs. SHx | $V_{Gxx2}$ | 8 | – | 14 | V | $V_{SD}$ = 6.4 V[1], $C_{Load}$ = 10 nF, $I_{CP}$ = 2.5 mA[2] | P_12.1.4 |
| High-level output voltage GHx vs. SHx | $V_{Gxx3}$ | 7 | – | 14 | V | $V_{SD}$ = 5.4 V, $C_{Load}$ = 10 nF, $I_{CP}$ = 2.5 mA[2] | P_12.1.5 |
| High-level output voltage GLx vs. GND | $V_{Gxx6}$ | 8 | – | 14 | V | $V_{SD}$ = 6.4 V[1], $C_{Load}$ = 10 nF, $I_{CP}$ = 2.5 mA[2] | P_12.1.6 |
| High-level output voltage GLx vs. GND | $V_{Gxx7}$ | 7 | – | 14 | V | $V_{SD}$ = 5.4 V, $C_{Load}$ = 10 nF, $I_{CP}$ = 2.5 mA[2] | P_12.1.7 |
| Rise time | $t_{rise3\_3nf}$ | – | 200 | – | ns | [1] $C_{Load}$ = 3.3 nF, $V_{SD} \geq 8$ V, 25% to 75% of $V_{Gxx1}$, $I_{CHARGE} = I_{DISCHG}$ = 31(max) | P_12.1.8 |
| Fall time | $t_{fall3\_3nf}$ | – | 200 | – | ns | [1] $C_{Load}$ = 3.3 nF, $V_{SD} \geq 8$ V, 75% to 25% of $V_{Gxx1}$, $I_{CHARGE} = I_{DISCHG}$ = 31(max) | P_12.1.9 |
| Rise time | $t_{risemax}$ | 100 | 250 | 450 | ns | $C_{Load}$ = 10 nF, $V_{SD} \geq 8$ V, 25% to 75% of $V_{Gxx1}$, $I_{CHARGE} = I_{DISCHG}$ = 31(max) | P_12.1.57 |
| Fall time | $t_{fallmax}$ | 100 | 250 | 450 | ns | $C_{Load}$ = 10 nF, $V_{SD} \geq 8$ V, 75% to 25% of $V_{Gxx1}$, $I_{CHARGE} = I_{DISCHG}$ = 31(max) | P_12.1.58 |
| Rise time | $t_{risemin}$ | 1.25 | 2.5 | 5 | µs | [1] $C_{Load}$ = 10 nF, $V_{SD} \geq 8$ V, 25% to 75% of $V_{Gxx1}$, $I_{CHARGE} = I_{DISCHG}$ = 3(min) | P_12.1.14 |
| Fall time | $t_{fallmin}$ | 1.25 | 2.5 | 5 | µs | [1] $C_{Load}$ = 10 nF, $V_{SD} \geq 8$ V, 75% to 25% of $V_{Gxx1}$, $I_{CHARGE} = I_{DISCHG}$ = 3(min) | P_12.1.15 |
| Absolute difference between rise and fall for all LSx | $t_{r\_f(diff)LSx}$ | – | – | 100 | ns | $C_{Load}$ = 10 nF, $V_{SD} \geq 8$ V, 25% to 75% of $V_{Gxx1}$, $I_{CHARGE} = I_{DISCHG}$ = 31(max) | P_12.1.35 |

**Table 42 Electrical characteristics of the MOSFET driver** (cont'd)

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Absolute difference between rise and fall for all HSx | $t_{r\_f(diff)HSx}$ | – | – | 100 | ns | $C_{Load}$ = 10 nF, $V_{SD} \geq$ 8 V, 25% to 75% of $V_{Gxx1}$, $I_{CHARGE} = I_{DISCHG}$ = 31(max) | P_12.1.36 |
| Resistor between GHx/GLx and GND | $R_{GGND}$ | 30 | 40 | 50 | kΩ | 1) | P_12.1.11 |
| Resistor between SHx and GND | $R_{SHGN}$ | 30 | 40 | 50 | kΩ | 1)3) This resistance is the resistance between GHx and GND connected through a diode to SHx. As a consequence, the voltage at SHx can rise up to 0.6 V typ. before it is discharged through the resistor | P_12.1.10 |
| Low-RDSON mode (boosted discharge mode) | $R_{ONCCP}$ | – | 9 | 12 | Ω | $V_{VSD}$ = 13.5 V, $V_{VCP}$ = $V_{VSD}$ + 14.0 V; $I_{CHARGE} = I_{DISCHG}$ = 31(max); 50 mA forced into Gx, Sx grounded | P_12.1.50 |
| Resistance between VDH and VSD | $I_{BSH}$ | – | 4 | – | kΩ | 1) | P_12.1.24 |
| Input propagation time (LS on) | $t_{P(ILN)min}$ | – | 1.5 | 3 | µs | 1) $C_{Load}$ = 10 nF, $I_{Charge}$ = 3(min), 25% of $V_{Gxx1}$ | P_12.1.37 |
| Input propagation time (LS off) | $t_{P(ILF)min}$ | – | 1.5 | 3 | µs | 1) $C_{Load}$ = 10 nF, $I_{Discharge}$ = 3(min), 75% of $V_{Gxx1}$ | P_12.1.38 |
| Input propagation time (HS on) | $t_{P(IHN)min}$ | – | 1.5 | 3 | µs | 1) $C_{Load}$ = 10 nF, $I_{Charge}$ = 3(min), 25% of $V_{Gxx1}$ | P_12.1.39 |
| Input propagation time (HS off) | $t_{P(IHF)min}$ | – | 1.5 | 3 | µs | 1) $C_{Load}$ = 10 nF, $I_{Discharge}$ = 3(min), 75% of $V_{Gxx1}$ | P_12.1.40 |
| Input propagation time (LS on) | $t_{P(ILN)max}$ | – | 200 | 350 | ns | $C_{Load}$ = 10 nF, $I_{Charge}$ = 31(max), 25% of $V_{Gxx1}$ | P_12.1.26 |
| Input propagation time (LS off) | $t_{P(ILF)max}$ | – | 200 | 300 | ns | $C_{Load}$ = 10 nF, $I_{Discharge}$ = 31(max), 75% of $V_{Gxx1}$ | P_12.1.27 |

**Table 42 Electrical characteristics of the MOSFET driver** (cont'd)

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Input propagation time (HS on) | $t_{P(IHN)max}$ | – | 200 | 350 | ns | $C_{Load}$ = 10 nF, $I_{Charge}$ = 31(max), 25% of $V_{Gxx1}$ | P_12.1.28 |
| Input propagation time (HS off) | $t_{P(IHF)max}$ | – | 200 | 300 | ns | $C_{Load}$ = 10 nF, $I_{Discharge}$ = 31(max), 75% of $V_{Gxx1}$ | P_12.1.29 |
| Absolute input propagation time difference between propagation times for all LSx (LSx on) | $t_{Pon(diff)LSx}$ | – | – | 100 | ns | $C_{Load}$ = 10 nF, $I_{Charge}$ = 31(max), 25% of $V_{Gxx1}$ | P_12.1.30 |
| Absolute input propagation time difference between propagation times for all LSx (LSx off) | $t_{Poff(diff)LSx}$ | – | – | 100 | ns | $C_{Load}$ = 10 nF, $I_{Discharge}$ = 31(max), 75% of $V_{Gxx1}$ | P_12.1.41 |
| Absolute input propagation time difference between propagation times for all HSx (HSx on) | $t_{Pon(diff)HSx}$ | – | – | 100 | ns | $C_{Load}$ = 10 nF, $I_{Charge}$ = 31(max), 25% of $V_{Gxx1}$ | P_12.1.42 |
| Absolute input propagation time difference between propagation times for all HSx (HSx off) | $t_{Poff(diff)HSx}$ | – | – | 100 | ns | $C_{Load}$ = 10 nF, $I_{Discharge}$ = 31(max), 75% of $V_{Gxx1}$ | P_12.1.43 |
| **Drain source monitoring** | | | | | | | |
| Drain source monitoring threshold | $V_{DSMONVTH}$ | – | – | – | V | DRV_CTRL3.DSMONVTH<2:0> xxx | P_12.1.46 |
| | | 0.07 | 0.25 | 0.40 | | 000 | |
| | | 0.35 | 0.50 | 0.650 | | 001 | |
| | | 0.55 | 0.75 | 0.90 | | 010 | |
| | | 0.65 | 1.00 | 1.25 | | 011 | |
| | | 0.90 | 1.25 | 1.45 | | 100 | |
| | | 1.00 | 1.5 | 1.80 | | 101 | |
| | | 1.20 | 1.75 | 2.10 | | 110 | |
| | | 1.40 | 2.00 | 2.40 | | 111 | |
| **Open load diagnostic currents** | | | | | | | |
| Pull-up diagnostic current | $I_{PUDiag}$ | -220 | -370 | -520 | µA | $I_{DISCHG}$ = 1; $V_{SHx}$ = 5.0 V | P_12.1.47 |
| Pull-down diagnostic current | $I_{PDDiag}$ | 650 | 900 | 1100 | µA | $I_{DISCHG}$ = 1; $V_{SHx}$ = 5.0 V | P_12.1.48 |

**Table 42 Electrical characteristics of the MOSFET driver** (cont'd)

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **Charge pump** | | | | | | | |
| Output voltage VCP vs. VSD | $V_{CPmin1}$ | 8.5 | – | – | V | $V_{VSD}$ = 5.4 V, $I_{CP}$ = 5 mA, $C_{CP1}$, $C_{CP2}$ = 220 nF, bridge driver enabled | P_12.1.53 |
| Regulated output voltage VCP vs. VSD | $V_{CP}$ | 12 | 14 | 16 | V | 8 V ≤ $V_{VSD}$ ≤ 28 V, $I_{CP}$ = 10 mA, $C_{CP1}$, $C_{CP2}$ = 220 nF, $f_{CP}$ = 250 kHz | P_12.1.49 |
| Turn-on time | $t_{ON\_VCP}$ | 10 | 24 | 40 | us | 8 V ≤ $V_{VSD}$ ≤ 28 V, $I_{CP}$ = 2.5 mA, (25%) of $V_{CP}$ [1)4)], $C_{CP1}$, $C_{CP2}$ = 220 nF, $f_{CP}$ = 250 kHz | P_12.1.59 |
| Rise time | $t_{rise\_VCP}$ | 20 | 60 | 88 | us | 8 V ≤ $V_{VSD}$ ≤ 28 V, $I_{CP}$ = 2.5 mA, (25% to 75%) of $V_{CP}$ [1)5)], $C_{CP1}$, $C_{CP2}$ = 220 nF, $f_{CP}$ = 250 kHz | P_12.1.60 |

1) Not subject to production test, specified by design.
2) The condition $I_{CP}$ = 2.5 mA emulates a H-Bridge Driver with 4 MOSFETs switching at 20 kHz with a $C_{Load}$ = 3.3 nF. Test condition: $I_{Gx}$ = - 100 µA, ICHARGE = IDISCHARGE = 31 (max), IDISCHARGEDIV2_N = 1 and ICHARGEDIV2_N = 1.
3) This resistance is connected through a diode between SHx and GHx to ground.
4) This time applies when the DRV_CP_CTRL_STS.bit.CP_EN bit is set.
5) This time applies when the DRV_CP_CLK_CTRL.bit.CPCLK_EN bit is set.

## 29.13 Operational amplifier

### 29.13.1 Electrical characteristics

**Table 43 Electrical characteristics of the operational amplifier**

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Differential gain (uncalibrated) | $G$ | <br>9.5<br>19<br>38<br>57 | <br>10<br>20<br>40<br>60 | <br>10.5<br>21<br>42<br>63 | | Gain settings GAIN<1:0>:<br>00<br>01<br>10<br>11 | P_13.1.6 |
| Differential input operating voltage range OP2 - OP1 | $V_{IX}$ | -1.5 / G | – | 1.5 / G | V | G is the gain specified below | P_13.1.1 |
| Operating: common mode input voltage range (referred to GND: OP2 - GND or OP1 - GND) | $V_{CM}$ | -2.0 | – | 2.0 | V | Input common mode has to be checked in evaluation if it fits the required range. | P_13.1.2 |
| Max. input voltage range (referred to GND: OP_2 - GND or OP1 - GND) | $V_{IX\_max}$ | -7.0 | – | 7.0 | V | Max. rating of operational amplifier inputs when no measurement is performed. | P_13.1.3 |
| Single-ended output voltage range (linear range) | $V_{OUT}$ | $V_{ZERO}$ - 1.5 | – | $V_{ZERO}$ + 1.5 | V | [1)2)] Offset output voltage 2 V ± 1.5 V | P_13.1.4 |
| Linearity error | $E_{PWM}$ | -15 | – | 15 | mV | Maximum deviation from best-fit straight line divided by the maximum value of the differential output voltage range (0.5 V - 3.5 V); this parameter is determined with G = 10 | P_13.1.5 |
| Linearity error | $E_{PWM\_\%}$ | -1.0 | – | 1.0 | % | Maximum deviation from best fit straight line divided by the maximum value of the differential output voltage range (0.5 V - 3.5 V); this parameter is determined with G = 10 | P_13.1.24 |

**Table 43 Electrical characteristics of the operational amplifier** (cont'd)

$V_S$ = 5.5 V to 28 V, $T_j$ = -40°C to +150°C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified).

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Gain drift | | -1 | – | 1 | % | Gain drift after calibration with G = 10 | P_13.1.7 |
| Adjusted output offset voltage | $V_{OOS}$ | -40 | 10 | 40 | mV | $V_{AIP}$= $V_{AIN}$ = 0 V and G = 40 | P_13.1.17 |
| DC input voltage common mode rejection ratio | DC-CMRR | 58 | 80 | – | dB | CMRR (in dB) = -20*log (differential mode gain / common mode gain) $V_{CMI}$ = -2 V … 2V, $V_{AIP}$-$V_{AIN}$= 0 V | P_13.1.8 |
| Settling time to 98% | $T_{SET}$ | – | 800 | 1400 | ns | 2) Derived from 80% - 20% rise fall times for ±2 V overload condition (3 Tau value of settling time constant) | P_13.1.9 |
| Current sense amplifier input resistance at OP1, OP2 | $R_{in\_OP1\_OP2}$ | 1 | 1.25 | 1.5 | kΩ | 2) | P_13.1.25 |

1) Typical $V_{ZERO}$ = 0,4 × $V_{AREF}$.

2) Not subject to production test, specified by design.

# 30 Package information

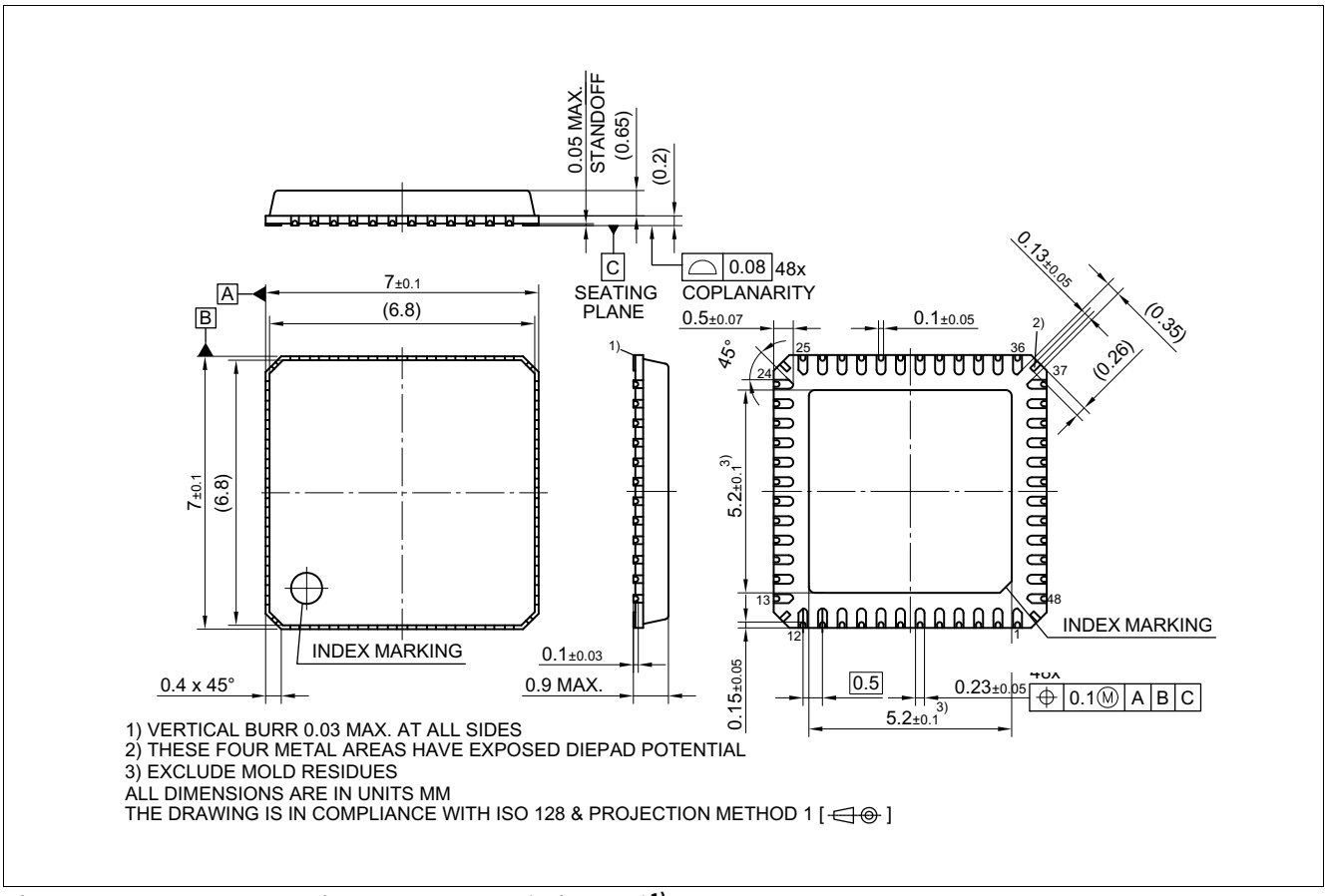


**Figure 36 Package outline VQFN-48-29 (with LTI)[1)]**

### Green product (RoHS-compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations, the device is available as a green product. Green products are RoHS-compliant (i.e., Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

### Further information on packages

**https://www.infineon.com/packages**

1) Dimensions in mm

# 31 Revision history

| Revision | Date | Changes |
|---|---|---|
| Rev. 1.0 | 2020-07-23 | Datasheet initial release. |

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